Alessandro Paccagnella

Elenco delle pubblicazioni

Tratto da database Scopus, aprile 2019

1. Rosati G., Ravarotto M., Scaramuzza M., De Toni A., Paccagnella A.,"Silver nanoparticles inkjet-printed flexible biosensor for rapid label-free antibiotic detection in milk",2019,"Sensors and Actuators, B: Chemical","280",,,"280","289",,"10.1016/j.snb.2018.09.084","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85055044105&doi=10.1016%2fj.snb.2018.09.084&partnerID=40&md5=f5e39ba5c5aed7b87842d1ad194f978b"
2. Cao H., Bastieri D., Rando R., Urso G., Luo G., Paccagnella A.,"Machine learning on compton event identification for a nano-satellite mission",2019,"Experimental Astronomy",,,,"","",,"10.1007/s10686-019-09620-4","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85060706516&doi=10.1007%2fs10686-019-09620-4&partnerID=40&md5=d766674301c8522b9865016f9db78271"
3. Bonaldo S., Mattiazzo S., Enz C., Baschirotto A., Paccagnella A., Jin X., Gerardin S.,"Influence of Halo Implantations on the Total Ionizing Dose Response of 28-nm pMOSFETs Irradiated to Ultrahigh Doses",2019,"IEEE Transactions on Nuclear Science","66","1", 8502145,"82","90",,"10.1109/TNS.2018.2876943","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85055213185&doi=10.1109%2fTNS.2018.2876943&partnerID=40&md5=41a3a7b45a91b0b56682e021bb9b055f"
4. Rosati G., Cunego A., Fracchetti F., Del Casale A., Scaramuzza M., De Toni A., Torriani S., Paccagnella A.,"Inkjet printed interdigitated biosensor for easy and rapid detection of bacteriophage contamination: A preliminary study for milk processing control applications",2019,"Chemosensors","7","1", 8,"","",,"10.3390/chemosensors7010008","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85064106397&doi=10.3390%2fchemosensors7010008&partnerID=40&md5=5085e658a707ef8d9784d38b94ea151a"
5. Bagatin M., Gerardin S., Paccagnella A., Beltrami S., Costantino A., Muschitiello M., Zadeh A., Ferlet-Cavrois V.,"Total Ionizing Dose Effects in 3-D NAND Flash Memories",2019,"IEEE Transactions on Nuclear Science","66","1", 8517156,"48","53",,"10.1109/TNS.2018.2878911","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85055873119&doi=10.1109%2fTNS.2018.2878911&partnerID=40&md5=53a5e38e8db082303d7f2c03391bbf66"
6. Stockman A., Tajalli A., Meneghini M., Uren M.J., Mouhoubi S., Gerardin S., Bagatin M., Paccagnella A., Meneghesso G., Zanoni E., Moens P., Bakeroot B.,"The Effect of Proton Irradiation in Suppressing Current Collapse in AlGaN/GaN High-Electron-Mobility Transistors",2019,"IEEE Transactions on Electron Devices","66","1", 8556004,"372","377",,"10.1109/TED.2018.2881325","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85057824667&doi=10.1109%2fTED.2018.2881325&partnerID=40&md5=5b232fcc008d1f5cfc1a8b16d45acde0"

7. Rosati G., Gherardi G., Grigoletto D., Marcolin G., Cancellara P., Mammucari C., Scaramuzza M., De Toni A., Reggiani C., Rizzuto R., Paccagnella A.,"Lactate Dehydrogenase and Glutamate Pyruvate Transaminase biosensing strategies for lactate detection on screen-printed sensors. Catalysis efficiency and interference analysis in complex matrices: from cell cultures to sport medicine",2018,"Sensing and Bio-Sensing Research","21",,,"54","64",,"10.1016/j.sbsr.2018.10.004","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85055173254&doi=10.1016%2fj.sbsr.2018.10.004&partnerID=40&md5=be7d4a7d06e99a6b8e965970d6af425b"
8. Resta F., Gerardin S., Mattiazzo S., Paccagnella A., De Matteis M., Enz C., Baschirotto A.,"1GigaRad TID impact on 28 nm HEP analog circuits",2018,"Integration","63",,,"306","314",,"10.1016/j.vlsi.2018.04.007","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85046685900&doi=10.1016%2fj.vlsi.2018.04.007&partnerID=40&md5=86091c63e61e51e471e2206f2b1bf655"
9. Borghello G., Faccio F., Lerario E., Michelis S., Kulis S., Fleetwood D.M., Schrimpf R.D., Gerardin S., Paccagnella A., Bonaldo S.,"Dose-rate sensitivity of 65-nm MOSFETs Exposed to ultrahigh doses",2018,"IEEE Transactions on Nuclear Science","65","8", 8340851,"1482","1487",,"10.1109/TNS.2018.2828142","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85045767747&doi=10.1109%2fTNS.2018.2828142&partnerID=40&md5=c9c29f75c6f951f5ebd5aba26786a4e3"
10. Tajalli A., Stockman A., Meneghini M., Mouhoubi S., Banerjee A., Gerardin S., Bagatin M., Paccagnella A., Zanoni E., Tack M., Bakeroot B., Moens P., Meneghesso G.,"Dynamic-ron control via proton irradiation in AlGaN/GaN transistors",2018,"Proceedings of the International Symposium on Power Semiconductor Devices and ICs","2018-May",,,"92","95",,"10.1109/ISPSD.2018.8393610","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85049968295&doi=10.1109%2fISPSD.2018.8393610&partnerID=40&md5=4aeab562d2ad27c6a9beb4b62b5b1404"
11. Andreani C., Senesi R., Paccagnella A., Bagatin M., Gerardin S., Cazzaniga C., Frost C.D., Picozza P., Gorini G., Mancini R., Sarno M.,"Fast neutron irradiation tests of flash memories used in space environment at the ISIS spallation neutron source",2018,"AIP Advances","8","2", 025013,"","",,"10.1063/1.5017945","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85042192034&doi=10.1063%2f1.5017945&partnerID=40&md5=c11df2c5f88c990b1d8ab88eee899f52"
12. Meneghim M., Tajalli A., Moens P., Banerjee A., Stockman A., Tack M., Gerardm S., Bagatin M., Paccagnella A., Zanom E., Meneghesso G.,"Total suppression of dynamic-ron in AlGaN/GaN-HEMTs through proton irradiation",2018,"Technical Digest - International Electron Devices Meeting, IEDM",,,,"33.5.1","33.5.4",,"10.1109/IEDM.2017.8268492","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85045201010&doi=10.1109%2fIEDM.2017.8268492&partnerID=40&md5=156726b600a0a803ece4fb7c93d83326"
13. Rosati G., Scaramuzza M., Pasqualotto E., De Toni A., Paccagnella A.,"Optimization of cyclic voltammetric curve parameters to measure lactate concentration in urine samples",2018,"Lecture Notes in Electrical Engineering","431",,,"103","110",,"10.1007/978-3-319-55077-0_14","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85029666059&doi=10.1007%2f978-3-319-55077-0_14&partnerID=40&md5=4764bd08e647ac5bd4172c1b528c045b"

14. Bagatin M., Gerardin S., Paccagnella A., Beltrami S., Cazzaniga C., Frost C.D.,"Atmospheric Neutron Soft Errors in 3D NAND Flash Memories",2018,"IEEE Transactions on Nuclear Science",,,,"","",,"10.1109/TNS.2018.2886401","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85058654003&doi=10.1109%2fTNS.2018.2886401&partnerID=40&md5=c7a058921324e3fb5872058de1678ef3"
15. Bagatin M., Gerardin S., Paccagnella A., Beltrami S., Camerlenghi E., Bertuccio M., Costantino A., Zadeh A., Ferlet-Cavrois V., Santin G., Daly E.,"Effects of Heavy-Ion Irradiation on Vertical 3-D NAND Flash Memories",2018,"IEEE Transactions on Nuclear Science","65","1",8119991,"318","325",,"10.1109/TNS.2017.2777887","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85035753325&doi=10.1109%2fTNS.2017.2777887&partnerID=40&md5=bb8e211b77c52bdd751faf2253e6c1c2"
16. Faccio F., Borghello G., Lerario E., Fleetwood D.M., Schrimpf R.D., Gong H., Zhang E.X., Wang P., Michelis S., Gerardin S., Paccagnella A., Bonaldo S.,"Influence of LDD Spacers and H+ Transport on the Total-Ionizing-Dose Response of 65-nm MOSFETs Irradiated to Ultrahigh Doses",2018,"IEEE Transactions on Nuclear Science","65","1",8060540,"164","174",,"10.1109/TNS.2017.2760629","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85031793644&doi=10.1109%2fTNS.2017.2760629&partnerID=40&md5=a6775f6b59a4f107525b58ed43f33beb"
17. Gerardin S., Bagatin M., Paccagnella A., Voss K., Grürmann K., Ferlet-Cavrois V.,"Complete loss of functionality and permanent page fails in NAND flash memories",2017,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS","2016-September",,,"1","4",,"10.1109/RADECS.2016.8093167","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85043596564&doi=10.1109%2fRADECS.2016.8093167&partnerID=40&md5=e97f3870d9598a76313fe84d8514666b"
18. Bagatin M., Gerardin S., Paccagnella A., Costantino A., Ferlet-Cavrois V., Virtanen A., Kettunen H., Wang P.,"Effects of high-energy electrons in advanced NAND flash memories",2017,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS","2016-September",,,"1","5",,"10.1109/RADECS.2016.8093108","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85043595649&doi=10.1109%2fRADECS.2016.8093108&partnerID=40&md5=f23428bd07cd1bc7cc5c003fe127d6cf"
19. Alayan M., Bagatin M., Gerardin S., Paccagnella A., Vianello E., Nowak E., De Salvo B., Larcher L., Perniola L.,"Heavy-ion upset immunity of RRAM cells based on thin HfO2 layers",2017,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS","2016-September",,,"1","5",,"10.1109/RADECS.2016.8093174","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85043577955&doi=10.1109%2fRADECS.2016.8093174&partnerID=40&md5=2b7ac6283a5eb34fa2b4d04bd82f8fc5"
20. Basiricò L., Basile A.F., Cosseddu P., Gerardin S., Cramer T., Bagatin M., Ciavatti A., Paccagnella A., Bonfiglio A., Fraboni B.,"Space Environment Effects on Flexible, Low-Voltage Organic Thin-Film Transistors",2017,"ACS Applied Materials and Interfaces","9","40",,"35150","35158",,"10.1021/acsami.7b08440","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

85031307650&doi=10.1021%2facsami.7b08440&partnerID=40&md5=f044d3076f9e032581660c43395672b1"

21. Alayan M., Bagatin M., Gerardin S., Paccagnella A., Larcher L., Vianello E., Nowak E., De Salvo B., Perniola L.,"Experimental and Simulation Studies of the Effects of Heavy-Ion Irradiation on HfO2-Based RRAM Cells",2017,"IEEE Transactions on Nuclear Science","64","8", 7964778,"2038","2045",,"10.1109/TNS.2017.2721980","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85023760337&doi=10.1109%2fTNS.2017.2721980&partnerID=40&md5=9d1bf464be8f722e3f3b184990ee9a54"
22. Resta F., Gerardin S., Mattiazzo S., Paccagnella A., De Matteis M., Enz C., Baschirotto A.,"1GigaRad TID impact on 28nm HEP analog circuits",2017,"PRIME 2017 - 13th Conference on PhD Research in Microelectronics and Electronics, Proceedings",,, 7974148,"225","228",,"10.1109/PRIME.2017.7974148","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85027580723&doi=10.1109%2fPRIME.2017.7974148&partnerID=40&md5=fe114a733af0eda648c103124a9ddb74"
23. Bagatin M., Gerardin S., Paccagnella A.,"Space and terrestrial radiation effects in flash memories",2017,"Semiconductor Science and Technology","32","3", 033003,"","",,"10.1088/1361-6641/32/3/033003","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85014512009&doi=10.1088%2f1361-6641%2f32%2f3%2f033003&partnerID=40&md5=91c0e97c3b70666b40660a506d8707c9"
24. Mattiazzo S., Bagatin M., Bisello D., Gerardin S., Marchioro A., Paccagnella A., Pantano D., Pezzotta A., Zhang C.-M., Baschirotto A.,"Total Ionizing Dose effects on a 28 nm Hi-K metal-gate CMOS technology up to 1 Grad",2017,"Journal of Instrumentation","12","2", C02003,"","",,"10.1088/1748-0221/12/02/C02003","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85014587448&doi=10.1088%2f1748-0221%2f12%2f02%2fC02003&partnerID=40&md5=958d05cdccd5fc491c622713bb788e58"
25. Bagatin M., Gerardin S., Paccagnella A., Visconti A., Virtanen A., Kettunen H., Costantino A., Ferlet-Cavrois V., Zadeh A.,"Single Event Upsets Induced by Direct Ionization from Low-Energy Protons in Floating Gate Cells",2017,"IEEE Transactions on Nuclear Science","64","1", 7778119,"464","470",,"10.1109/TNS.2016.2637571","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85015752887&doi=10.1109%2fTNS.2016.2637571&partnerID=40&md5=53b375f08c1f616afa9cf12a43c2037c"
26. Gerardin S., Bagatin M., Paccagnella A., Visconti A., Bonanomi M., Calabrese M., Chiavarone L., Ferlet-Cavrois V., Schwank J.R., Shaneyfelt M.R., Dodds N., Trinczek M., Blackmore E.,"Upsets in Erased Floating Gate Cells with High-Energy Protons",2017,"IEEE Transactions on Nuclear Science","64","1", 7779057,"421","426",,"10.1109/TNS.2016.2636830","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85015740251&doi=10.1109%2fTNS.2016.2636830&partnerID=40&md5=81a4f84a8394b563a6c595d2a7125d3a"
27. Demaria N., Barbero M.B., Fougeron D., Gensolen F., Godiot S., Menouni M., Pangaud P., Rozanov A., Wang A., Bomben M., Calderini G., Crescioli F., Dortz O.L., Marchiori G., Dzahini D., Rarbi F.E., Gaglione R., Gonella L., Hemperek T., Huegging F., Karagounis M., Kishishita T., Krueger H., Rymaszewski P., Wermes N., Ciciriello F., Corsi F., Marzocca C., Robertis G.D., Loddo F., Licciulli F., Andreazza A., Liberali V., Shojaii S., Stabile A., Bagatin M., Bisello D., Mattiazzo S., Ding L., Gerardin S., Giubilato P., Neviani A., Paccagnella A., Vogrig D., Wyss J., Bacchetta N., Canio F.D., Gaioni L.,

Nodari B., Manghisoni M., Re V., Traversi G., Comotti D., Ratti L., Vacchi C., Beccherle R., Bellazzini R., Magazzu G., Minuti M., Morsani F., Palla F., Poulios S., Fanucci L., Rizzi A., Saponara S., Androsov K., Bilei G.M., Menichelli M., Conti E., Marconi S., Passeri D., Placidi P., Casa G.D., Mazza G., Rivetti A., Rolo M.D.D.R., Monteil E., Pacher L., Gajanana D., Gromov V., Hessey N., Kluit R., Zivkovic V., Havranek M., Janoska Z., Marcisovsky M., Neue G., Tomasek L., Kafka V., Sicho P., Vrba V., Vila I., Lopez-Morillo E., Aguirre M.A., Palomo F.R., Muñoz F., Abbaneo D., Christiansen J., Dannheim D., Dobos D., Linssen L., Pernegger H., Valerio P., Tehrani N.A., Bell S., Prydderch M.L., Thomas S., Christian D.C., Fahim F., Hoff J., Lipton R., Liu T., Zimmerman T., Garcia-Sciveres M., Gnani D., Mekkaoui A., Gorelov I., Hoeferkamp M., Seidel S., Toms K., Witt J.N.D., Grillo A., Paternò A.,"Recent progress of RD53 Collaboration towards next generation Pixel Read-Out Chip for HL-LHC",2016,"Journal of Instrumentation","11","12", C12058,"","",,"10.1088/1748-0221/11/12/C12058","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85008196553&doi=10.1088%2f1748-0221%2f11%2f12%2fC12058&partnerID=40&md5=0da970de1ee7cca184a763ca8634b4d9"

28. Andreou C.M., Javanainen A., Rominski A., Virtanen A., Liberali V., Calligaro C., Prokofiev A.V., Gerardin S., Bagatin M., Paccagnella A., Gonzalez-Castano D.M., Gomez F., Nahmad D., Georgiou J.,"Single Event Transients and Pulse Quenching Effects in Bandgap Reference Topologies for Space Applications",2016,"IEEE Transactions on Nuclear Science","63","6", 7572195,"2950","2961",,"10.1109/TNS.2016.2611639","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85012937717&doi=10.1109%2fTNS.2016.2611639&partnerID=40&md5=bc776097fd03b196a0f5df3869acb6f0"
29. Rosati G., Scaramuzza M., Pasqualotto E., De Toni A., Reggiani C., Paccagnella A.,"Modeling of SAM impedance onto gold and silver thin-film mass-produced electrodes and their use for optimization of lactic acid detection",2016,"IEEE Transactions on Nanobioscience","15","7", 7587410,"756","764",,"10.1109/TNB.2016.2616194","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85008440114&doi=10.1109%2fTNB.2016.2616194&partnerID=40&md5=ddfb0b0b23e975555c98c81a0b43c960"
30. Bagatin M., Gerardin S., Paccagnella A., Visconti A., Beltrami S., Bertuccio M., Ishida K., Frost C.D., Hillier A., Ferlet-Cavrois V.,"Muon-induced soft errors in 16-nm NAND flash memories",2016,"IEEE International Reliability Physics Symposium Proceedings","2016-September",, 7574552,"5C11","5C15",,"10.1109/IRPS.2016.7574552","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84990950511&doi=10.1109%2fIRPS.2016.7574552&partnerID=40&md5=4e6b5a62c04f02fd364657ea3e0a17c9"
31. Ding L., Gerardin S., Bagatin M., Bisello D., Mattiazzo S., Paccagnella A.,"Radiation tolerance study of a commercial 65 nm CMOS technology for high energy physics applications",2016,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","831",,,"265","268",,"10.1016/j.nima.2016.03.096","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84962473521&doi=10.1016%2fj.nima.2016.03.096&partnerID=40&md5=6cca280750ee4643212e9f45fbd34fd0"
32. Ding L., Gerardin S., Bagatin M., Bisello D., Mattiazzo S., Paccagnella A.,"Comparison of radiation degradation induced by x-ray and 3-MeV protons in 65-nm CMOS transistors",2016,"Chinese Physics B","25","9", 096110,"","",,"10.1088/1674-1056/25/9/096110","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

84988358664&doi=10.1088%2f1674-1056%2f25%2f9%2f096110&partnerID=40&md5=b3ebff675133ed3220596d8b604eaec7"

33. Ding L., Gnani E., Gerardin S., Bagatin M., Driussi F., Selmi L., Le Royer C., Paccagnella A.,"Impact of bias conditions on electrical stress and ionizing radiation effects in Si-based TFETs",2016,"Solid-State Electronics","115",,,"146","151",,"10.1016/j.sse.2015.09.003","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84948093205&doi=10.1016%2fj.sse.2015.09.003&partnerID=40&md5=f7f72d2677a8d3fe68ab2e9c748c0f81"
34. Gaioni L., De Canio F., Nodari B., Manghisoni M., Re V., Traversi G., Barbero M.B., Fougeron D., Gensolen F., Godiot S., Menouni M., Pangaud P., Rozanov A., Wang A., Bomben M., Calderini G., Crescioli F., Le Dortz O., Marchiori G., Dzahini D., Rarbi F.E., Gaglione R., Gonella L., Hemperek T., Huegging F., Karagounis M., Kishishita T., Krueger H., Rymaszewski P., Wermes N., Ciciriello F., Corsi F., Marzocca C., De Robertis G., Loddo F., Licciulli F., Andreazza A., Liberali V., Shojaii S., Stabile A., Bagatin M., Bisello D., Mattiazzo S., Ding L., Gerardin S., Giubilato P., Neviani A., Paccagnella A., Vogrig D., Wyss J., Bacchetta N., Della Casa G., Demaria N., Mazza G., Rivetti A., Da Rocha Rolo M.D., Comotti D., Ratti L., Vacchi C., Beccherle R., Bellazzini R., Magazzu G., Minuti M., Morsani F., Palla F., Poulios S., Fanucci L., Rizzi A., Saponara S., Androsov K., Bilei G.M., Menichelli M., Conti E., Marconi S., Passeri D., Placidi P., Monteil E., Pacher L., Paternò A., Gajanana D., Gromov V., Hessey N., Kluit R., Zivkovic V., Havranek M., Janoska Z., Marcisovsky M., Neue G., Tomasek L., Kafka V., Sicho P., Vrba V., Vila I., Lopez-Morillo E., Aguirre M.A., Palomo F.R., Muñoz F., Abbaneo D., Christiansen J., Dannheim D., Dobos D., Linssen L., Pernegger H., Valerio P., Alipour Tehrani N., Bell S., Prydderch M.L., Thomas S., Christian D.C., Fahim F., Hoff J., Lipton R., Liu T., Zimmerman T., Garcia-Sciveres M., Gnani D., Mekkaoui A., Gorelov I., Hoeferkamp M., Seidel S., Toms K., De Witt J.N., Grillo A.,"Design of analog front-ends for the RD53 demonstrator chip",2016,"Proceedings of Science","287",,,"","",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-85040911532&partnerID=40&md5=105d4e1563da40140d539aca1bab8203"
35. Marcello G., Mura G., Vanzi M., Bagatin M., Gerardin S., Paccagnella A.,"Proton irradiation effects on commercial laser diodes",2015,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS","2015-December",, 7365649,"","",,"10.1109/RADECS.2015.7365649","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84973352392&doi=10.1109%2fRADECS.2015.7365649&partnerID=40&md5=c3a2f217c4940402469e76b4e2bcbb7f"
36. Ding L., Gerardin S., Bagatin M., Mattiazzo S., Bisello D., Paccagnella A.,"Radiation vulnerability in 65 nm CMOS I/O transistors after exposure to grad dose",2015,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS","2015-December",, 7365655,"","",,"10.1109/RADECS.2015.7365655","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84973334335&doi=10.1109%2fRADECS.2015.7365655&partnerID=40&md5=da28e795df0bf532449fd61f22cf2753"
37. Paccagnella A.,"2015 IEEE Nuclear and Space Radiation Effects Conference Awards Comments by the Chairman",2015,"IEEE Transactions on Nuclear Science","62","6", 7348912,"2381","2382",,"10.1109/TNS.2015.2502499","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84961807612&doi=10.1109%2fTNS.2015.2502499&partnerID=40&md5=6070034409752bec4b037a72bf5e56a5"
38. Gerardin S., Bagatin M., Bertoldo A., Paccagnella A., Ferlet-Cavrois V.,"Sample-to-Sample Variability of Floating Gate Errors Due to Total Ionizing Dose",2015,"IEEE Transactions on Nuclear

Science","62","6", 7348755,"2511","2516",,"10.1109/TNS.2015.2498520","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84961822008&doi=10.1109%2fTNS.2015.2498520&partnerID=40&md5=d4980a7c5414014cbab1fbb6fe5c1e97"

39. Faccio F., Michelis S., Cornale D., Paccagnella A., Gerardin S.,"Radiation-Induced Short Channel (RISCE) and Narrow Channel (RINCE) Effects in 65 and 130 nm MOSFETs",2015,"IEEE Transactions on Nuclear Science","62","6", 7348757,"2933","2940",,"10.1109/TNS.2015.2492778","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84961777284&doi=10.1109%2fTNS.2015.2492778&partnerID=40&md5=58b1693f23aec909b960e24187033956"
40. DIng L., Gerardin S., Bagatin M., Mattiazzo S., Bisello D., Paccagnella A.,"Drain Current Collapse in 65 nm pMOS Transistors after Exposure to Grad Dose",2015,"IEEE Transactions on Nuclear Science","62","6", 7347478,"2899","2905",,"10.1109/TNS.2015.2499255","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84949870815&doi=10.1109%2fTNS.2015.2499255&partnerID=40&md5=7c99afd2d27bff3e8491fa1b32974b16"
41. Bagatin M., Gerardin S., Paccagnella A., Visconti A., Bonanomi M., Chiavarone L., Calabrese M., Ferlet-Cavrois V.,"Sensitive Volume and Extreme Shifts in Floating Gate Cells Irradiated with Heavy Ions",2015,"IEEE Transactions on Nuclear Science","62","6", 7348947,"2815","2821",,"10.1109/TNS.2015.2498403","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84961854571&doi=10.1109%2fTNS.2015.2498403&partnerID=40&md5=cea2d18ca09c03f0b87f1d343c28b76f"
42. Gerardin S., Bagatin M., Cornale D., DIng L., Mattiazzo S., Paccagnella A., Faccio F., Michelis S.,"Enhancement of Transistor-to-Transistor Variability Due to Total Dose Effects in 65-nm MOSFETs",2015,"IEEE Transactions on Nuclear Science","62","6", 7348776,"2398","2403",,"10.1109/TNS.2015.2498539","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84961775211&doi=10.1109%2fTNS.2015.2498539&partnerID=40&md5=fbb4b5d3ea55051f3be151be957d060f"
43. Bagatin M., Gerardin S., Paccagnella A., Sellier C., Wang P.X., Ferlet-Cavrios V., Poivey C.,"SEE tests of the NAND flash radiation tolerant intelligent memory stack",2015,"IEEE Radiation Effects Data Workshop","2015-November",, 7336732,"","",,"10.1109/REDW.2015.7336732","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84958652586&doi=10.1109%2fREDW.2015.7336732&partnerID=40&md5=7deabcd324943144e64c8b8a19bc6c45"
44. Ding L., Gerardin S., Bagatin M., Bisello D., Mattiazzo S., Paccagnella A.,"Investigation of total ionizing dose effect and displacement damage in 65 nm CMOS transistors exposed to 3 MeV protons",2015,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","796",, 57588,"104","107",,"10.1016/j.nima.2015.03.021","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84939778200&doi=10.1016%2fj.nima.2015.03.021&partnerID=40&md5=42516f83b61cc98dcfff760fb1020bc6"

45. Rossetto I., Rampazzo F., Gerardin S., Meneghini M., Bagatin M., Zanandrea A., Dua C., Di Forte-Poisson M.-A., Aubry R., Oualli M., Delage S.L., Paccagnella A., Meneghesso G., Zanoni E.,"Impact of proton fluence on DC and trapping characteristics in InAlN/GaN HEMTs",2015,"Solid-State Electronics","113",, 6802,"15","21",,"10.1016/j.sse.2015.05.013","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84937253654&doi=10.1016%2fj.sse.2015.05.013&partnerID=40&md5=2abe9e76715bf505c4b6beef42d6afbb"
46. Rossi D., Omaña M., Metra C., Paccagnella A.,"Impact of Bias Temperature Instability on Soft Error Susceptibility",2015,"IEEE Transactions on Very Large Scale Integration (VLSI) Systems","23","4", 6814927,"743","751",,"10.1109/TVLSI.2014.2320307","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85027920474&doi=10.1109%2fTVLSI.2014.2320307&partnerID=40&md5=171244f44bdfa3bbeb8830a808aeae94"
47. Zuppella P., Pasqualotto E., Pasqualotto E., Zuccon S., Gerlin F., Corso A.J., Scaramuzza M., De Toni A., De Toni A., Paccagnella A., Pelizzo M.G.,"Palladium on plastic substrates for plasmonic devices",2015,"Sensors (Switzerland)","15","1",,"1138","1147",,"10.3390/s150101138","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84920997372&doi=10.3390%2fs150101138&partnerID=40&md5=f079a2b1c4f2ca8a2afc0f2a201831cd"
48. Perino M., Pasqualotto E., Scaramuzza M., De Toni A., Paccagnella A.,"Enhancement and control of surface plasmon resonance sensitivity using grating in conical mounting configuration",2015,"Optics Letters","40","2",,"221","224",,"10.1364/OL.40.000221","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84924272818&doi=10.1364%2fOL.40.000221&partnerID=40&md5=e0eddb9735c89259cb184aa4c86cbf5b"
49. Perino M., Scaramuzza M., De Toni A., Paccagnella A., Rosati G., Pasqualotto E.,"Comparative study of two measurement/modeling techniques for biodevices functionalization assessment in agri-food applications",2015,"Proceedings of the 2015 18th AISEM Annual Conference, AISEM 2015",,, 7066848,"","",,"10.1109/AISEM.2015.7066848","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84937149219&doi=10.1109%2fAISEM.2015.7066848&partnerID=40&md5=0c5fd5ee8854b62582cdabda25c774a1"
50. Ding L., Gerardin S., Paccagnella A., Gnani E., Bagatin M., Driussi F., Selmi L., Le Royer C.,"Effects of electrical stress and ionizing radiation on Si-based TFETs",2015,"EUROSOI-ULIS 2015 - 2015 Joint International EUROSOI Workshop and International Conference on Ultimate Integration on Silicon",,, 7063792,"137","140",,"10.1109/ULIS.2015.7063792","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84926482053&doi=10.1109%2fULIS.2015.7063792&partnerID=40&md5=42b1611d7fb1cc5813f6544faccffe17"
51. Ding L., Gnani E., Gerardin S., Bagatin M., Driussi F., Palestri P., Selmi L., Royer C.L., Paccagnella A.,"Investigation of hot carrier stress and constant voltage stress in high-κ Si-based TFETs",2015,"IEEE Transactions on Device and Materials Reliability","15","2", 7086030,"236","241",,"10.1109/TDMR.2015.2423095","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

84941625386&doi=10.1109%2fTDMR.2015.2423095&partnerID=40&md5=c6fb348dd35bf2ca32fae48625274d91"

52. Andreou C.M., Paccagnella A., Gonzalez-Castano D.M., Gomez F., Liberali V., Prokofiev A.V., Calligaro C., Javanainen A., Virtanen A., Nahmad D., Georgiou J.,"A subthreshold, low-power, RHBD reference circuit, for earth observation and communication satellites",2015,"Proceedings - IEEE International Symposium on Circuits and Systems","2015-July",, 7169129,"2245","2248",,"10.1109/ISCAS.2015.7169129","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84946235250&doi=10.1109%2fISCAS.2015.7169129&partnerID=40&md5=c52331abf7f6b83a9c3d396bf436e3f8"
53. Demaria N., Dellacasa G., Mazza G., Rivetti A., Da Rocha Rolo M.D., Monteil E., Pacher L., Ciciriello F., Corsi F., Marzocca C., De Roberts G., Loddo F., Tamma C., Bagatin M., Bisello D., Gerardin S., Mattiazzo S., Ding L., Giubilato P., Paccagnella A., De Canio F., Gaioni L., Manghisoni M., Re V., Traversi G., Riceputi E., Ratti L., Vacchi C., Beccherle R., Magazzu G., Minuti M., Morsani F., Palla F., Liberali V., Shojaii S., Stabile A., Bilei G.M., Menichelli M., Conti E., Marconi S., Passen D., Placidi P.,"CHIPIX65: Developments on a new generation pixel readout ASIC in CMOS 65 nm for HEP experiments",2015,"Proceedings - 2015 6th IEEE International Workshop on Advances in Sensors and Interfaces, IWASI 2015",,, 7184947,"49","54",,"10.1109/IWASI.2015.7184947","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84944184326&doi=10.1109%2fIWASI.2015.7184947&partnerID=40&md5=2fa253aa4fea8780376cc1760706f688"
54. Gerardin S., Bagatin M., Paccagnella A., Visconti A., Bonanomi M., Beltrami S., Ferlet-Cavrois V.,"Upsets in phase change memories due to high-let heavy ions impinging at an angle",2014,"IEEE Transactions on Nuclear Science","61","6", 6966802,"3491","3496",,"10.1109/TNS.2014.2367655","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84919922263&doi=10.1109%2fTNS.2014.2367655&partnerID=40&md5=5115735d8a1e42c0284f90b0c95118e5"
55. Bagatin M., Gerardin S., Ferrarese F., Paccagnella A., Ferlet-Cavrois V., Costantino A., Muschitiello M., Visconti A., Wang P.-X.,"Sample-to-sample variability and bit errors induced by total dose in advanced NAND flash memories",2014,"IEEE Transactions on Nuclear Science","61","6", 6966799,"2889","2895",,"10.1109/TNS.2014.2367813","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84919950447&doi=10.1109%2fTNS.2014.2367813&partnerID=40&md5=0eb03fd92225d3f17e870a0d1e8afd30"
56. Ding L., Gnani E., Gerardin S., Bagatin M., Driussi F., Palestri P., Selmi L., Royer C.L., Paccagnella A.,"Total ionizing dose effects in si-based tunnel FETs",2014,"IEEE Transactions on Nuclear Science","61","6", 6966809,"2874","2880",,"10.1109/TNS.2014.2367548","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84919919980&doi=10.1109%2fTNS.2014.2367548&partnerID=40&md5=822355a741c75567e8bd6e04dcf4cd4e"
57. De Santi C., Meneghini M., Trivellin N., Gerardin S., Bagatin M., Paccagnella A., Meneghesso G., Zanoni E.,"Recoverable degradation of blue InGaN-based light emitting diodes submitted to 3 MeV proton irradiation",2014,"Applied Physics Letters","105","21", 213506,"","",,"10.1063/1.4902870","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84912121308&doi=10.1063%2f1.4902870&partnerID=40&md5=2b09c914e603bfbbd8bb7a91183c39aa"

58. Perino M., Pasqualotto E., De Toni A., Garoli D., Scaramuzza M., Zilio P., Ongarello T., Paccagnella A., Romanato F.,"Development of a complete plasmonic grating-based sensor and its application for self-assembled monolayer detection",2014,"Applied Optics","53","26",,"5969","5976",,"10.1364/AO.53.005969","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84907583593&doi=10.1364%2fAO.53.005969&partnerID=40&md5=9fda836dc4865308642a05dbe3a0eafd"
59. Abbate C., Alderighi M., Baccaro S., Busatto G., Citterio M., Cova P., Delmonte N., Luca Vde., Fiore S., Gerardin S., Ghisolfi E., Giuliani F., Iannuzzo F., Lanza A., Latorre S., Lazzaroni M., Meneghesso G., Paccagnella A., Rampazzo F., Riva M., Sanseverino A., Silvestri R., Spiazzi G., Velardi F., Zanoni E.,"Developments on DC/DC converters for the LHC experiment upgrades",2014,"Journal of Instrumentation","9","2", C02017,"","",,"10.1088/1748-0221/9/02/C02017","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84894683830&doi=10.1088%2f1748-0221%2f9%2f02%2fC02017&partnerID=40&md5=a9a13f5b05462d4898d3af922a5fb650"
60. Ding L., Gnani E., Gerardin S., Bagatin M., Royer C.L., Paccagnella A.,"Effects of bias on the radiation responses of Si-based TFETs",2014,"Proceedings - 2014 IEEE 12th International Conference on Solid-State and Integrated Circuit Technology, ICSICT 2014",,, 7021289,"","",,"10.1109/ICSICT.2014.7021289","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84946689101&doi=10.1109%2fICSICT.2014.7021289&partnerID=40&md5=4763af13780a8faeb859834534e79258"
61. Perino M., Pasqualotto E., Scaramuzza M., De Toni A., Paccagnella A.,"Characterization of Grating Coupled Surface Plasmon Polaritons Using Diffracted Rays Transmittance",2014,"Plasmonics","9","5",,"1103","1111",,"10.1007/s11468-014-9720-5","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84924227984&doi=10.1007%2fs11468-014-9720-5&partnerID=40&md5=533cc3daafd1ff4d7f838a18850fe280"
62. Gerardin S., Bagatin M., Paccagnella A., Ferlet-Cavrois V., Visconti A., Frost C.D.,"Neutron and alpha single event upsets in advanced NAND flash memories",2014,"IEEE Transactions on Nuclear Science","61","4", 6866248,"1799","1805",,"10.1109/TNS.2014.2328097","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84906787710&doi=10.1109%2fTNS.2014.2328097&partnerID=40&md5=dbff5e83cf4e997a00311ba9eec202a0"
63. Bagatin M., Gerardin S., Paccagnella A., Visconti A., Chiavarone L., Calabrese M., Frost C.D.,"Sensitivity of NOR flash memories to wide-energy spectrum neutrons during accelerated tests",2014,"IEEE International Reliability Physics Symposium Proceedings",,, 6861094,"5F.3.1","5F.3.6",,"10.1109/IRPS.2014.6861094","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84905671287&doi=10.1109%2fIRPS.2014.6861094&partnerID=40&md5=5f6ee141b12b4a7363f607e02614e164"
64. Gerardin S., Bagatin M., Paccagnella A., Visconti A., Bonanomi M., Beltrami S., Frost C., Ferlet-Cavrois V.,"Heavy-ion induced single event upsets in phase-change memories",2014,"IEEE International Reliability Physics Symposium Proceedings",,, 6860586,"2B.3.1","2B.3.6",,"10.1109/IRPS.2014.6860586","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84905648447&doi=10.1109%2fIRPS.2014.6860586&partnerID=40&md5=c9bf4fcd75a7d5576d741cf0c8824646"

65. Puzyrev Y., Mukherjee S., Chen J., Roy T., Silvestri M., Schrimpf R.D., Fleetwood D.M., Singh J., Hinckley J.M., Paccagnella A., Pantelides S.T.,"Gate bias dependence of defect-mediated hot-carrier degradation in GaN HEMTs",2014,"IEEE Transactions on Electron Devices","61","5", 6767107,"1316","1320",,"10.1109/TED.2014.2309278","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84899900786&doi=10.1109%2fTED.2014.2309278&partnerID=40&md5=6e5eb94c6f54bd10943bb1c030b82b39"
66. Ding L., Guo H., Chen W., Yao Z., Yan Y., Chen D., Paccagnella A., Gerardin S., Bagatin M., Chen L., Sun H., Fan R.,"Analysis of TID failure modes in SRAM-based FPGA under gamma-ray and focused synchrotron x-ray irradiation",2014,"IEEE Transactions on Nuclear Science","61","4", 6832651,"1777","1784",,"10.1109/TNS.2014.2314530","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84906787885&doi=10.1109%2fTNS.2014.2314530&partnerID=40&md5=ee5964998401f14222080806527a4cbc"
67. Rossetto I., Rampazzo F., Gerardin S., Meneghini M., Bagatin M., Zanandrea A., Paccagnella A., Meneghesso G., Zanoni E., Dua C., Di Forte-Poisson M.-A., Aubry R., Oualli M., Delage S.L.,"Degradation of dc and pulsed characteristics of InAlN/GaN HEMTs under different proton fluences",2014,"European Solid-State Device Research Conference",,, 6948840,"381","384",,"10.1109/ESSDERC.2014.6948840","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84911982228&doi=10.1109%2fESSDERC.2014.6948840&partnerID=40&md5=43342fddd746841a813ff59bf130ab97"
68. Demaria N., Ciciriello F., Corsi F., Marzocca C., De Robertis G., Loddo F., Tamma C., Liberali V., Shojaii S., Stabile A., Bagatin M., Bisello D., Gerardin S., Mattiazzo S., Ding L., Giubilato P., Paccagnella A., De Canio F., Gaioni L., Manghisoni M., Re V., Traversi G., Riceputi E., Ratti L., Vacchi C., Beccherle R., Magazzu G., Morsani F., Palla F., Bilei G.M., Menichelli M., Conti E., Marconi S., Passeri D., Placidi P., Dellacasa G., Mazza G., Rivetti A., Da Rocha Rolo M.D., Monteil E., Pacher L.,"RD53 collaboration and CHIPIX65 project for the development of an innovative pixel front end chip for HL-LHC",2014,"Proceedings of Science","2014-March",,,"","",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-85051971047&partnerID=40&md5=fa36d015ad4e40662bfa7f057f93fe7d"
69. Valerio P., Barbero M.B., Fougeron D., Gensolen F., Godiot S., Menouni M., Pangaud P., Rozanov A., Wang A., Bomben M., Calderini G., Crescioli F., Genat J.-F., Le Dortz O., Marchiori G., Dzahini D., Rarbi F.E., Gaglione R., Gonella L., Hemperek T., Huegging F., Karagounis M., Kishishita T., Krueger H., Rymaszewski P., Wermes N., Ciciriello F., Corsi F., Licciulli F., Marzocca C., De Robertis G., Loddo F., Tamma C., Andreazza A., Liberali V., Shojaii S., Stabile A., Bagatin M., Bisello D., Mattiazzo S., Ding L., Gerardin S., Giubilato P., Neviani A., Paccagnella A., Vogrig D., Wyss J., Bacchetta N., De Canio F., Gaioni L., Nodari B., Manghisoni M., Re V., Traversi G., Comotti D., Ratti L., Vacchi C., Beccherle R., Bellazzini R., Magazzu G., Minuti M., Morsani F., Palla F., Fanucci L., Rizzi A., Saponara S., Androsov K., Bilei G.M., Menichelli M., Conti E., Marconi S., Passeri D., Placidi P., Della Casa G., Demaria N., Mazza G., Rivetti A., Da Rocha Rolo M.D., Monteil E., Pacher L., Gajanana D., Gromov V., Hessey N., Kluit R., Zivkovic V., Havranek M., Janoska Z., Marcisovsky M., Neue G., Tomasek L., Kafka V., Sicho P., Vrba V., Vila I., Aguirre M.A., Muñoz F., Palomo F.R., Abbaneo D., Christiansen J., Dannheim D., Dobos D., Linssen L., Pernegger H., Alipour Tehrani N., Bell S., Prydderch M.L., Thomas S., Christian D.C., Deptuch G., Fahim F., Hoff J., Lipton R., Liu T., Zimmerman T., Garcia-Sciveres M., Gnani D., Mekkaoui A., Gorelov I., Hoeferkamp M., Seidel S., Toms K., De Witt J.N., Grillo A.,"65 nm technology for HEP: Status and perspective",2014,"Proceedings of Science","15-19-September-2014",, 043,"","",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-84999274214&partnerID=40&md5=2cd7af49ba68546d82221174e28e55e0"

70. Bagatin M., Gerardin S., Paccagnella A., Ferlet-Cavrois V., Visconti A., Gorini G., Andreani C., Frost C.D.,"Neutron and alpha ser in advanced NAND Flash memories",2013,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 6937440,"","",,"10.1109/RADECS.2013.6937440","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84949924457&doi=10.1109%2fRADECS.2013.6937440&partnerID=40&md5=79f8ed9a17185e514f75dd5bf9f532ef"
71. Ding L.-L., Guo H.-X., Chen W., Yao Z.-B., Yan Y.-H., Chen D.-L., Paccagnella A., Gerardin S., Bartagin M., Chen L., Sun H.-B., Fan R.-Y.,"Analysis of TID failure modes in SRAM-based FPGA based on gamma-ray and synchrotron X-ray irradiation",2013,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 6937434,"","",,"10.1109/RADECS.2013.6937434","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84949924757&doi=10.1109%2fRADECS.2013.6937434&partnerID=40&md5=fbbe0c99eb156594c9f470d98117f6e4"
72. Bagatin M., Gerardin S., Paccagnella A., Ferlet-Cavrois V.,"Single and multiple cell upsets in 25-nm NAND flash memories",2013,"IEEE Transactions on Nuclear Science","60","4", 6575174,"2675","2681",,"10.1109/TNS.2013.2273436","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84883135082&doi=10.1109%2fTNS.2013.2273436&partnerID=40&md5=40891de6a02e9c34d1f72fea988862da"
73. Tavani M., Argan A., Paccagnella A., Pesoli A., Palma F., Gerardin S., Bagatin M., Trois A., Picozza P., Benvenuti P., Flamini E., Marisaldi M., Pittori C., Giommi P.,"Possible effects on avionics induced by terrestrial gamma-ray flashes",2013,"Natural Hazards and Earth System Science","13","4",,"1127","1133",,"10.5194/nhess-13-1127-2013","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84879223725&doi=10.5194%2fnhess-13-1127-2013&partnerID=40&md5=649842d85c3f1f3ad44f09fcdfda16d8"
74. Gerardin S., Bagatin M., Paccagnella A., Grurmann K., Gliem F., Oldham T.R., Irom F., Nguyen D.N.,"Radiation effects in flash memories",2013,"IEEE Transactions on Nuclear Science","60","3", 6515709,"1953","1969",,"10.1109/TNS.2013.2254497","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84879234076&doi=10.1109%2fTNS.2013.2254497&partnerID=40&md5=d499619499c236dfd6dc3d258c373552"
75. Bastani Y., Cortés-Peña A.Y., Wilson A.D., Gerardin S., Bagatin M., Paccagnella A., Bassiri-Gharb N.,"Effects of high energy x ray and proton irradiation on lead zirconate titanate thin films dielectric and piezoelectric response",2013,"Applied Physics Letters","102","19", 192906,"","",,"10.1063/1.4805045","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84877933301&doi=10.1063%2f1.4805045&partnerID=40&md5=b9c57ca7d281dd167138f74079ec3f4d"
76. Ferrario A., Scaramuzza M., Pasqualotto E., De Toni A., Paccagnella A.,"Coadsorption optimization of DNA in binary self-assembled monolayer on gold electrode for electrochemical detection of oligonucleotide sequences",2013,"Journal of Electroanalytical Chemistry","689",,,"57","62",,"10.1016/j.jelechem.2012.11.029","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84871757614&doi=10.1016%2fj.jelechem.2012.11.029&partnerID=40&md5=36f55912d3f173de44d2647a27540571"
77. Bagatin M., Gerardin S., Paccagnella A., Ferlet-Cavrois V., Schwank J.R., Shaneyfelt M.R., Visconti A.,"Proton-induced upsets in SLC and MLC nand flash memories",2013,"IEEE Transactions on

Nuclear Science","60","6", 6678662,"4130","4135",,"10.1109/TNS.2013.2290033","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84891558219&doi=10.1109%2fTNS.2013.2290033&partnerID=40&md5=2f559b71fd9969a12687e782660892e9"

78. Gerardin S., Bagatin M., Paccagnella A., Bisello D., Giubilato P., Mattiazzo S., Pantano D., Silvestrin L., Tessaro M., Wyss J., Ferlet-Cavrois V.,"Investigation of supply current spikes in flash memories using ion-electron emission microscopy",2013,"IEEE Transactions on Nuclear Science","60","6", 6678313,"4136","4141",,"10.1109/TNS.2013.2290012","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84891559272&doi=10.1109%2fTNS.2013.2290012&partnerID=40&md5=c4214d624fd952bcb1d34d0d4d78e5a5"
79. Abbate C., Alderighi M., Baccaro S., Busatto G., Citterio M., Cova P., Delmonte N., De Luca V., Fiore S., Gerardin S., Ghisolfi E., Giuliani F., Iannuzzo F., Lanza A., Latorre S., Lazzaroni M., Meneghesso G., Paccagnella A., Rampazzo F., Riva M., Sanseverino A., Silvestri R., Spiazzi G., Velardi F., Zanoni E.,"Radiation performance of new semiconductor power devices for the LHC experiment upgrades",2013,"Proceedings of Science","2013-July",,,"","",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-85052397228&partnerID=40&md5=8777e868008b3a84c4d693650b80a1e3"
80. Bagatin M., Gerardin S., Paccagnella A.,"Retention errors in 65-nm floating gate cells after exposure to heavy ions",2012,"IEEE Transactions on Nuclear Science","59","6", 6365389,"2785","2790",,"10.1109/TNS.2012.2222929","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84871362374&doi=10.1109%2fTNS.2012.2222929&partnerID=40&md5=914775b296bc547c95d9cf6cac823ce7"
81. Gerardin S., Bagatin M., Paccagnella A., Ferlet-Cavrois V.,"Degradation of sub 40-nm NAND flash memories under total dose irradiation",2012,"IEEE Transactions on Nuclear Science","59","6", 6365394,"2952","2958",,"10.1109/TNS.2012.2222928","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84871385043&doi=10.1109%2fTNS.2012.2222928&partnerID=40&md5=4058bfdc6371cc981812fe6d5d73bc82"
82. Bolchini C., Miele A., Sandionigi C., Ottavi M., Pontarelli S., Salsano A., Metra C., Omaña M., Rossi D., Reorda M.S., Sterpone L., Violante M., Gerardin S., Bagatin M., Paccagnella A.,"High-reliability fault tolerant digital systems in nanometric technologies: Characterization and design methodologies",2012,"Proceedings - IEEE International Symposium on Defect and Fault Tolerance in VLSI Systems",,, 6378211,"121","125",,"10.1109/DFT.2012.6378211","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84872297282&doi=10.1109%2fDFT.2012.6378211&partnerID=40&md5=177c8c26ee49754f66581bb06da7416c"
83. Alderighi M., Citterio M., Latorre S., Riva M., Cova P., Delmonte N., Lanza A., Bernardoni M., Menozzi R., Costabeber A., Paccagnella A., Sichirollo F., Spiazzi G., Stellini M., Tenti P., Baccaro S., Iannuzzo F., Sanseverino A., Busatto G., De Luca V.,"Power distribution architecture for high energy physic hostile environment",2012,"Astroparticle, Particle, Space Physics and Detectors for Physics Applications - Proceedings of the 13th ICATPP Conference",,,,"890","894",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-84886882653&partnerID=40&md5=2ada1a38da8df15922b7d2c7585b828d"
84. Bagatin M., Gerardin S., Paccagnella A., Ferlet-Cavrois V.,"Alpha-induced soft errors in floating gate flash memories",2012,"IEEE International Reliability Physics Symposium Proceedings",,,

6241811,"3C.2.1","3C.2.7",,"10.1109/IRPS.2012.6241811","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84866617462&doi=10.1109%2fIRPS.2012.6241811&partnerID=40&md5=b94ace32bb985cbcb4c9557922e98fb9"

85. Bagatin M., Coniglio A., D'Arienzo M., De Lorenzi A., Gerardin S., Paccagnella A., Pasqualotto R., Peruzzo S., Sandri S.,"Radiation environment in the ITER neutral beam injector prototype",2012,"IEEE Transactions on Nuclear Science","59","4 PART 1", 6172630,"1099","1104",,"10.1109/TNS.2012.2187461","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84865360862&doi=10.1109%2fTNS.2012.2187461&partnerID=40&md5=6f8b72d61d698fb011cda66df38d5907"
86. Gerardin S., Bagatin M., Ferrario A., Paccagnella A., Visconti A., Beltrami S., Andreani C., Gorini G., Frost C.D.,"Neutron-induced upsets in NAND floating gate memories",2012,"IEEE Transactions on Device and Materials Reliability","12","2", 6176212,"437","444",,"10.1109/TDMR.2012.2192440","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84862007030&doi=10.1109%2fTDMR.2012.2192440&partnerID=40&md5=9400f8fc366d668435a59ea66ce42ae6"
87. Scaramuzza M., Ferrario A., Pasqualotto E., Rosati G., De Toni A., Quarta M., Paccagnella A., Reggiani C.,"Low-cost enzyme-based biosensor for lactic acid amperometric detection: Electrical modeling and validation for clinical and food processing applications",2012,"BIODEVICES 2012 - Proceedings of the International Conference on Biomedical Electronics and Devices",,,,"380","383",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-84861983993&partnerID=40&md5=d724560c5d13a7aeafeb6c47c0cc65ff"
88. Gerardin S., Bagatin M., Paccagnella A., Schwank J.R., Shaneyfelt M.R., Blackmore E.W.,"Proton-induced upsets in 41-nm NAND floating gate cells",2012,"IEEE Transactions on Nuclear Science","59","4 PART 1", 6194356,"838","844",,"10.1109/TNS.2012.2192750","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84865392671&doi=10.1109%2fTNS.2012.2192750&partnerID=40&md5=4f570d359175bb7ececbd9a9d948a076"
89. Alderighi M., Citterio M., Riva M., Latorre S., Costabeber A., Paccagnella A., Sichirollo F., Spiazzi G., Stellini M., Tenti P., Cova P., Delmonte N., Lanza A., Bernardoni M., Menozzi R., Baccaro S., Iannuzzo F., Sanseverino A., Busatto G., De Luca V., Velardi F.,"Power converters for future LHC experiments",2012,"Journal of Instrumentation","7","3", C03012,"","",,"10.1088/1748-0221/7/03/C03012","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84858791721&doi=10.1088%2f1748-0221%2f7%2f03%2fC03012&partnerID=40&md5=ff84c3f6c5a0d8909d936751cc7bacd1"
90. Bagatin M., Gerardin S., Paccagnella A., Andreani C., Gorini G., Frost C.D.,"Temperature dependence of neutron-induced soft errors in SRAMs",2012,"Microelectronics Reliability","52","1",,"289","293",,"10.1016/j.microrel.2011.08.011","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84155167175&doi=10.1016%2fj.microrel.2011.08.011&partnerID=40&md5=c9c3ad5bde7ad4e8b1a7ff30d71d1129"
91. Rossi D., Omaña M., Metra C., Paccagnella A.,"Impact of aging phenomena on soft error susceptibility",2011,"Proceedings - IEEE International Symposium on Defect and Fault Tolerance in VLSI Systems",,, 6104505,"18","24",,"10.1109/DFT.2011.45","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

84855803291&doi=10.1109%2fDFT.2011.45&partnerID=40&md5=9f3ca00ac35c8bdad319dc6d1762636e"

92. Gerardin S., Bagatin M., Paccagnella A., Schwank J.R., Shaneyfelt M.R., Blackmore E.W.,"Proton-induced upsets in 41-nm NAND floating gate cells",2011,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,,6131302,"191","194",,"10.1109/RADECS.2011.6131302","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84860202029&doi=10.1109%2fRADECS.2011.6131302&partnerID=40&md5=8914903ad410af6ddb1d5e14a2ae80be"
93. Gerardin S., Bagatin M., Paccagnella A., Visconti A., Bonanomi M., Beltrami S.,"Angular dependence of heavy-ion induced errors in floating gate memories",2011,"IEEE Transactions on Nuclear Science","58","6 PART 1",6078445,"2621","2627",,"10.1109/TNS.2011.2171717","https://www.scopus.com/inward/record.uri?eid=2-s2.0-83855163501&doi=10.1109%2fTNS.2011.2171717&partnerID=40&md5=c31bfcf4c000034ac28ca1dcdbf1c9de"
94. Bagatin M., Gerardin S., Paccagnella A., Visconti A., Beltrami S., Bertuccio M., Czeppel L.T.,"Effects of total ionizing dose on the retention of 41-nm NAND flash cells",2011,"IEEE Transactions on Nuclear Science","58","6 PART 1",6078444,"2824","2829",,"10.1109/TNS.2011.2171505","https://www.scopus.com/inward/record.uri?eid=2-s2.0-83855163500&doi=10.1109%2fTNS.2011.2171505&partnerID=40&md5=c2484538c222ff0debabec06c98b2086"
95. Gerardin S., Bagatin M., Paccagnella A., Visconti A., Bonanomi M., Pellizzer F., Vela M., Ferlet-Cavrois V.,"Single event effects in 90-nm phase change memories",2011,"IEEE Transactions on Nuclear Science","58","6 PART 1",6068270,"2755","2760",,"10.1109/TNS.2011.2171719","https://www.scopus.com/inward/record.uri?eid=2-s2.0-83855165160&doi=10.1109%2fTNS.2011.2171719&partnerID=40&md5=8b3ce09d65dbdeb8689f6592f7f60139"
96. Bagatin M., Coniglio A., D'Arienzo M., De Lorenzi A., Gerardin S., Paccagnella A., Pasqualotto R., Peruzzo S., Sandri S.,"Radiation environment in the ITER neutral beam injector prototype",2011,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,,6131442,"595","598",,"10.1109/RADECS.2011.6131442","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84860173533&doi=10.1109%2fRADECS.2011.6131442&partnerID=40&md5=5be1781a2824a6723cfe489f941e8a36"
97. Sterpone L., Violante M., Panariti A., Bocquillon A., Miller F., Buard N., Manuzzato A., Gerardin S., Paccagnella A.,"Layout-aware multi-cell upsets effects analysis on TMR circuits implemented on SRAM-based fpgas",2011,"IEEE Transactions on Nuclear Science","58","5 PART 2",5991971,"2325","2332",,"10.1109/TNS.2011.2161887","https://www.scopus.com/inward/record.uri?eid=2-s2.0-80054077114&doi=10.1109%2fTNS.2011.2161887&partnerID=40&md5=58377b55c557eec5eb5593473da56c17"
98. Bagatin M., Coniglio A., D'Arienzo M., De Lorenzi A., Gerardin S., Paccagnella A., Pasqualotto R., Peruzzo S., Sandri S., Zaniol B.,"Ionizing radiation compatibility in the MITICA neutral beam prototype",2011,"Fusion Engineering and Design","86","6-8",,"1268","1272",,"10.1016/j.fusengdes.2011.02.021","https://www.scopus.com/inward/record.u

ri?eid=2-s2.0-80054052934&doi=10.1016%2fj.fusengdes.2011.02.021&partnerID=40&md5=410116ad8d6b2cc478e6ab0733e44364"

99. Ferrario A., Scaramuzza M., Pasqualotto E., De Toni A., Paccagnella A., Maschietto M., Vassanelli S.,"Electrochemical impedance spectroscopy study of the cells adhesion over microelectrodes array",2011,"2011 7th Conference on Ph.D. Research in Microelectronics and Electronics, PRIME 2011 - Conference Proceedings",,, 5966216,"57","60",,"10.1109/PRIME.2011.5966216","https://www.scopus.com/inward/record.uri?eid=2-s2.0-80052255831&doi=10.1109%2fPRIME.2011.5966216&partnerID=40&md5=ca9f3aa4111ceb0cdeac2da6dfe09496"
100. Gerardin S., Bagatin M., Paccagnella A., Visconti A., Beltrami S., Bertuccio M., Czeppel L.T.,"A study on the short- and long-term effects of X-ray exposure on NAND Flash memories",2011,"IEEE International Reliability Physics Symposium Proceedings",,, 5784572,"EX.1.1","EX.1.5",,"10.1109/IRPS.2011.5784572","https://www.scopus.com/inward/record.uri?eid=2-s2.0-79959300624&doi=10.1109%2fIRPS.2011.5784572&partnerID=40&md5=bf5496773561fcb408827c24da10d103"
101. Bagatin M., Gerardin S., Paccagnella A., Visconti A.,"Impact of technology scaling on the heavy-ion upset cross section of multi-level floating gate cells",2011,"IEEE Transactions on Nuclear Science","58","3 PART 2", 5740382,"969","974",,"10.1109/TNS.2011.2122268","https://www.scopus.com/inward/record.uri?eid=2-s2.0-79959379861&doi=10.1109%2fTNS.2011.2122268&partnerID=40&md5=4b642ea5f79cd05a84f44b1e01f09f1e"
102. Gerardin S., Bagatin M., Paccagnella A., Visconti A., Greco E.,"Heavy-ion induced threshold voltage shifts in sub 70-nm charge-trap memory cells",2011,"IEEE Transactions on Nuclear Science","58","3 PART 2", 5740623,"827","833",,"10.1109/TNS.2011.2122269","https://www.scopus.com/inward/record.uri?eid=2-s2.0-79959380269&doi=10.1109%2fTNS.2011.2122269&partnerID=40&md5=75705b89c9f8b837874dee96e39722f3"
103. Cellere G., Paccagnella A., Murat M., Barak J., Akkerman A., Harboe-Sorensen R., Virtanen A., Visconti A., Bonanomi M.,"Impact of time and space evolution of ion tracks in nonvolatile memory cells approaching nanoscale",2010,"Journal of Applied Physics","108","12", 124907,"","",,"10.1063/1.3514167","https://www.scopus.com/inward/record.uri?eid=2-s2.0-78650924728&doi=10.1063%2f1.3514167&partnerID=40&md5=34a9a848cd74a6d8155794679829e098"
104. Gerardin S., Paccagnella A.,"Present and future non-volatile memories for space",2010,"IEEE Transactions on Nuclear Science","57","6 PART 1", 5658042,"3016","3039",,"10.1109/TNS.2010.2084101","https://www.scopus.com/inward/record.uri?eid=2-s2.0-78650379799&doi=10.1109%2fTNS.2010.2084101&partnerID=40&md5=b214c73f2484aa11cd3927fd704edbb6"
105. Bagatin M., Cellere G., Gerardin S., Paccagnella A.,"Radiation effects on NAND flash memories",2010,"Inside NAND Flash Memories",,,,"537","571",,"10.1007/978-90-481-9431-5_19","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84892006156&doi=10.1007%2f978-90-481-9431-5_19&partnerID=40&md5=dcb83d4e768440a9b1fd5f7c344dde21"

106. Bagatin M., Gerardin S., Paccagnella A., Faccio F.,"Impact of NBTI aging on the single-event upset of SRAM cells",2010,"IEEE Transactions on Nuclear Science","57","6 PART 1", 5658057,"3245","3250",,"10.1109/TNS.2010.2084100","https://www.scopus.com/inward/record.uri?eid=2-s2.0-78650357472&doi=10.1109%2fTNS.2010.2084100&partnerID=40&md5=946dd680a4b46c3eb8805da833ef56a9"
107. Calligaro C., Liberali V., Stabile A., Bagatin M., Gerardin S., Paccagnella A.,"A multi-megarad, radiation hardened by design 512 kbit SRAM in CMOS technology",2010,"Proceedings of the International Conference on Microelectronics, ICM",,, 5696165,"375","378",,"10.1109/ICM.2010.5696165","https://www.scopus.com/inward/record.uri?eid=2-s2.0-79951704645&doi=10.1109%2fICM.2010.5696165&partnerID=40&md5=1dd8277079d8230ba1f220442d5f0ce6"
108. Bagatin M., Gerardin S., Paccagnella A., Cellere G., Visconti A., Bonanomi M.,"Increase in the heavy-ion upset cross section of floating gate cells previously exposed to TID",2010,"IEEE Transactions on Nuclear Science","57","6 PART 1", 5621940,"3407","3413",,"10.1109/TNS.2010.2073485","https://www.scopus.com/inward/record.uri?eid=2-s2.0-78650417571&doi=10.1109%2fTNS.2010.2073485&partnerID=40&md5=7d7c2921284872caecee8d2519c22d96"
109. Claeys C., Put S., Griffoni A., Cester A., Gerardin S., Meneghesso G., Paccagnella A., Simoen E.,"Impact of radiation on the operation and reliability of deep submicron CMOS technologies",2010,"ECS Transactions","27","1",,"39","46",,"10.1149/1.3360593","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84857383183&doi=10.1149%2f1.3360593&partnerID=40&md5=a2ed54d2ab3ee9c4b289b2704c18ac10"
110. Gerardin S., Bagatin M., Paccagnella A., Cellere G., Visconti A., Bonanomi M., Hjalmarsson A., Prokofiev A.V.,"Heavy-ion induced threshold voltage tails in floating gate arrays",2010,"IEEE Transactions on Nuclear Science","57","6 PART 1", 5658039,"3199","3205",,"10.1109/TNS.2010.2084592","https://www.scopus.com/inward/record.uri?eid=2-s2.0-78650406100&doi=10.1109%2fTNS.2010.2084592&partnerID=40&md5=d152d134aa6948989d0d88b62e1be92c"
111. Rech P., Grosso M., Melchiori F., Loparco D., Appello D., Dilillo L., Paccagnella A., Sonza Reorda M.,"Analysis of root causes of alpha sensitivity variations on microprocessors manufactured using different cell layouts",2010,"Proceedings of the 2010 IEEE 16th International On-Line Testing Symposium, IOLTS 2010",,, 5560236,"29","34",,"10.1109/IOLTS.2010.5560236","https://www.scopus.com/inward/record.uri?eid=2-s2.0-77958004796&doi=10.1109%2fIOLTS.2010.5560236&partnerID=40&md5=f53a1f9b3b1d7e6adc7d97017a07dde5"
112. Tazzoli A., Barbato M., Giliberto V., Monaco G., Gerardin S., Nicolosi P., Paccagnella A., Meneghesso G.,"Accelerated testing of RF-MEMS contact degradation through radiation sources",2010,"IEEE International Reliability Physics Symposium Proceedings",,, 5488823,"246","251",,"10.1109/IRPS.2010.5488823","https://www.scopus.com/inward/record.uri?eid=2-s2.0-77957897339&doi=10.1109%2fIRPS.2010.5488823&partnerID=40&md5=31d39b3b027c7d053f2989ae1b95fd13"

113. Gerardin S., Bagatin M., Paccagnella A., Cellere G., Visconti A., Beltrami S., Andreani C., Gorini G., Frost C.D.,"Scaling trends of neutron effects in MLC NAND Flash memories",2010,"IEEE International Reliability Physics Symposium Proceedings",,,5488797,"400","406",,"10.1109/IRPS.2010.5488797","https://www.scopus.com/inward/record.uri?eid=2-s2.0-77957917763&doi=10.1109%2fIRPS.2010.5488797&partnerID=40&md5=5603b291580c3f8f0512b5d4bae3d335"

114. Gerardin S., Bagatin M., Paccagnella A., Cellere G., Visconti A., Bonanomi M.,"Impact of total dose on heavy-ion upsets in floating gate arrays",2010,"Microelectronics Reliability","50","9-11",,"1837","1841",,"10.1016/j.microrel.2010.07.142","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84755161653&doi=10.1016%2fj.microrel.2010.07.142&partnerID=40&md5=997b016716b1f5138faceb2b2e894a42"

115. Bagatin M., Gerardin S., Paccagnella A., Cellere G., Irom F., Nguyen D.N.,"Destructive events in NAND Flash memories irradiated with heavy ions",2010,"Microelectronics Reliability","50","9-11",,"1832","1836",,"10.1016/j.microrel.2010.07.032","https://www.scopus.com/inward/record.uri?eid=2-s2.0-83855164451&doi=10.1016%2fj.microrel.2010.07.032&partnerID=40&md5=ac7ac0e7de234226e233277713d6c899"

116. Bräuer-Krisch E., Rosenfeld A., Lerch M., Petasecca M., Akselrod M., Sykora J., Bartz J., Ptaszkiewicz M., Olko P., Berg A., Wieland M., Doran S., Brochard T., Kamlowski A., Cellere G., Paccagnella A., Siegbahn E.A., Prezado Y., Martinez-Rovira I., Bravin A., Dusseau L., Berkvens P.,"Potential high resolution dosimeters for MRT",2010,"AIP Conference Proceedings","1266",,,"89","97",,"10.1063/1.3478205","https://www.scopus.com/inward/record.uri?eid=2-s2.0-77955628353&doi=10.1063%2f1.3478205&partnerID=40&md5=2029768390f39bd0a37e7f4def708790"

117. Silvestri M., Gerardin S., Faccio F., Paccagnella A.,"Single event gate rupture in 130-nm CMOS transistor arrays subjected to X-ray irradiation",2010,"IEEE Transactions on Nuclear Science","57","4 PART 1",5550321,"1842","1848",,"10.1109/TNS.2009.2039002","https://www.scopus.com/inward/record.uri?eid=2-s2.0-77955796421&doi=10.1109%2fTNS.2009.2039002&partnerID=40&md5=3073602d4eee7e87fa109d2d5a37b4ec"

118. Griffoni A., Gerardin S., Meneghesso G., Paccagnella A., Simoen E., Claeys C.,"Angular and strain dependence of heavy-ions induced degradation in SOI FinFETs",2010,"IEEE Transactions on Nuclear Science","57","4 PART 1",5550425,"1924","1932",,"10.1109/TNS.2010.2040196","https://www.scopus.com/inward/record.uri?eid=2-s2.0-77955839693&doi=10.1109%2fTNS.2010.2040196&partnerID=40&md5=92420d0c44577c3b37690a2626501116"

119. Rech P., Paccagnella A., Grosso M., Sonza Reorda M., Melchiori F., Loparco D., Appello D.,"Evaluating the impact of DfM library optimizations on alpha-induced SEU sensitivity in a microprocessor core",2010,"IEEE Transactions on Nuclear Science","57","4 PART 1",5550318,"2098","2105",,"10.1109/TNS.2010.2049119","https://www.scopus.com/inward/record.uri?eid=2-s2.0-77955786602&doi=10.1109%2fTNS.2010.2049119&partnerID=40&md5=a8f07b610f0e1561cb4c8c997b98a8f5"

120. Bagatin M., Gerardin S., Cellere G., Paccagnella A., Visconti A., Beltrami S., Bonanomi M., Harboe-Sorensen R.,"Annealing of heavy-ion induced floating gate errors: LET and feature size dependence",2010,"IEEE Transactions on Nuclear Science","57","4 PART 1", 5550300,"1835","1841",,"10.1109/TNS.2010.2045131","https://www.scopus.com/inward/record.uri?eid=2-s2.0-77955838697&doi=10.1109%2fTNS.2010.2045131&partnerID=40&md5=cc98e704460a0c43885fa387a2aa743d"
121. Irom F., Nguyen D.N., Bagatin M., Cellere G., Gerardin S., Paccagnella A.,"Catastrophic failure in highly scaled commercial NAND flash memories",2010,"IEEE Transactions on Nuclear Science","57","1 PART 2", 5410018,"266","271",,"10.1109/TNS.2009.2035315","https://www.scopus.com/inward/record.uri?eid=2-s2.0-77950651913&doi=10.1109%2fTNS.2009.2035315&partnerID=40&md5=c883c09b6e859c56ef3f44eb47dc6d64"
122. Abdo A.A., Ackermann M., Ajello M., Allafort A., Antolini E., Atwood W.B., Axelsson M., Baldini L., Ballet J., Barbiellini G., Bastieri D., Baughman B.M., Bechtol K., Bellazzini R., Belli F., Berenji B., Bisello D., Blandford R.D., Bloom E.D., Bonamente E., Bonnell J., Borgland A.W., Bouvier A., Bregeon J., Brez A., Brigida M., Bruel P., Burnett T.H., Busetto G., Buson S., Caliandro G.A., Cameron R.A., Campana R., Canadas B., Caraveo P.A., Carrigan S., Casandjian J.M., Cavazzuti E., Ceccanti M., Cecchi C., Çelik Ö., Charles E., Chekhtman A., Cheung C.C., Chiang J., Cillis A.N., Ciprini S., Claus R., Cohen-Tanugi J., Conrad J., Corbet R., Davis D.S., Deklotz M., Den Hartog P.R., Dermer C.D., De Angelis A., De Luca A., De Palma F., Digel S.W., Dormody M., Do Couto E Silva E., Drell P.S., Dubois R., Dumora D., Fabiani D., Farnier C., Favuzzi C., Fegan S.J., Ferrara E.C., Focke W.B., Fortin P., Frailis M., Fukazawa Y., Funk S., Fusco P., Gargano F., Gasparrini D., Gehrels N., Germani S., Giavitto G., Giebels B., Giglietto N., Giommi P., Giordano F., Giroletti M., Glanzman T., Godfrey G., Grenier I.A., Grondin M.-H., Grove J.E., Guillemot L., Guiriec S., Gustafsson M., Hadasch D., Hanabata Y., Harding A.K., Hayashida M., Hays E., Healey S.E., Hill A.B., Horan D., Hughes R.E., Iafrate G., Jóhannesson G., Johnson A.S., Johnson R.P., Johnson T.J., Johnson W.N., Kamae T., Katagiri H., Kataoka J., Kawai N., Kerr M., Knödlseder J., Kocevski D., Kuss M., Lande J., Landriu D., Latronico L., Lee S.-H., Lemoine-Goumard M., Lionetto A.M., Llena Garde M., Longo F., Loparco F., Lott B., Lovellette M.N., Lubrano P., Madejski G.M., Makeev A., Marangelli B., Marelli M., Massaro E., Mazziotta M.N., McConville W., McEnery J.E., Michelson P.F., Minuti M., Mitthumsiri W., Mizuno T., Moiseev A.A., Mongelli M., Monte C., Monzani M.E., Moretti E., Morselli A., Moskalenko I.V., Murgia S., Nakajima H., Nakamori T., Naumann-Godo M., Nolan P.L., Norris J.P., Nuss E., Ohno M., Ohsugi T., Omodei N., Orlando E., Ormes J.F., Ozaki M., Paccagnella A., Paneque D., Panetta J.H., Parent D., Pelassa V., Pepe M., Pesce-Rollins M., Pinchera M., Piron F., Porter T.A., Poupard L., Rainò S., Rando R., Ray P.S., Razzano M., Razzaque S., Rea N., Reimer A., Reimer O., Reposeur T., Ripken J., Ritz S., Rochester L.S., Rodriguez A.Y., Romani R.W., Roth M., Sadrozinski H.F.-W., Salvetti D., Sanchez D., Sander A., Saz Parkinson P.M., Scargle J.D., Schalk T.L., Scolieri G., Sgrò C., Shaw M.S., Siskind E.J., Smith D.A., Smith P.D., Spandre G., Spinelli P., Starck J.-L., Stephens T.E., Striani E., Strickman M.S., Strong A.W., Suson D.J., Tajima H., Takahashi H., Takahashi T., Tanaka T., Thayer J.B., Thayer J.G., Thompson D.J., Tibaldo L., Tibolla O., Tinebra F., Torres D.F., Tosti G., Tramacere A., Uchiyama Y., Usher T.L., Van Etten A., Vasileiou V., Vilchez N., Vitale V., Waite A.P., Wallace E., Wang P., Watters K., Winer B.L., Wood K.S., Yang Z., Ylinen T., Ziegler M.,"Fermi large area telescope first source catalog",2010,"Astrophysical Journal, Supplement Series","188","2",,"405","436",,"10.1088/0067-0049/188/2/405","https://www.scopus.com/inward/record.uri?eid=2-s2.0-77953203960&doi=10.1088%2f0067-0049%2f188%2f2%2f405&partnerID=40&md5=1167015e15ba24de5c3c09a6fe71fbde"

123. Silvestri M., Gerardin S., Faccio F., Paccagnella A.,"Single event gate rupture in 130-nm CMOS transistor arrays subjected to X-ray irradiation",2009,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5994565,"119","125",,"10.1109/RADECS.2009.5994565","https://www.scopus.com/inward/record.uri?eid=2-s2.0-80052759328&doi=10.1109%2fRADECS.2009.5994565&partnerID=40&md5=0e75a3c4a542a68c7c4c542bd592e73e"

124. Tazzoli A., Gasperin A., Paccagnella A., Meneghesso G.,"EOS/ESD sensitivity of phase-change-memories",2009,"Electrical Overstress/Electrostatic Discharge Symposium Proceedings",,, 5340119,"","",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-77950989489&partnerID=40&md5=6946438f8eb2321afe3431a0e54c22ac"

125. Rech P., Paccagnella A., Grosso M., Reorda M.S., Melchiori F., Appello D.,"Evaluating the impact of DFM library optimizations on alpha-induced SEU sensitivity in a microprocessor core",2009,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5994699,"481","488",,"10.1109/RADECS.2009.5994699","https://www.scopus.com/inward/record.uri?eid=2-s2.0-80052756412&doi=10.1109%2fRADECS.2009.5994699&partnerID=40&md5=67419eda7dff33064a5bfa035ae2168e"

126. Griffoni A., Gerardin S., Meneghesso G., Paccagnella A., Simoen E., Claeys C.,"Angular and strain dependence of heavy-ions induced degradation in SOI FinFETs",2009,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5994640,"267","274",,"10.1109/RADECS.2009.5994640","https://www.scopus.com/inward/record.uri?eid=2-s2.0-80052747345&doi=10.1109%2fRADECS.2009.5994640&partnerID=40&md5=89242154a8da548a1407353e19726fdc"

127. Silvestri M., Gerardin S., Schrimpf R.D., Fleetwood D.M., Faccio F., Paccagnella A.,"The role of irradiation bias on the time-dependent dielectric breakdown of 130-nm MOSFETs exposed to X-rays",2009,"IEEE Transactions on Nuclear Science","56","6", 5341387,"3244","3249",,"10.1109/TNS.2009.2033360","https://www.scopus.com/inward/record.uri?eid=2-s2.0-72349086512&doi=10.1109%2fTNS.2009.2033360&partnerID=40&md5=58b67c76155237c047e39b040a20e90d"

128. Bagatin M., Gerardin S., Cellere G., Paccagnella A., Visconti A., Bonanomi M., Beltrami S.,"Error instability in floating gate flash memories exposed to TID",2009,"IEEE Transactions on Nuclear Science","56","6", 5341401,"3267","3273",,"10.1109/TNS.2009.2033364","https://www.scopus.com/inward/record.uri?eid=2-s2.0-72349096808&doi=10.1109%2fTNS.2009.2033364&partnerID=40&md5=40765afa6744d36cf5dbdc5676f8a60f"

129. Bagatin M., Gerardin S., Cellere G., Paccagnella A., Visconti A., Beltrami S., Bonanomi M., Harboe-Sørensen R.,"Annealing of heavy-ion induced floating gate errors: LET and feature size dependence",2009,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5994564,"112","118",,"10.1109/RADECS.2009.5994564","https://www.scopus.com/inward/record.uri?eid=2-s2.0-80052752518&doi=10.1109%2fRADECS.2009.5994564&partnerID=40&md5=6f4388c3b03a2e405c55e146e26f9743"

130. Battezzati N., Gerardin S., Manuzzato A., Merodio D., Paccagnella A., Poivey C., Sterpone L., Violante M.,"Methodologies to study frequency-dependent single event effects sensitivity in flash-based FPGAs",2009,"IEEE Transactions on Nuclear Science","56","6",5341402,"3534","3541",,"10.1109/TNS.2009.2034316","https://www.scopus.com/inward/record.uri?eid=2-s2.0-72349090868&doi=10.1109%2fTNS.2009.2034316&partnerID=40&md5=e3840c0d68af05a83b1797c731f49151"

131. Griffoni A., Gerardin S., Roussel P.J., Degraeve R., Meneghesso G., Paccagnella A., Simoen E., Claeys C.,"A statistical approach to microdose induced degradation in finfet devices",2009,"IEEE Transactions on Nuclear Science","56","6",5341343,"3285","3292",,"10.1109/TNS.2009.2033365","https://www.scopus.com/inward/record.uri?eid=2-s2.0-72349084454&doi=10.1109%2fTNS.2009.2033365&partnerID=40&md5=03f748ac8b46b1bcb1ec5105918d018c"

132. Rech P., Gerardin S., Paccagnella A., Bernardi P., Grosso M., Reorda M.S., Appello D.,"Evaluating alpha-induced soft errors in embedded microprocessors",2009,"2009 15th IEEE International On-Line Testing Symposium, IOLTS 2009",,,5195985,"69","74",,"10.1109/IOLTS.2009.5195985","https://www.scopus.com/inward/record.uri?eid=2-s2.0-70449399661&doi=10.1109%2fIOLTS.2009.5195985&partnerID=40&md5=493e100c8bfc18251d2e252f3fad8832"

133. Adam W., Bergauer T., Dragicevic M., Friedl M., Frühwirth R., Hänsel S., Hrubec J., Krammer M., Oberegger M., Pernicka M., Schmid S., Stark R., Steininger H., Uhl D., Waltenberger W., Widl E., Van Mechelen P., Cardaci M., Beaumont W., De Langhe E., De Wolf E.A., Delmeire E., M Hashemi, Bouhali O., Charaf O., Clerbaux B., J-P Dewulf, Elgammal S., Hammad G., De Lentdecker G., Marage P., Vander Velde C., Vanlaer P., Wickens J., Adler V., Devroede O., De Weirdt S., D'Hondt J., Goorens R., Heyninck J., Maes J., Mozer M., Tavernier S., Van Lancker L., Van Mulders P., Villella I., Wastiels C., Bonnet J.-L., Bruno G., De Callatay B., Florins B., Giammanco A., Gregoire G., Th Keutgen, Kcira D., Lemaitre V., Michotte D., Militaru O., Piotrzkowski K., Quertermont L., Roberfroid V., Rouby X., Teyssier D., Daubie E., Anttila E., Czellar S., Engström P., Härkönen J., Karimäki V., Kostesmaa J., Kuronen A., Lampén T., Lindén T., P-R Luukka, Mäenää T., Michal S., Tuominen E., Tuominiemi J., Ageron M., Baulieu G., Bonnevaux A., Boudoul G., Chabanat E., Chabert E., Chierici R., Contardo D., Della Negra R., Dupasquier T., Gelin G., Giraud N., Guillot G., Estre N., Haroutunian R., Lumb N., Perries S., Schirra F., Trocme B., Vanzetto S., J-L Agram, Blaes R., Drouhin F., J-P Ernenwein, J-C Fontaine, J-D Berst, J-M Brom, Didierjean F., Goerlach U., Graehling P., Gross L., Hosselet J., Juillot P., Lounis A., Maazouzi C., Olivetto C., Strub R., Van Hove P., Anagnostou G., Brauer R., Esser H., Feld L., Karpinski W., Klein K., Kukulies C., Olzem J., Ostapchuk A., Pandoulas D., Pierschel G., Raupach F., Schael S., Schwering G., Sprenger D., Thomas M., Weber M., Wittmer B., Wlochal M., Beissel F., Bock E., Flugge G., Gillissen C., Hermanns T., Heydhausen D., Jahn D., Kaussen G., Linn A., Perchalla L., Poettgens M., Pooth O., Stahl A., Zoeller M.H., Buhmann P., Butz E., Flucke G., Hamdorf R., Hauk J., Klanner R., Pein U., Schleper P., Steinbrück G., Blüm P., De Boer W., Dierlamm A., Dirkes G., Fahrer M., Frey M., Furgeri A., Hartmann F., Heier S., K-H Hoffmann, Kaminski J., Ledermann B., Liamsuwan T., Müller S., Th Müller, F-P Schilling, Simonis H.-J., Steck P., Zhukov V., Cariola P., De Robertis G., Ferorelli R., Fiore L., Preda M., Sala G., Silvestris L., Tempesta P., Zito G., Creanza D., De Filippis N., De Palma M., Giordano D., Maggi G., Manna N., My S., Selvaggi G., Albergo S., Chiorboli M., Costa S., Galanti M., Giudice N., Guardone N., Noto F., Potenza R., Saizu M.A., Sparti V., Sutera C., Tricomi A., Tuvè C., Brianzi M., Civinini C., Maletta F., Manolescu F., Meschini M., Paoletti S., Sguazzoni G., Broccolo B., Ciulli V., Focardi R.D.E., Frosali S., Genta C., Landi G., Lenzi P., MacChiolo A., Magini N., Parrini G., Scarlini E., Cerati G., Azzi P., Bacchetta N., Candelori A., Dorigo T., Kaminsky

A., Karaevski S., Khomenkov V., Reznikov S., Tessaro M., Bisello D., De Mattia M., Giubilato P., Loreti M., Mattiazzo S., Nigro M., Paccagnella A., Pantano D., Pozzobon N., Tosi M., Bilei M., Checcucci B., Fanò L., Servoli L., Ambroglini F., Babucci E., Benedetti D., Biasini M., Caponeri B., Covarelli R., Giorgi M., Lariccia P., Mantovani G., Marcantonini M., Postolache V., Santocchia A., Spiga D., Bagliesi G., Balestri G., Berretta L., Bianucci S., Boccali T., Bosi F., Bracci F., Castaldi R., Ceccanti M., Cecchi R., Cerri C., Cucoanes S., Dell'Orso R., Dobur D., Dutta S., Giassi A., Giusti S., Kartashov D., Kraan A., Lomtadze T., Lungu G.A., Magazz G., Mammini P., Mariani F., Martinelli G., Moggi A., Palla F., Palmonari F., Petragnani G., Profeti A., Raffaelli F., Rizzi D., Sanguinetti G., Sarkar S., Sentenac D., Serban T., Slav A., Soldani A., Spagnolo P., Tenchini R., Tolaini S., Venturi A., Verdini P.G., Vos M., Zaccarelli L., Avanzini C., Basti A., Benucci L., Bocci A., Cazzola U., Fiori F., Linari S., Massa M., Messineo A., Segneri G., Tonelli G., Azzurri P., Bernardini J., Borrello L., Calzolari F., Fo L., Gennai S., Ligabue F., Petrucciani G., Rizzi A., Yang Z., Benotto F., Demaria N., Dumitrache F., Farano R., Borgia M.A., Castello R., Costa M., Migliore E., Romero A., Abbaneo D., Abbas M., Ahmed I., Akhtar I., Albert E., Bloch C., Breuker H., Butt S., Buchmuller O., Cattai A., Delaere C., Delattre M., Edera L.M., Engstrom P., Eppard M., Gateau M., Gill K., Giolo-Nicollerat A.-S., Grabit R., Honma A., Huhtinen M., Kloukinas K., Kortesmaa J., Kottelat J., Kuronen A., Leonardo N., Ljuslin C., Mannelli M., Masetti L., Marchioro A., Mersi S., Michal S., Mirabito L., Muffat-Joly J., Onnela A., Paillard C., Pal I., Pernot F., Petagna P., Petit P., Piccut C., Pioppi M., Postema H., Ranieri R., Ricci D., Rolandi G., Ronga F., Sigaud C., Syed A., Siegrist P., Tropea P., Troska J., Tsirou A., Vander Donckt M., Vasey F., Alagoz E., Amsler C., Chiochia V., Regenfus C., Robmann P., Rochet J., Rommerskirchen T., Schmidt A., Steiner S., Wilke L., Church I., Cole J., Coughlan J., Gay A., Taghavi S., Tomalin I., Bainbridge R., Cripps N., Fulcher J., Hall G., Noy M., Pesaresi M., Radicci V., Raymond D.M., Sharp P., Stoye M., Wingham M., Zorba O., Goitom I., Hobson P.R., Reid I., Teodorescu L., Hanson G., Jeng G.-Y., Liu H., Pasztor G., Satpathy A., Stringer R., Mangano B., Affolder K., Affolder T., Allen A., Barge D., Burke S., Callahan D., Campagnari C., Crook A., D'Alfonso M., Dietch J., Garberson J., Hale D., Incandela H., Incandela J., Jaditz S., Kalavase P., Kreyer S., Kyre S., Lamb J., Mc Guinness C., Mills C., Nguyen H., Nikolic M., Lowette S., Rebassoo F., Ribnik J., Richman J., Rubinstein N., Sanhueza S., Shah Y., Simms L., Staszak D., Stoner J., Stuart D., Swain S., Vlimant J.-R., White D., Ulmer A., Wagner S.R., Bagby L., Bhat P.C., Burkett K., Cihangir S., Gutsche O., Jensen H., Johnson M., Luzhetskiy N., Mason D., Miao T., Moccia S., Noeding C., Ronzhin A., Skup E., Spalding J., Spiegel L., Tkaczyk S., Yumiceva F., Zatserklyaniy A., Zerev E., Anghel I., Bazterra V.E., Gerber C.E., Khalatian S., Shabalina E., Baringer P., Bean A., Chen J., Hinchey C., Martin C., Moulik T., Robinson R., Gritsan A.V., Lae C.K., Tran N.V., Everaerts P., Hahn K.A., Harris P., Nahn S., Rudolph M., Sung K., Betchart B., Demina R., Gotra Y., Korjenevski S., Miner D., Orbaker D., Christofek L., Hooper R., Landsberg G., Nguyen D., Narain M., Speer T., Tsang K.V.,"Alignment of the CMS silicon strip tracker during stand-alone commissioning",2009,"Journal of Instrumentation","4","7", T07001,"","",,"10.1088/1748-0221/4/07/T07001","https://www.scopus.com/inward/record.uri?eid=2-s2.0-71049187595&doi=10.1088%2f1748-0221%2f4%2f07%2fT07001&partnerID=40&md5=e7a9464b052487a6d54531f796353e5b"

134. Adam W., Bergauer T., Dragicevic M., Friedl M., Frühwirth R., Hänsel S., Hrubec J., Krammer M., Oberegger M., Pernicka M., Schmid S., Stark R., Steininger H., Uhl D., Waltenberger W., Widl E., Van Mechelen P., Cardaci M., Beaumont W., De Langhe E., De Wolf E.A., Delmeire E., Hashemi M., Bouhali O., Charaf O., Clerbaux B., Dewulf J.-P., Elgammal S., Hammad G., De Lentdecker G., Marage P., Vander Velde C., Vanlaer P., Wickens J., Adler V., Devroede O., De Weirdt S., DHondt J., Goorens R., Heyninck J., Maes J., Mozer M., Tavernier S., Van Lancker L., Van Mulders P., Villella I., Wastiels C., Bonnet J.-L., Bruno G., De Callatay B., Florins B., Giammanco A., Gregoire G., Keutgen Th., Kcira D., Lemaitre V., Michotte D., Militaru O., Piotrzkowski K., Quertermont L., Roberfroid V., Rouby X., Teyssier D., Daubie E., Anttila E., Czellar S., Engström P., Härkönen J., Karimäki V., Kostesmaa J., Kuronen A., Lampén T., Lindén T., Luukka P.-R., Mäenpää T., Michal S., Tuominen E., Tuominiemi J.,

Ageron M., Baulieu G., Bonnevaux A., Boudoul G., Chabanat E., Chabert E., Chierici R., Contardo D., DellaNegra R., Dupasquier T., Gelin G., Giraud N., Guillot G., Estre N., Haroutunian R., Lumb N., Perries S., Schirra F., Trocme B., Vanzetto S., Agram J.-L., Blaes R., Drouhin F., Ernenwein J.-P., Fontaine J.-C., Berst J.-D., Brom J.-M., Didierjean F., Goerlach U., Graehling P., Gross L., Hosselet J., Juillot P., Lounis A., Maazouzi C., Olivetto C., Strub R., Van Hove P., Anagnostou G., Brauer R., Esser H., Feld L., Karpinski W., Klein K., Kukulies C., Olzem J., Ostapchuk A., Pandoulas D., Pierschel G., Raupach F., Schael S., Schwering G., Sprenger D., Thomas M., Weber M., Wittmer B., Wlochal M., Beissel F., Bock E., Flugge G., Gillissen C., Hermanns T., Heydhausen D., Jahn D., Kaussen G., Linn A., Perchalla L., Poettgens M., Pooth O., Stahl A., Zoeller M.H., Buhmann P., Butz E., Flucke G., Hamdorf R., Hauk J., Klanner R., Pein U., Schleper P., Steinbrück G., Blüm P., De Boer W., Dierlamm A., Dirkes G., Fahrer M., Frey M., Furgeri A., Hartmann F., Heier S., Hoffmann K.-H., Kaminski J., Ledermann B., Liamsuwan T., Müller S., Müller Th., Schilling F.-P., Simonis H.-J., Steck P., Zhukov V., Cariola P., De Robertis G., Ferorelli R., Fiore L., Preda M., Sala G., Silvestris L., Tempesta P., Zito G., Creanza D., De Filippis N., De Palma M., Giordano D., Maggi G., Manna N., My S., Selvaggi G., Albergo S., Chiorboli M., Costa S., Galanti M., Giudice N., Guardone N., Noto F., Potenza R., Saizu M.A., Sparti V., Sutera C., Tricomi A., Tuvè C., Brianzi M., Civinini C., Maletta F., Manolescu F., Meschini M., Paoletti S., Sguazzoni G., Broccolo B., Ciulli V., DAlessandro R., Focardi E., Frosali S., Genta C., Landi G., Lenzi P., MacChiolo A., Magini N., Parrini G., Scarlini E., Cerati G., Azzi P., Bacchetta N., Candelori A., Dorigo T., Kaminsky A., Karaevski S., Khomenkov V., Reznikov S., Tessaro M., Bisello D., De Mattia M., Giubilato P., Loreti M., Mattiazzo S., Nigro M., Paccagnella A., Pantano D., Pozzobon N., Tosi M., Bilei G.M., Checcucci B., Fanò L., Servoli L., Ambroglini F., Babucci E., Benedetti D., Biasini M., Caponeri B., Covarelli R., Giorgi M., Lariccia P., Mantovani G., Marcantonini M., Postolache V., Santocchia A., Spiga D., Bagliesi G., Balestri G., Berretta L., Bianucci S., Boccali T., Bosi F., Bracci F., Castaldi R., Ceccanti M., Cecchi R., Cerri C., Cucoanes A.S., DellOrso R., Dobur D., Dutta S., Giassi A., Giusti S., Kartashov D., Kraan A., Lomtadze T., Lungu G.A., Magazzù G., Mammini P., Mariani F., Martinelli G., Moggi A., Palla F., Palmonari F., Petragnani G., Profeti A., Raffaelli F., Rizzi D., Sanguinetti G., Sarkar S., Sentenac D., Serban A.T., Slav A., Soldani A., Spagnolo P., Tenchini R., Tolaini S., Venturi A., Verdini P.G., Vos M., Zaccarelli L., Avanzini C., Basti A., Benucci L., Bocci A., Cazzola U., Fiori F., Linari S., Massa M., Messineo A., Segneri G., Tonelli G., Azzurri P., Bernardini J., Borrello L., Calzolari F., Foà L., Gennai S., Ligabue F., Petrucciani G., Rizzi A., Yang Z., Benotto F., Demaria N., Dumitrache F., Farano R., Borgia M.A., Castello R., Costa M., Migliore E., Romero A., Abbaneo D., Abbas M., Ahmed I., Akhtar I., Albert E., Bloch C., Breuker H., Butt S., Buchmuller O., Cattai A., Delaere C., Delattre M., Edera L.M., Engstrom P., Eppard M., Gateau M., Gill K., Giolo-Nicollerat A.-S., Grabit R., Honma A., Huhtinen M., Kloukinas K., Kortesmaa J., Kottelat L.J., Kuronen A., Leonardo N., Ljuslin C., Mannelli M., Masetti L., Marchioro A., Mersi S., Michal S., Mirabito L., Muffat-Joly J., Onnela A., Paillard C., Pal I., Pernot J.F., Petagna P., Petit P., Piccut C., Pioppi M., Postema H., Ranieri R., Ricci D., Rolandi G., Ronga F., Sigaud C., Syed A., Siegrist P., Tropea P., Troska J., Tsirou A., Vander Donckt M., Vasey F., Alagoz E., Amsler C., Chiochia V., Regenfus C., Robmann P., Rochet J., Rommerskirchen T., Schmidt A., Steiner S., Wilke L., Church I., Cole J., Coughlan J., Gay A., Taghavi S., Tomalin I., Bainbridge R., Cripps N., Fulcher J., Hall G., Noy M., Pesaresi M., Radicci V., Raymond D.M., Sharp P., Stoye M., Wingham M., Zorba O., Goitom I., Hobson P.R., Reid I., Teodorescu L., Hanson G., Jeng G.-Y., Liu H., Pasztor G., Satpathy A., Stringer R., Mangano B., Affolder K., Affolder T., Allen A., Barge D., Burke S., Callahan D., Campagnari C., Crook A., DAlfonso M., Dietch J., Garberson J., Hale D., Incandela H., Incandela J., Jaditz S., Kalavase P., Kreyer S., Kyre S., Lamb J., Mc Guinness C., Mills C., Nguyen H., Nikolic M., Lowette S., Rebassoo F., Ribnik J., Richman J., Rubinstein N., Sanhueza S., Shah Y., Simms L., Staszak D., Stoner J., Stuart D., Swain S., Vlimant J.-R., White D., Ulmer K.A., Wagner S.R., Bagby L., Bhat P.C., Burkett K., Cihangir S., Gutsche O., Jensen H., Johnson M., Luzhetskiy N., Mason D., Miao T., Moccia S., Noeding C., Ronzhin A., Skup E., Spalding W.J., Spiegel L., Tkaczyk S., Yumiceva F., Zatserklyaniy A., Zerev E., Anghel I., Bazterra V.E., Gerber C.E., Khalatian S., Shabalina E., Baringer P., Bean A., Chen J., Hinchey C., Martin C., Moulik T., Robinson R., Gritsan A.V., Lae C.K., Tran N.V., Everaerts P., Hahn K.A., Harris P., Nahn S., Rudolph M., Sung K., Betchart B., Demina R., Gotra Y., Korjenevski S., Miner D., Orbaker D., Christofek L., Hooper R., Landsberg G., Nguyen D., Narain M., Speeras T., Tsangas K.V.,"Stand-alone cosmic muon reconstruction before installation of the CMS silicon strip tracker",2009,"Journal of Instrumentation","4","5", P05004,"","",,"10.1088/1748-0221/4/05/P05004","https://www.scopus.com/inward/record.uri?eid=2-s2.0-71049142164&doi=10.1088%2f1748-0221%2f4%2f05%2fP05004&partnerID=40&md5=bd52572a8dbde3e3314a7b23a2a63ae1"

135. Adam W., Bergauer T., Dragicevic M., Friedl M., Frühwirth R., Hänsel S., Hrubec J., Krammer M., Oberegger M., Pernicka M., Schmid S., Stark R., Steininger H., Uhl D., Waltenberger W., Widl E., Van Mechelen P., Cardaci M., Beaumont W., De Langhe E., De Wolf E.A., Delmeire E., Hashemi M., Bouhali O., Charaf O., Clerbaux B., Dewulf J.-P., Elgammal S., Hammad G., De Lentdecker G., Marage P., Vander Velde C., Vanlaer P., Wickens J., Adler V., Devroede O., De Weirdt S., D'Hondt J., Goorens R., Heyninck J., Maes J., Mozer M., Tavernier S., Van Lancker L., Van Mulders P., Villella I., Wastiels C., Bonnet J.-L., Bruno G., De Callatay B., Florins B., Giammanco A., Gregoire G., Keutgen Th., Kcira D., Lemaitre V., Michotte D., Militaru O., Piotrzkowski K., Quertermont L., Roberfroid V., Rouby X., Teyssier D., Daubie E., Anttila E., Czellar S., Engström P., Härkönen J., Karimäki V., Kostesmaa J., Kuronen A., Lampén T., Lindén T., Luukka P.-R., Mäenpää T., Michal S., Tuominen E., Tuominiemi J., Ageron M., Baulieu G., Bonnevaux A., Boudoul G., Chabanat E., Chabert E., Chierici R., Contardo D., Della Negra R., Dupasquier T., Gelin G., Giraud N., Guillot G., Estre N., Haroutunian R., Lumb N., Perries S., Schirra F., Trocme B., Vanzetto S., Agram J.-L., Blaes R., Drouhin F., Ernenwein J.-P., Fontaine J.-C., Berst J.-D., Brom J.-M., Didierjean F., Goerlach U., Graehling P., Gross L., Hosselet J., Juillot P., Lounis A., Maazouzi C., Olivetto C., Strub R., Van Hove P., Anagnostou G., Brauer R., Esser H., Feld L., Karpinski W., Klein K., Kukulies C., Olzem J., Ostapchuk A., Pandoulas D., Pierschel G., Raupach F., Schael S., Schwering G., Sprenger D., Thomas M., Weber M., Wittmer B., Wlochal M., Beissel F., Bock E., Flugge G., Gillissen C., Hermanns T., Heydhausen D., Jahn D., Kaussen G., Linn A., Perchalla L., Poettgens M., Pooth O., Stahl A., Zoeller M.H., Buhmann P., Butz E., Flucke G., Hamdorf R., Hauk J., Klanner R., Pein U., Schleper P., Steinbrück G., Blüm P., De Boer W., Dierlamm A., Dirkes G., Fahrer M., Frey M., Furgeri A., Hartmann F., Heier S., Hoffmann K.-H., Kaminski J., Ledermann B., Liamsuwan T., Müller S., Müller Th., Schilling F.-P., Simonis H.-J., Steck P., Zhukov V., Cariola P., De Robertis G., Ferorelli R., Fiore L., Preda M., Sala G., Silvestris L., Tempesta P., Zito G., Creanza D., De Filippis N., De Palma M., Giordano D., Maggi G., Manna N., My S., Selvaggi G., Albergo S., Chiorboli M., Costa S., Galanti M., Giudice N., Guardone N., Noto F., Potenza R., Saizu M.A., Sparti V., Sutera C., Tricomi A., Tuvè C., Brianzi M., Civinini C., Maletta F., Manolescu F., Meschini M., Paoletti S., Sguazzoni G., Broccolo B., Ciulli V., D'Alessandro R., Focardi E., Frosali S., Genta C., Landi G., Lenzi P., MacChiolo A., Magini N., Parrini G., Scarlini E., Cerati G., Azzi P., Bacchetta N., Candelori A., Dorigo T., Kaminsky A., Karaevski S., Khomenkov V., Reznikov S., Tessaro M., Bisello D., De Mattia M., Giubilato P., Loreti M., Mattiazzo S., Nigro M., Paccagnella A., Pantano D., Pozzobon N., Tosi M., Bilei G.M., Checcucci B., Fanò L., Servoli L., Ambroglini F., Babucci E., Benedetti D., Biasini M., Caponeri B., Covarelli R., Giorgi M., Lariccia P., Mantovani G., Marcantonini M., Postolache V., Santocchia A., Spiga D., Bagliesi G., Balestri G., Berretta L., Bianucci S., Boccali T., Bosi F., Bracci F., Castaldi R., Ceccanti M., Cecchi R., Cerri C., Cucoanes A.S., Dell'Orso R., Dobur D., Dutta S., Giassi A., Giusti S., Kartashov D., Kraan A., Lomtadze T., Lungu G.A., Magazzù G., Mammini P., Mariani F., Martinelli G., Moggi A., Palla F., Palmonari F., Petragnani G., Profeti A., Raffaelli F., Rizzi D., Sanguinetti G., Sarkar S., Sentenac D., Serban A.T., Slav A., Soldani A., Spagnolo P., Tenchini R., Tolaini S., Venturi A., Verdini P.G., Vos M., Zaccarelli L., Avanzini C., Basti A., Benucci L., Bocci A., Cazzola U., Fiori F., Linari S., Massa M., Messineo A., Segneri G., Tonelli G., Azzurri P., Bernardini J., Borrello L., Calzolari F., Foà L., Gennai S., Ligabue F., Petrucciani G., Rizzi A., Yang Z., Benotto F.,

Demaria N., Dumitrache F., Farano R., Borgia M.A., Castello R., Costa M., Migliore E., Romero A., Abbaneo D., Abbas M., Ahmed I., Akhtar I., Albert E., Bloch C., Breuker H., Butt S., Buchmuller O., Cattai A., Delaere C., Delattre M., Edera L.M., Engstrom P., Eppard M., Gateau M., Gill K., Giolo-Nicollerat A.-S., Grabit R., Honma A., Huhtinen M., Kloukinas K., Kortesmaa J., Kottelat L.J., Kuronen A., Leonardo N., Ljuslin C., Mannelli M., Masetti L., Marchioro A., Mersi S., Michal S., Mirabito L., Muffat-Joly J., Onnela A., Paillard C., Pal I., Pernot J.F., Petagna P., Petit P., Piccut C., Pioppi M., Postema H., Ranieri R., Ricci D., Rolandi G., Ronga F., Sigaud C., Syed A., Siegrist P., Tropea P., Troska J., Tsirou A., Vander Donckt M., Vasey F., Alagoz E., Amsler C., Chiochia V., Regenfus C., Robmann P., Rochet J., Rommerskirchen T., Schmidt A., Steiner S., Wilke L., Church I., Cole J., Coughlan J., Gay A., Taghavi S., Tomalin I., Bainbridge R., Cripps N., Fulcher J., Hall G., Noy M., Pesaresi M., Radicci V., Raymond D.M., Sharp P., Stoye M., Wingham M., Zorba O., Goitom I., Hobson P.R., Reid I., Teodorescu L., Hanson G., Jeng G.-Y., Liu H., Pasztor G., Satpathy A., Stringer R., Mangano B., Affolder K., Affolder T., Allen A., Barge D., Burke S., Callahan D., Campagnari C., Crook A., D'Alfonso M., Dietch J., Garberson J., Hale D., Incandela H., Incandela J., Jaditz S., Kalavase P., Kreyer S., Kyre S., Lamb J., Mc Guinness C., Mills C., Nguyen H., Nikolic M., Lowette S., Rebassoo F., Ribnik J., Richman J., Rubinstein N., Sanhueza S., Shah Y., Simms L., Staszak D., Stoner J., Stuart D., Swain S., Vlimant J.-R., White D., Ulmer K.A., Wagner S.R., Bagby L., Bhat P.C., Burkett K., Cihangir S., Gutsche O., Jensen H., Johnson M., Luzhetskiy N., Mason D., Miao T., Moccia S., Noeding C., Ronzhin A., Skup E., Spalding W.J., Spiegel L., Tkaczyk S., Yumiceva F., Zatserklyaniy A., Zerev E., Anghel I., Bazterra V.E., Gerber C.E., Khalatian S., Shabalina E., Baringer P., Bean A., Chen J., Hinchey C., Martin C., Moulik T., Robinson R., Gritsan A.V., Lae C.K., Tran N.V., Everaerts P., Hahn K.A., Harris P., Nahn S., Rudolph M., Sung K., Betchart B., Demina R., Gotra Y., Korjenevski S., Miner D., Orbaker D., Christofek L., Hooper R., Landsberg G., Nguyen D., Narain M., Speer T., Tsang K.V.,"Performance studies of the CMS Strip Tracker before installation",2009,"Journal of Instrumentation","4","6", P06009,"","",,"10.1088/1748-0221/4/06/P06009","https://www.scopus.com/inward/record.uri?eid=2-s2.0-71049130701&doi=10.1088%2f1748-0221%2f4%2f06%2fP06009&partnerID=40&md5=bdd33f8be104630fcf2f7202f3876ba3"

136. Appello D., Bernardi P., Gerardin S., Grosso M., Paccagnella A., Rech P., Reorda M.S.,"DfT reuse for low-cost radiation testing of SoCs: A case study",2009,"Proceedings of the IEEE VLSI Test Symposium",,, 5116647,"276","281",,"10.1109/VTS.2009.26","https://www.scopus.com/inward/record.uri?eid=2-s2.0-70350374095&doi=10.1109%2fVTS.2009.26&partnerID=40&md5=0f2158fa1b1ff7f8d20d394b8b49535d"

137. Martín-Martínez J., Gerardin S., Rodríguez R., Nafría M., Aymerich X., Paccagnella A., Ghidini G.,"Gate dielectric degradation in CMOS inverters",2009,"Microelectronic Engineering","86","10",,"2123","2126",,"10.1016/j.mee.2009.02.033","https://www.scopus.com/inward/record.uri?eid=2-s2.0-67649986902&doi=10.1016%2fj.mee.2009.02.033&partnerID=40&md5=d688c7d65e96dab975bf8e6975f06a0c"

138. Gasperin A., Amat E., Porti M., Martín-Martínez J., Nafría M., Aymerich X., Paccagnella A.,"Effects of the localization of the charge in nanocrystal memory cells",2009,"IEEE Transactions on Electron Devices","56","10",,"2319","2326",,"10.1109/TED.2009.2028404","https://www.scopus.com/inward/record.uri?eid=2-s2.0-70350043366&doi=10.1109%2fTED.2009.2028404&partnerID=40&md5=741c55ec6dfb0eafa6b6baa3390072b9"

139. Martín-Martínez J., Gerardin S., Amat E., Rodríguez R., Nafría M., Aymerich X., Paccagnella A., Ghidini G.,"Channel-hot-carrier degradation and bias temperature instabilities in CMOS inverters",2009,"IEEE Transactions on Electron Devices","56","9",,"2155","2159",,"10.1109/TED.2009.2026206","https://www.scopus.com/inward/record.uri?eid=2-s2.0-69549128148&doi=10.1109%2fTED.2009.2026206&partnerID=40&md5=e5ff2cd0f3602f22943f6cead94df87a"
140. Silvestri M., Gerardin S., Paccagnella A., Ghidini G.,"Gate rupture in ultra-thin gate oxides irradiated with heavy ions",2009,"IEEE Transactions on Nuclear Science","56","4", 5204597,"1964","1970",,"10.1109/TNS.2009.2022364","https://www.scopus.com/inward/record.uri?eid=2-s2.0-69549131019&doi=10.1109%2fTNS.2009.2022364&partnerID=40&md5=57ab2b0f605b1140ca9183dc5aa17634"
141. Gasperin A., Paccagnella A., Ghidini G., Sebastiani A.,"Heavy ion irradiation effects on capacitors with SiO2 and ONO as Dielectrics",2009,"IEEE Transactions on Nuclear Science","56","4", 5204603,"2218","2224",,"10.1109/TNS.2009.2015879","https://www.scopus.com/inward/record.uri?eid=2-s2.0-69549083121&doi=10.1109%2fTNS.2009.2015879&partnerID=40&md5=7e29686ffe7c7eb1f8e31408c6526a9b"
142. Bagatin M., Cellere G., Gerardin S., Paccagnella A., Visconti A., Beltrami S.,"TID sensitivity of NAND flash memory building blocks",2009,"IEEE Transactions on Nuclear Science","56","4", 5204727,"1909","1913",,"10.1109/TNS.2009.2016095","https://www.scopus.com/inward/record.uri?eid=2-s2.0-69549118769&doi=10.1109%2fTNS.2009.2016095&partnerID=40&md5=52ee75c762d64119f6d039519e275534"
143. Griffoni A., Silvestri M., Gerardin S., Meneghesso G., Paccagnella A., Kaczer B., De Potter De Ten Broeck M., Verbeeck R., Nackaerts A.,"Dose enhancement due to interconnects in deep-submicron MOSFETs exposed to X-rays",2009,"IEEE Transactions on Nuclear Science","56","4", 5204691,"2205","2212",,"10.1109/TNS.2009.2012860","https://www.scopus.com/inward/record.uri?eid=2-s2.0-69549096606&doi=10.1109%2fTNS.2009.2012860&partnerID=40&md5=00fb165c50520682bdd8dadb849cdcab"
144. Tazzoli A., Cellere G., Peretti V., Paccagnella A., Meneghesso G.,"Radiation sensitivity of OHAMIC RF-MEMS switches for spatial applications",2009,"Proceedings of the IEEE International Conference on Micro Electro Mechanical Systems (MEMS)",,, 4805462,"634","637",,"10.1109/MEMSYS.2009.4805462","https://www.scopus.com/inward/record.uri?eid=2-s2.0-65949096315&doi=10.1109%2fMEMSYS.2009.4805462&partnerID=40&md5=e584672556610d777bd6676e1f00f0c3"
145. Abdo A.A., Ackermann M., Atwood W.B., Bagagli R., Baldini L., Ballet J., Band D.L., Barbiellini G., Baring M.G., Bartelt J., Bastieri D., Baughman B.M., Bechtol K., Bellardi F., Bellazzini R., Berenji B., Bisello D., Blandford R.D., Bloom E.D., Bogart J.R., Bonamente E., Borgland A.W., Bouvier A., Bregeon J., Brez A., Brigida M., Bruel P., Burnett T.H., Caliandro G.A., Cameron R.A., Camilo F., Caraveo P.A., Casandjian J.M., Ceccanti M., Cecchi C., Charles E., Chekhtman A., Cheung C.C., Chiang J., Ciprini S., Claus R., Cognard I., Cohen-Tanugi J., Cominsky L.R., Conrad J., Corbet R., Corucci L., Cutini S., Davis D.S., Deklotz M., Dermer C.D., De Angelis A., De Palma F., Digel S.W., Dormody M., Silva E.D.C.E., Drell P.S., Dubois R., Dumora D., Espinoza C., Farnier C., Favuzzi C., Flath D.L., Fleury P., Focke W.B., Frailis M., Friere P.C.C., Fukazawa Y., Funk S., Fusco P., Gargano F., Gasparrini D., Gehrels N., Germani S., Giannitrapani R., Giebels B., Giglietto N., Giordano F.,

Glanzman T., Godfrey G., Gotthelf E.V., Grenier I.A., Grondin M.-H., Grove J.E., Guillemot L., Guiriec S., Haller G., Harding A.K., Hart P.A., Hartman R.C., Hays E., Hobbs G., Hughes R.E., Jóhannesson G., Johnson A.S., Johnson R.P., Johnson T.J., Johnson W.N., Johnston S., Kamae T., Kanbach G., Kaspi V.M., Katagiri H., Kataoka J., Kavelaars A., Kawai N., Kelly H., Kerr M., Kiziltan B., Klamra W., Knödlseder J., Kramer M., Kuehn F., Kuss M., Lande J., Landriu D., Latronico L., Lee B., Lee S.-H., Lemoine-Goumard M., Livingstone M., Longo F., Loparco F., Lott B., Lovellette M.N., Lubrano P., Lyne A.G., Madejski G.M., Makeev A., Manchester R.N., Marangelli B., Marelli M., Mazziotta M.N., McEnery J.E., McGlynn S., McLaughlin M.A., Menon N., Meurer C., Michelson P.F., Mineo T., Mirizzi N., Mitthumsiri W., Mizuno T., Moiseev A.A., Mongelli M., Monte C., Monzani M.E., Moretti E., Morselli A., Moskalenko I.V., Murgia S., Nakamori T., Nolan P.L., Noutsos A., Nuss E., Ohsugi T., Omodei N., Orlando E., Ormes J.F., Ozaki M., Paccagnella A., Paneque D., Panetta J.H., Parent D., Pearce M., Pepe M., Perchiazzi M., Pesce-Rollins M., Pieri L., Pinchera M., Piron F., Porter T.A., Rainò S., Rando R., Ransom S.M., Rapposelli E., Razzano M., Reimer A., Reimer O., Reposeur T., Reyes L.C., Ritz S., Rochester L.S., Rodriguez A.Y., Romani R.W., Roth M., Ryde F., Sacchetti A., Sadrozinski H.F.-W., Saggini N., Sanchez D., Sander A., Parkinson P.M.S., Segal K.N., Sellerholm A., Sgrò C., Siskind E.J., Smith D.A., Smith P.D., Spandre G., Spinelli P., Stamatikos M., Starck J.-L., Stecker F.W., Stephens T.E., Strickman M.S., Strong A.W., Suson D.J., Tajima H., Takahashi H., Takahashi T., Tanaka T., Tenze A., Thayer J.B., Thayer J.G., Theureau G., Thompson D.J., Thorsett S.E., Tibaldo L., Tibolla O., Torres D.F., Tramacere A., Turri M., Usher T.L., Vigiani L., Vilchez N., Vitale V., Waite A.P., Wang P., Watters K., Weltevrede P., Winer B.L., Wood K.S., Ylinen T., Ziegler M.,"Fermi large area telescope observations of the vela pulsar",2009,"Astrophysical Journal","696","2",,"1084","1093",,"10.1088/0004-637X/696/2/1084","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84863115445&doi=10.1088%2f0004-637X%2f696%2f2%2f1084&partnerID=40&md5=8c7b4867f780cb27c29ee112feeed5b0"

146. Paccagnella A., Gerardin S., Cellere G.,"Radiation damage on dielectrics: Single event effects",2009,"Journal of Vacuum Science and Technology B: Microelectronics and Nanometer Structures","27","1",,"406","410",,"10.1116/1.3054271","https://www.scopus.com/inward/record.uri?eid=2-s2.0-59949090937&doi=10.1116%2f1.3054271&partnerID=40&md5=56c44063d775888394f0afce8b43ea27"

147. Gasperin A., Amat E., Martin J., Porti M., Nafria M., Paccagnella A.,"Peculiar characteristics of nanocrystal memory cells programming window",2009,"Journal of Vacuum Science and Technology B: Microelectronics and Nanometer Structures","27","1",,"512","516",,"10.1116/1.3025854","https://www.scopus.com/inward/record.uri?eid=2-s2.0-59949097132&doi=10.1116%2f1.3025854&partnerID=40&md5=ad5ca8ddca419439a37b691d2acaa314"

148. Porti M., Nafria N., Gerardin S., Aymerich X., Cester A., Paccagnella A., Ghidini G.,"Implanted and irradiated Si O2 Si structure electrical properties at the nanoscale",2009,"Journal of Vacuum Science and Technology B: Microelectronics and Nanometer Structures","27","1",,"421","425",,"10.1116/1.3043475","https://www.scopus.com/inward/record.uri?eid=2-s2.0-59949090119&doi=10.1116%2f1.3043475&partnerID=40&md5=b8e30a252f553ad69bd0b233698baf04"

149. Cellere G., Gerardin S., Bagatin M., Paccagnella A., Visconti A., Bonanomi M., Beltrami S., Harboe-Sørensen R., Virtanen A., Roche P.,"Can atmospheric neutrons induce soft errors in floating gate memories?",2009,"IEEE Electron Device Letters","30","2",,"178","180",,"10.1109/LED.2008.2009885","https://www.scopus.com/inward/re

cord.uri?eid=2-s2.0-59649126912&doi=10.1109%2fLED.2008.2009885&partnerID=40&md5=25e04f00a27706ffb0a8f6c09721f920"

150. Atwood W.B., Abdo A.A., Ackermann M., Althouse W., Anderson B., Axelsson M., Baldini L., Ballet J., Band D.L., Barbiellini G., Bartelt J., Bastieri D., Baughman B.M., Bechtol K., Bédérède D., Bellardi F., Bellazzini R., Berenji B., Bignami G.F., Bisello D., Bissaldi E., Blandford R.D., Bloom E.D., Bogart J.R., Bonamente E., Bonnell J., Borgland A.W., Bouvier A., Bregeon J., Brez A., Brigida M., Bruel P., Burnett T.H., Busetto G., Caliandro G.A., Cameron R.A., Caraveo P.A., Carius S., Carlson P., Casandjian J.M., Cavazzuti E., Ceccanti M., Cecchi C., Charles E., Chekhtman A., Cheung C.C., Chiang J., Chipaux R., Cillis A.N., Ciprini S., Claus R., Cohen-Tanugi J., Condamoor S., Conrad J., Corbet R., Corucci L., Costamante L., Cutini S., Davis D.S., Decotigny D., Deklotz M., Dermer C.D., De Angelis A., Digel S.W., Do Couto E Silva E., Drell P.S., Dubois R., Dumora D., Edmonds Y., Fabiani D., Farnier C., Favuzzi C., Flath D.L., Fleury P., Focke W.B., Funk S., Fusco P., Gargano F., Gasparrini D., Gehrels N., Gentit F.-X., Germani S., Giebels B., Giglietto N., Giommi P., Giordano F., Glanzman T., Godfrey G., Grenier I.A., Grondin M.-H., Grove J.E., Guillemot L., Guiriec S., Haller G., Harding A.K., Hart P.A., Hays E., Healey S.E., Hirayama M., Hjalmarsdotter L., Horn R., Hughes R.E., Jóhannesson G., Johansson G., Johnson A.S., Johnson R.P., Johnson T.J., Johnson W.N., Kamae T., Katagiri H., Kataoka J., Kavelaars A., Kawai N., Kelly H., Kerr M., Klamra W., Knödlseder J., Kocian M.L., Komin N., Kuehn F., Kuss M., Landriu D., Latronico L., Lee B., Lee S.-H., Lemoine-Goumard M., Lionetto A.M., Longo F., Loparco F., Lott B., Lovellette M.N., Lubrano P., Madejski G.M., Makeev A., Marangelli B., Massai M.M., Mazziotta M.N., McEnery J.E., Menon N., Meurer C., Michelson P.F., Minuti M., Mirizzi N., Mitthumsiri W., Mizuno T., Moiseev A.A., Monte C., Monzani M.E., Moretti E., Morselli A., Moskalenko I.V., Murgia S., Nakamori T., Nishino S., Nolan P.L., Norris J.P., Nuss E., Ohno M., Ohsugi T., Omodei N., Orlando E., Ormes J.F., Paccagnella A., Paneque D., Panetta J.H., Parent D., Pearce M., Pepe M., Perazzo A., Pesce-Rollins M., Picozza P., Pieri L., Pinchera M., Piron F., Porter T.A., Poupard L., Rainò S., Rando R., Rapposelli E., Razzano M., Reimer A., Reimer O., Reposeur T., Reyes L.C., Ritz S., Rochester L.S., Rodriguez A.Y., Romani R.W., Roth M., Russell J.J., Ryde F., Sabatini S., Sadrozinski H.F.-W., Sanchez D., Sander A., Sapozhnikov L., Parkinson P.M.S., Scargle J.D., Schalk T.L., Scolieri G., Sgrò C., Share G.H., Shaw M., Shimokawabe T., Shrader C., Sierpowska-Bartosik A., Siskind E.J., Smith D.A., Smith P.D., Spandre G., Spinelli P., Starck J.-L., Stephens T.E., Strickman M.S., Strong A.W., Suson D.J., Tajima H., Takahashi H., Takahashi T., Tanaka T., Tenze A., Tether S., Thayer J.B., Thayer J.G., Thompson D.J., Tibaldo L., Tibolla O., Torres D.F., Tosti G., Tramacere A., Turri M., Usher T.L., Vilchez N., Vitale V., Wang P., Watters K., Winer B.L., Wood K.S., Ylinen T., Ziegler M.,"The large area telescope on the fermi gamma-ray space telescope mission",2009,"Astrophysical Journal","697","2",,"1071","1102",,"10.1088/0004-637X/697/2/1071","https://www.scopus.com/inward/record.uri?eid=2-s2.0-66649126398&doi=10.1088%2f0004-637X%2f697%2f2%2f1071&partnerID=40&md5=b3b4b56e923442ce55a6df49e664ce43"

151. Abdo A.A., Ackermann M., Ajello M., Ampe J., Anderson B., Atwood W.B., Axelsson M., Bagagli R., Baldini L., Ballet J., Barbiellini G., Bartelt J., Bastieri D., Baughman B.M., Bechtol K., Bédérède D., Bellardi F., Bellazzini R., Belli F., Berenji B., Bisello D., Bissaldi E., Bloom E.D., Bogaert G., Bogart J.R., Bonamente E., Borgland A.W., Bourgeois P., Bouvier A., Bregeon J., Brez A., Brigida M., Bruel P., Burnett T.H., Busetto G., Caliandro G.A., Cameron R.A., Campell M., Caraveo P.A., Carius S., Carlson P., Casandjian J.M., Cavazzuti E., Ceccanti M., Cecchi C., Charles E., Chekhtman A., Cheung C.C., Chiang J., Chipaux R., Cillis A.N., Ciprini S., Claus R., Cohen-Tanugi J., Condamoor S., Conrad J., Corbet R., Cutini S., Davis D.S., DeKlotz M., Dermer C.D., de Angelis A., de Palma F., Digel S.W., Dizon P., Dormody M., do Couto e Silva E., Drell P.S., Dubois R., Dumora D., Edmonds Y., Fabiani D., Farnier C., Favuzzi C., Ferrara E.C., Ferreira O., Fewtrell Z., Flath D.L., Fleury P., Focke W.B., Fouts K., Frailis M., Freytag D., Fukazawa Y., Funk S., Fusco P., Gargano F., Gasparrini D.,

Gehrels N., Germani S., Giebels B., Giglietto N., Giordano F., Glanzman T., Godfrey G., Goodman J., Grenier I.A., Grondin M.-H., Grove J.E., Guillemot L., Guiriec S., Hakimi M., Haller G., Hanabata Y., Hart P.A., Hascall P., Hays E., Huffer M., Hughes R.E., Jóhannesson G., Johnson A.S., Johnson R.P., Johnson T.J., Johnson W.N., Kamae T., Katagiri H., Kataoka J., Kavelaars A., Kelly H., Kerr M., Klamra W., Knödlseder J., Kocian M.L., Kuehn F., Kuss M., Latronico L., Lavalley C., Leas B., Lee B., Lee S.-H., Lemoine-Goumard M., Longo F., Loparco F., Lott B., Lovellette M.N., Lubrano P., Lung D.K., Madejski G.M., Makeev A., Marangelli B., Marchetti M., Massai M.M., May D., Mazzenga G., Mazziotta M.N., McEnery J.E., McGlynn S., Meurer C., Michelson P.F., Minuti M., Mirizzi N., Mitra P., Mitthumsiri W., Mizuno T., Moiseev A.A., Mongelli M., Monte C., Monzani M.E., Moretti E., Morselli A., Moskalenko I.V., Murgia S., Nelson D., Nilsson L., Nishino S., Nolan P.L., Nuss E., Ohno M., Ohsugi T., Omodei N., Orlando E., Ormes J.F., Ozaki M., Paccagnella A., Paneque D., Panetta J.H., Parent D., Pelassa V., Pepe M., Pesce-Rollins M., Picozza P., Pinchera M., Piron F., Porter T.A., Rainò S., Rando R., Rapposelli E., Raynor W., Razzano M., Reimer A., Reimer O., Reposeur T., Reyes L.C., Ritz S., Robinson S., Rochester L.S., Rodriguez A.Y., Romani R.W., Roth M., Ryde F., Sacchetti A., Sadrozinski H.F.-W., Saggini N., Sanchez D., Sander A., Sapozhnikov L., Saxton O.H., Saz Parkinson P.M., Sellerholm A., Sgrò C., Siskind E.J., Smith D.A., Smith P.D., Spandre G., Spinelli P., Starck J.-L., Stephens T.E., Strickman M.S., Strong A.W., Sugizaki M., Suson D.J., Tajima H., Takahashi H., Takahashi T., Tanaka T., Tenze A., Thayer J.B., Thayer J.G., Thompson D.J., Tibaldo L., Tibolla O., Torres D.F., Tosti G., Tramacere A., Turri M., Usher T.L., Vilchez N., Virmani N., Vitale V., Wai L.L., Waite A.P., Wang P., Winer B.L., Wood D.L., Wood K.S., Yasuda H., Ylinen T., Ziegler M.,"The on-orbit calibration of the Fermi Large Area Telescope",2009,"Astroparticle Physics","32","3-4",,"193","219",,"10.1016/j.astropartphys.2009.08.002","https://www.scopus.com/inward/record.uri?eid=2-s2.0-70449109153&doi=10.1016%2fj.astropartphys.2009.08.002&partnerID=40&md5=218a0847eb8b8d97996baa951db15d2d"

152. Gossner H., Paccagnella A.,"Characterization, reliability, and yield - ESD/Memory reliability",2008,"Technical Digest - International Electron Devices Meeting, IEDM",,, 4796687,"","",,"10.1109/IEDM.2008.4796687","https://www.scopus.com/inward/record.uri?eid=2-s2.0-64549145383&doi=10.1109%2fIEDM.2008.4796687&partnerID=40&md5=45a76cd8f0bec5b1fe9eb3fb3e1130ee"

153. Gasperin A., Paccagnella A., Ghidini G., Sebastiani A.,"Heavy ion irradiation effects on capacitors with SiO2 and ONO as dielectrics",2008,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5782761,"447","452",,"10.1109/RADECS.2008.5782761","https://www.scopus.com/inward/record.uri?eid=2-s2.0-79960651907&doi=10.1109%2fRADECS.2008.5782761&partnerID=40&md5=22d8f6973c0170f1d4c56000a8f833ca"

154. Silvestri M., Gerardin S., Paccagnella A., Ghidini G.,"Gate rupture in ultra-thin gate oxides irradiated with heavy ions",2008,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5782694,"107","112",,"10.1109/RADECS.2008.5782694","https://www.scopus.com/inward/record.uri?eid=2-s2.0-79960626633&doi=10.1109%2fRADECS.2008.5782694&partnerID=40&md5=3949f3af1c2da67f0a2f5f2390b41e93"

155. Silvestri M., Gerardin S., Paccagnella A., Faccio F.,"Degradation induced by X-Ray irradiation and channel Hot carrier stresses in 130-nm NMOSFETs with enclosed layout",2008,"IEEE Transactions on Nuclear Science","55","6", 4723782,"3216","3223",,"10.1109/TNS.2008.2006747","https://www.scopus.com/inward/record.u

ri?eid=2-s2.0-58849120963&doi=10.1109%2fTNS.2008.2006747&partnerID=40&md5=9476cdf9f73bd8e0729f314c113a9b5e"

156. Bagatin M., Cellere G., Gerardin S., Paccagnella A., Visconti A., Beltrami S.,"TID sensitivity of NAND Flash memory building blocks",2008,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5782680,"34","39",,"10.1109/RADECS.2008.5782680","https://www.scopus.com/inward/record.uri?eid=2-s2.0-79960633423&doi=10.1109%2fRADECS.2008.5782680&partnerID=40&md5=c49cc7d3d186df0acd932d51d0bba182"
157. Gasperin A., Paccagnella A., Schwank J.R., Vizkelethy G., Ottogalli F., Pellizzer F.,"Analysis of proton and heavy-ion irradiation effects on phase change memories with MOSFET and BJT selectors",2008,"IEEE Transactions on Nuclear Science","55","6", 4723720,"3189","3196",,"10.1109/TNS.2008.2007639","https://www.scopus.com/inward/record.uri?eid=2-s2.0-58849149912&doi=10.1109%2fTNS.2008.2007639&partnerID=40&md5=d03890e93425725f737009b22cad322c"
158. Griffoni A., Gerardin S., Meneghesso G., Paccagnella A., Simoen E., Put S., Claeys C.,"Microdose and breakdown effects induced by heavy ions on sub 32-nm triple-gate SOI FETs",2008,"IEEE Transactions on Nuclear Science","55","6", 4723722,"3182","3188",,"10.1109/TNS.2008.2007234","https://www.scopus.com/inward/record.uri?eid=2-s2.0-58849117161&doi=10.1109%2fTNS.2008.2007234&partnerID=40&md5=9068f052a96b781f2007eeddb374b488"
159. Bagatin M., Gerardin S., Paccagnella A., Andreani C., Gorini G., Pietropaolo A., Platt S.P., Frost C.D.,"Factors impacting the temperature dependence of soft errors in commercial SRAMs",2008,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5782693,"100","106",,"10.1109/RADECS.2008.5782693","https://www.scopus.com/inward/record.uri?eid=2-s2.0-79960621428&doi=10.1109%2fRADECS.2008.5782693&partnerID=40&md5=20a94153f6a55740dcb8eed8471acf72"
160. Bagatin M., Gerardin S., Cellere G., Paccagnella A., Visconti A., Beltrami S., Harboe-Sørensen R., Virtanen A.,"Key contributions to the cross section of NAND flash memories irradiated with heavy ions",2008,"IEEE Transactions on Nuclear Science","55","6", 4723775,"3302","3308",,"10.1109/TNS.2008.2007905","https://www.scopus.com/inward/record.uri?eid=2-s2.0-58849095010&doi=10.1109%2fTNS.2008.2007905&partnerID=40&md5=1939299dfdf3e268f55a21e469fd2120"
161. Griffoni A., Silvestri M., Gerardin S., Meneghesso G., Paccagnella A., Kaczer B., De Potter De Ten Broeck M., Verbeeck R., Nackaerts A.,"Dose enhancement due to interconnects in deep-submicron MOSFETs exposed to X-rays",2008,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5782758,"432","437",,"10.1109/RADECS.2008.5782758","https://www.scopus.com/inward/record.uri?eid=2-s2.0-79960627633&doi=10.1109%2fRADECS.2008.5782758&partnerID=40&md5=7f0f4d01de77ec00436977edbbfc8ded"
162. Cellere G., Paccagnella A., Visconti A., Beltrami S., Schwank J., Shaneyfelt M., Lambert D., Paillet P., Ferlet-Cavrois V., Baggio J., Harboe-Sorensen R., Blackmore E., Virtanen A., Fuochi

P.,"Direct evidence of secondary recoiled nuclei from high energy protons",2008,"IEEE Transactions on Nuclear Science","55","6", 4723746,"2904","2913",,"10.1109/TNS.2008.2007799","https://www.scopus.com/inward/record.uri?eid=2-s2.0-58849099600&doi=10.1109%2fTNS.2008.2007799&partnerID=40&md5=1fd692816d211b091084ce62a28f9a5b"

163. Cellere G., Gerardin S., Bagatin M., Paccagnella A., Visconti A., Bonanomi M., Beltrami S., Roche P., Gasiot G., Sørensen R.H., Virtanen A., Frost C., Fuochi P., Andreani C., Gorini G., Pietropaolo A., Platt S.,"Neutron-induced soft errors in advanced Flash memories",2008,"Technical Digest - International Electron Devices Meeting, IEDM",,, 4796693,"","",,"10.1109/IEDM.2008.4796693","https://www.scopus.com/inward/record.uri?eid=2-s2.0-64549090985&doi=10.1109%2fIEDM.2008.4796693&partnerID=40&md5=1aad327a8a3b91dadadcdb3487e500c7"
164. Manuzzato A., Gerardin S., Paccagnella A., Sterpone L., Violante M.,"On the static cross section of SRAM-based FPGAs",2008,"IEEE Radiation Effects Data Workshop",,, 4638622,"94","97",,"10.1109/REDW.2008.24","https://www.scopus.com/inward/record.uri?eid=2-s2.0-56349157158&doi=10.1109%2fREDW.2008.24&partnerID=40&md5=028327609fa8a30fd303e2307861bafe"
165. Battezzati N., Gerardin S., Manuzzato A., Paccagnella A., Rezgui S., Sterpone L., Violante M.,"On the evaluation of radiation-induced transient faults in flash-based FPGAs",2008,"Proceedings - 14th IEEE International On-Line Testing Symposium, IOLTS 2008",,, 4567075,"135","140",,"10.1109/IOLTS.2008.47","https://www.scopus.com/inward/record.uri?eid=2-s2.0-52049119497&doi=10.1109%2fIOLTS.2008.47&partnerID=40&md5=20ed7a53d007ee6990fdea416e427f66"
166. Cellere G., Paccagnella A., Visconti A., Bonanomi M., Harboe-Sørensen R., Virtanen A.,"Traces of errors due to single ion in floating gate memories",2008,"Proceedings - 2008 IEEE International Conference on Integrated Circuit Design and Technology, ICICDT",,, 4567285,"237","240",,"10.1109/ICICDT.2008.4567285","https://www.scopus.com/inward/record.uri?eid=2-s2.0-51849136860&doi=10.1109%2fICICDT.2008.4567285&partnerID=40&md5=d9c9d4878310d0f8dce2f28a0a456dbf"
167. Cellere G., Borgo M., De Toni A., Bandiera L., Santoni L., Biondato L., Paccagnella A., Lorenzelli L.,"Using a cell manipulation biochip to investigate toe adhesion characteristics of single mammalian cells",2008,"ULIS 2008 - 9th International Conference on ULtimate Integration of Silicon",,, 4527169,"183","186",,"10.1109/ULIS.2008.4527169","https://www.scopus.com/inward/record.uri?eid=2-s2.0-49049094682&doi=10.1109%2fULIS.2008.4527169&partnerID=40&md5=f0bc2ca6f5c9e49b583f079f986ae88b"
168. Silvestri M., Gerardin S., Paccagnella A., Faccio F., Gonella L.,"Channel hot carrier stress on irradiated 130-nm NMOSFETs",2008,"IEEE Transactions on Nuclear Science","55","4", 4636947,"1960","1967",,"10.1109/TNS.2008.2000771","https://www.scopus.com/inward/record.uri?eid=2-s2.0-53349101385&doi=10.1109%2fTNS.2008.2000771&partnerID=40&md5=debdbf8445336270009feb91a730b148"

169. Manuzzato A., Gerardin S., Paccagnella A., Sterpone L., Violante M.,"Effectiveness of TMR-based techniques to mitigate alpha-induced SEU accumulation in commercial SRAM-based FPGAs",2008,"IEEE Transactions on Nuclear Science","55","4", 4636890,"1968","1973",,"10.1109/TNS.2008.2000850","https://www.scopus.com/inward/record.uri?eid=2-s2.0-53349099275&doi=10.1109%2fTNS.2008.2000850&partnerID=40&md5=6fa078f577de61129d20678534fd7462"
170. Cellere G., Paccagnella A., Visconti A., Bonanomi M., Beltrami S., Harboe-Sørensen R., Virtanen A.,"Effect of ion energy on charge loss from floating gate memories",2008,"IEEE Transactions on Nuclear Science","55","4", 4636910,"2042","2047",,"10.1109/TNS.2008.2000779","https://www.scopus.com/inward/record.uri?eid=2-s2.0-53349176926&doi=10.1109%2fTNS.2008.2000779&partnerID=40&md5=106c1de7030efba423fcbc023655df71"
171. Gasperin A., Wrachien N., Paccagnella A., Ottogalli F., Corda U., Fuochi P., Lavalle M.,"Total ionizing dose effects on 4 Mbit phase change memory arrays",2008,"IEEE Transactions on Nuclear Science","55","4", 4636883,"2090","2097",,"10.1109/TNS.2008.920425","https://www.scopus.com/inward/record.uri?eid=2-s2.0-53349171479&doi=10.1109%2fTNS.2008.920425&partnerID=40&md5=0e95f1b346b3d6d6357138e7cfead8e8"
172. Vassanelli S., Bandiera L., Borgo M., Cellere G., Santoni L., Bersani C., Salamon M., Zaccolo M., Lorenzelli L., Girardi S., Maschietto M., Dal Maschio M., Paccagnella A.,"Space and time-resolved gene expression experiments on cultured mammalian cells by a single-cell electroporation microarray",2008,"New Biotechnology","25","1",,"55","67",,"10.1016/j.nbt.2008.03.002","https://www.scopus.com/inward/record.uri?eid=2-s2.0-44049097920&doi=10.1016%2fj.nbt.2008.03.002&partnerID=40&md5=a4f239fbb072f4b2dc6bc52a35f1c9db"
173. Andreani C., Pietropaolo A., Salsano A., Gorini G., Tardocchi M., Paccagnella A., Gerardin S., Frost C.D., Ansell S., Platt S.P.,"Facility for fast neutron irradiation tests of electronics at the ISIS spallation neutron source",2008,"Applied Physics Letters","92","11", 114101,"","",,"10.1063/1.2897309","https://www.scopus.com/inward/record.uri?eid=2-s2.0-41049103493&doi=10.1063%2f1.2897309&partnerID=40&md5=944e14510f9b1c8123d2dafdd4c4bfc6"
174. Cellere G., Gerardin S., Paccagnella A.,"Defects in thin and ultrathin silicon dioxides",2008,"Defects in Microelectronic Materials and Devices",,,,"497","532",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-79960056714&partnerID=40&md5=2f756f5f529e8ae4f7d371f8b110704d"
175. Chatrchyan S., Hmayakyan G., Khachatryan V., Sirunyan A.M., Adam W., Bauer T., Bergauer T., Bergauer H., Dragicevic M., Erö J., Friedl M., Frühwirth R., Ghete V.M., Glaser P., Hartl C., Hoermann N., Hrubec J., Hänsel S., Jeitler M., Kastner K., Krammer M., De Abril I.M., Markytan M., Mikulec I., Neuherz B., Nöbauer T., Oberegger M., Padrta M., Pernicka M., Porth P., Rohringer H., Schmid S., Schreiner T., Stark R., Steininger H., Strauss J., Taurok A., Uhl D., Waltenberger W., Walzel G., Widl E., Wulz C.-E., Petrov V., Prosolovich V., Chekhovsky V., Dvornikov O., Emeliantchik I., Litomin A., Makarenko V., Marfin I., Mossolov V., Shumeiko N., Solin A., Stefanovitch R., Gonzalez S.J., Tikhonov A., Fedorov A., Korzhik M., Missevitch O., Zuyeuski R., Beaumont W., Cardaci M., De Langhe E., De Wolf E.A., Delmeire E., Ochesanu S., Tasevsky M., Van Mechelen P., D'Hondt J., De Weirdt S., Devroede O., Goorens R., Hannaert S., Heyninck J., Maes J., Mozer M.U., Tavernier S.,

Van Doninck W., Van Lancker L., Van Mulders P., Villella I., Wastiels C., Yu C., Bouhali O., Charaf O., Clerbaux B., De Harenne P., De Lentdecker G., Dewulf J.P., Elgammal S., Gindroz R., Hammad G.H., Mahmoud T., Neukermans L., Pins M., Pins R., Rugovac S., Stefanescu J., Sundararajan V., Velde C.V., Vanlaer P., Wickens J., Tytgat M., Assouak S., Bonnet J.L., Bruno G., Caudron J., De Callatay B., De Jeneret D.F.J., De Visscher S., Demin P., Favart D., Felix C., Florins B., Forton E., Giammanco A., Grégoire G., Jonckman M., Kcira D., Keutgen T., Lemaitre V., Michotte D., Militaru O., Ovyn S., Pierzchala T., Piotrzkowski K., Roberfroid V., Rouby X., Schul N., Van Der Aa O., Beliy N., Daubie E., Herquet P., Alves G., Pol M.E., Souza M.H.G., Vaz M., Damiao D.D.J., Oguri V., Santoro A., Sznajder A., Gregores E.D.M., Iope R.L., Novaes S.F., Tomei T., Anguelov T., Antchev G., Atanasov I., Damgov J., Darmenov N., Dimitrov L., Genchev V., Iaydjiev P., Marinov A., Piperov S., Stoykova S., Sultanov G., Trayanov R., Vankov I., Cheshkov C., Dimitrov A., Dyulendarova M., Glushkov I., Kozhuharov V., Litov L., Makariev M., Marinova E., Markov S., Mateev M., Nasteva I., Pavlov B., Petev P., Petkov P., Spassov V., Toteva Z., Velev V., Verguilov V., Bian J.G., Chen G.M., Chen H.S., Chen M., Jiang C.H., Liu B., Shen X.Y., Sun H.S., Tao J., Wang J., Yang M., Zhang Z., Zhao W.R., Zhuang H.L., Ban Y., Cai J., Ge Y.C., Liu S., Liu H.T., Liu L., Qian S.J., Wang Q., Xue Z.H., Yang Z.C., Ye Y.L., Ying J., Li P.J., Liao J., Xue Z.L., Yan D.S., Yuan H., Montoya C.A.C., Sanabria J.C., Godinovic N., Puljak I., Soric I., Antunovic Z., Dzelalija M., Marasovic K., Brigljevic V., Kadija K., Morovic S., Fereos R., Nicolaou C., Papadakis A., Ptochos F., Razis P.A., Tsiakkouri D., Zinonos Z., Hektor A., Kadastik M., Kannike K., Lippmaa E., Müntel M., Raidal M., Rebane L., Aarnio P.A., Anttila E., Banzuzi K., Bulteau P., Czellar S., Eiden N., Eklund C., Engstrom P., Heikkinen A., Honkanen A., Härkönen J., Karimäki V., Katajisto H.M., Kinnunen R., Klem J., Kortesmaa J., Kotamäki M., Kuronen A., Lampén T., Lassila-Perini K., Lefébure V., Lehti S., Lindén T., Luukka P.R., Michal S., Brigido F.M., Mäenpää T., Nyman T., Nystén J., Pietarinen E., Skog K., Tammi K., Tuominen E., Tuominiemi J., Ungaro D., Vanhala T.P., Wendland L., Williams C., Iskanius M., Korpela A., Polese G., Tuuva T., Bassompierre G., Bazan A., David P.Y., Ditta J., Drobychev G., Fouque N., Guillaud J.P., Hermel V., Karneyeu A., Le Flour T., Lieunard S., Maire M., Mendiburu P., Nedelec P., Peigneux J.P., Schneegans M., Sillou D., Vialle J.P., Anfreville M., Bard J.P., Besson P., Bougamont E., Boyer M., Bredy P., Chipaux R., Dejardin M., Denegri D., Descamps J., Fabbro B., Faure J.L., Ganjour S., Gentit F.X., Givernaud A., Gras P., De Monchenault G.H., Jarry P., Jeanney C., Kircher F., Lemaire M.C., Lemoigne Y., Levesy B., Locci E., Lottin J.P., Mandjavidze I., Mur M., Pansart J.P., Payn A., Rander J., Reymond J.M., Rolquin J., Rondeaux F., Rosowsky A., Rousse J.Y.A., Sun Z.H., Tartas J., Van Lysebetten A., Venault P., Verrecchia P., Anduze M., Badier J., Baffioni S., Bercher M., Bernet C., Berthon U., Bourotte J., Busata A., Busson P., Cerutti M., Chamont D., Charlot C., Collard C., Debraine A., Decotigny D., Dobrzynski L., Ferreira O., Geerebaert Y., Gilly J., Gregory C., Riveros L.G., Haguenauer M., Karar A., Koblitz B., Lecouturier D., Mathieu A., Milleret G., Miné P., Paganini P., Poilleux P., Pukhaeva N., Regnault N., Romanteau T., Semeniouk I., Sirois Y., Thiebaux C., Vanel J.C., Zabi A., Agram J.L., Albert A., Anckenmann L., Andrea J., Anstotz F., Bergdolt A.M., Berst J.D., Blaes R., Bloch D., Brom J.M., Cailleret J., Charles F., Christophel E., Claus G., Coffin J., Colledani C., Croix J., Dangelser E., Dick N., Didierjean F., Drouhin F., Dulinski W., Ernenwein J.P., Fang R., Fontaine J.C., Gaudiot G., Geist W., Gelé D., Goeltzenlichter T., Goerlach U., Graehling P., Gross L., Hu C.G., Helleboid J.M., Henkes T., Hoffer M., Hoffmann C., Hosselet J., Houchu L., Hu Y., Huss D., Illinger C., Jeanneau F., Juillot P., Kachelhoffer T., Kapp M.R., Kettunen H., Ayat L.L., Le Bihan A.C., Lounis A., Maazouzi C., Mack V., Majewski P., Mangeol D., Michel J., Moreau S., Olivetto C., Pallarès A., Patois Y., Prala- vorio P., Racca C., Riahi Y., Ripp-Baudot I., Schmitt P., Schunck J.P., Schuster G., Schwaller B., Sigward M.H., Sohler J.L., Speck J., Strub R., Todorov T., Turchetta R., Van Hove P., Vintache D., Zghiche A., Ageron M., Augustin J.E., Baty C., Baulieu G., Bedjidian M., Blaha J., Bonnevaux A., Boudoul G., Brunet P., Chabanat E., Chabert E.C., Chierici R., Chorowicz V., Combaret C., Contardo D., Negra R.D., Depasse P., Drapier O., Dupanloup M., Dupasquier T., El Mamouni H., Estre N., Fay J., Gascon S., Giraud N., Girerd C., Guillot G., Haroutunian R., Ille B., Lethuillier M., Lumb N., Martin C., Mathez H., Maurelli G., Muanza S., Pangaud P., Perries S., Ravat O., Schibler E., Schirra F., Smadja G., Tissot S., Trocme B., Vanzetto S., Walder J.P., Bagaturia Y., Mjavia D., Mzhavia A., Tsamalaidze Z., Roinishvili V., Adolphi R., Anagnostou G., Brauer R., Braunschweig W., Esser H., Feld L., Karpinski W., Khomich A., Klein K., Kukulies C., Lübelsmeyer K., Olzem J., Ostaptchouk A., Pan-doulas D., Pierschel G., Raupach F., Schael S., Von Dratzig A.S., Schwering G., Siedling R., Thomas M., Weber M., Wittmer B., Wlochal M., Adamczyk F., Adolf A., Altenhöfer G., Bechstein S., Bethke S., Biallass P., Biebel O., Bontenackels M., Bosseler K., Böhm A., Erdmann M., Faissner H., Fehr B., Fesefeldt H., Fetchenhauer G., Frangenheim J., Frohn J.H., Grooten J., Hebbeker T., Hermann S., Hermens E., Hilgers G., Hoepfner K., Hof C., Jacobi E., Kappler S., Kirsch M., Kreuzer P., Kupper R., Lampe H.R., Lanske D., Mameghani R., Meyer A., Meyer S., Moers T., Müller E., Pahlke R., Philipps B., Rein D., Reithler H., Reuter W., Rütten P., Schulz S., Schwarthoff H., Sobek W., Sowa M., Stapelberg T., Szczesny H., Teykal H., Teyssier D., Tomme H., Tomme W., Tonutti M., Tsigenov O., Tutas J., Vandenhirtz J., Wagner H., Wegner M., Zeidler C., Beissel F., Davids M., Duda M., Flügge G., Giffels M., Hermanns T., Heydhausen D., Kalinin S., Kasselmann S., Kaussen G., Kress T., Linn A., Nowack A., Perchalla L., Poettgens M., Pooth O., Sauerland P., Stahl A., Tornier D., Zoeller M.H., Behrens U., Borras K., Flossdorf A., Hatton D., Hegner B., Kasemann M., Mankel R., Meyer A., Mnich J., Rosemann C., Youngman C., Zeuner W.D., Bechtel F., Buhmann P., Butz E., Flucke G., Hamdorf R.H., Holm U., Klanner R., Pein U., Schirm N., Schleper P., Steinbrück G., Van Staa R., Wolf R., Atz B., Barvich T., Blüm P., Boegelspacher F., Bol H., Chen Z.Y., Chowdhury S., De Boer W., Dehm P., Dirkes G., Fahrer M., Felzmann U., Frey M., Furgeri A., Gregoriev E., Hartmann F., Hauler F., Heier S., Kärcher K., Ledermann B., Mueller S., Müller Th., Neuberger D., Piasecki C., Quast G., Rabbertz K., Sabellek A., Scheurer A., Schilling F.P., Simonis H.J., Skiba A., Steck P., Theel A., Thümmel W.H., Trunov A., Vest A., Weiler T., Weiser C., Weseler S., Zhukov V., Barone M., Daskalakis G., Dimitriou N., Fanourakis G., Filippidis C., Geralis T., Kalfas C., Karafasoulis K., Koimas A., Kyriakis A., Kyriazopoulou S., Loukas D., Markou A., Markou C., Mastroyiannopoulos N., Mavrommatis C., Mousa J., Papadakis I., Petrakou E., Siotis I., The-ofilatos K., Tzamarias S., Vayaki A., Vermisoglou G., Zachariadou A., Gouskos L., Karapostoli G., Katsas P., Panagiotou A., Papadimitropoulos C., Aslanoglou X., Evangelou I., Kokkas P., Manthos N., Papadopoulos I., Triantis F.A., Bencze G., Boldizsar L., Debreczeni G., Hajdu C., Hidas P., Horvath D., Kovesarki P., Laszlo A., Odor G., Patay G., Sikler F., Veres G., Vesztergombi G., Zalan P., Fenyvesi A., Imrek J., Molnar J., Novak D., Palinkas J., Szekely G., Beni N., Kapusi A., Marian G., Radics B., Raics P., Szabo Z., Szillasi Z., Trocsanyi Z.L., Zilizi G., Bawa H.S., Beri S.B., Bhandari V., Bhatnagar V., Kaur M., Kohli J.M., Kumar A., Singh B., Singh J.B., Arora S., Bhattacharya S., Chatterji S., Chauhan S., Choudhary B.C., Gupta P., Jha M., Ranjan K., Shivpuri R.K., Srivastava A.K., Choudhury R.K., Dutta D., Ghodgaonkar M., Kailas S., Kataria S.K., Mohanty A.K., Pant L.M., Shukla P., Topkar A., Aziz T., Banerjee S., Bose S., Chendvankar S., Deshpande P.V., Guchait M., Gurtu A., Maity M., Majumder G., Mazumdar K., Nayak A., Patil M.R., Sharma S., Sudhakar K., Acharya B.S., Banerjee S., Bheesette S., Dugad S., Kalmani S.D., Lakkireddi V.R., Mondal N.K., Panyam N., Verma P., Arfaei H., Hashemi M., Najafabadi M.M., Moshaii A., Mehdiabadi S.P., Felcini M., Grunewald M., Abadjiev K., Abbrescia M., Barbone L., Cariola P., Chiumarulo F., Clemente A., Colaleo A., Creanza D., De Filippis N., De Palma M., De Robertis G., Donvito G., Ferorelli R., Fiore L., Franco M., Giordano D., Guida R., Iaselli G., Lacalamita N., Loddo F., Maggi G., Maggi M., Manna N., Marangelli B., Mennea M.S., My S., Natali S., Nuzzo S., Papagni G., Pinto C., Pom- pili A., Pugliese G., Ranieri A., Romano F., Roselli G., Sala G., Selvaggi G., Silvestris L., Tempesta P., Trentadue R., Tupputi S., Zito G., Abbiendi G., Bacchi W., Battilana C., Benvenuti A.C., Boldini M., Bonacorsi D., Braibant-Giacomelli S., Cafaro V.D., Capiluppi P., Castro A., Cavallo F.R., Ciocca C., Codispoti G., Cuffiani M., D'Antone I., Dallavalle G.M., Fabbri F., Fanfani A., Finelli S., Giacomelli P., Giordano V., Giunta M., Grandi C., Guerzoni M., Guiducci L., Marcellini S., Masetti G., Montanari A., Navarria F.L., Odorici F., Paolucci A., Pellegrini G., Perrotta A., Rossi A.M., Rovelli T., Siroli G.P., Torromeo G., Travaglini R., Veronese G.P., Albergo S., Chiorboli M., Costa S., Galanti M., Rotondo G., Giudice N., Guardone N., Noto F., Potenza R., Saizu M.A., Salemi G., Sutera C., Tricomi A., Tuve C., Bellucci L., Brianzi M., Broccolo G., Catacchini E., Ciulli V., Civinini C., D'Alessandro R., Focardi E., Frosali S., Genta C., Landi G., Lenzi P., Macchiolo A., Maletta F., Manolescu F., Marchettini C., Masetti L., Mersi S., Meschini M., Minelli C., Paoletti S., Parrini G., Scarlini E., Sguazzoni G., Benussi L., Bertani M., Bianco S., Caponero M., Colonna D., Daniello L., Fabbri F., Felli F., Giardoni M., La Monaca A., Ortenzi B., Pallotta M., Paolozzi A., Paris C., Passamonti L., Pier-luigi D., Ponzio B., Pucci C., Russo A., Saviano G., Fabbricatore P., Farinon S., Greco M., Musenich R., Badoer S., Berti L., Biasotto M., Fantinel S., Frizziero E., Gastaldi U., Gulmini M., Lelli F., Maron G., Squizzato S., Toniolo N., Traldi S., Banfi S., Bertoni R., Bonesini M., Carbone L., Cerati G.B., Chignoli F., D'Angelo P., De Min A., Dini P., Farina F.M., Ferri F., Govoni P., Magni S., Malberti M., Malvezzi S., Mazza R., Menasce D., Miccio V., Moroni L., Negri P., Paganoni M., Pedrini D., Pullia A., Ragazzi S., Redaelli N., Rovere M., Sala L., Sala S., Salerno R., De Fatis T.T., Tancini V., Taroni S., Boiano A., Cassese F., Cassese C., Cimmino A., D'Aquino B., Lista L., Lomidze D., Noli P., Paolucci P., Passeggio G., Piccolo D., Roscilli L., Sciacca C., Vanzanella A., Azzi P., Bacchetta N., Barcellan L., Bellato M., Benettoni M., Bisello D., Borsato E., Can-delori A., Carlin R., Castellani L., Checchia P., Ciano L., Colombo A., Conti E., Da Rold M., Dal Corso F., De Giorgi M., De Mattia M., Dorigo T., Dosselli U., Fanin C., Galet G., Gas-parini F., Gasparini U., Giraldo A., Giubilato P., Gonella F., Gresele A., Griggio A., Guaita P., Kaminskiy A., Karaevskii S., Khomenkov V., Kostylev D., Lacaprara S., Lazzizzera I., Lippi I., Loreti M., Margoni M., Martinelli R., Mattiazzo S., Mazzucato M., Meneguzzo A.T., Modenese L., Montecassiano F., Neviani A., Nigro M., Paccagnella A., Pantano D., Parenti A., Passaseo M., Pedrotta R., Pegoraro M., Rampazzo G., Reznikov S., Ronchese P., SDaponte A.A., Sartori P., Stavitskiy I., Tessaro M., Torassa E., Triossi A., Vanini S., Ventura S., Ventura L., Verlato M., Zago M., Zatti F., Zotto P., Zumerle G., Baesso P., Belli G., Berzano U., Bricola S., Grelli A., Musitelli G., Nardò R., Necchi M.M., Pagano D., Ratti S.P., Riccardi C., Torre P., Vicini A., Vitulo P., Viviani C., Aisa D., Aisa S., Ambroglini F., Angarano M.M., Babucci E., Benedetti D., Biasini M., Bilei G.M., Bizzaglia S., Brunetti M.T., Caponeri B., Checcucci B., Covarelli R., Dinu N., Fanò L., Farnesini L., Giorgi M., Lariccia P., Mantovani G., Moscatelli F., Passeri D., Piluso A., Placidi P., Postolache V., Santinelli R., Santocchia A., Servoli L., Spiga D., Azzurri P., Bagliesi G., Balestri G., Basti A., Bellazzini R., Benucci L., Bernardini J., Berretta L., Bianucci S., Boccali T., Bocci A., Borrello L., Bosi F., Bracci F., Brez A., Calzolari F., Castaldi R., Cazzola U., Ceccanti M., Cecchi R., Cerri C., Cucoanes A.S., Dell'Orso R., Dobur D., Dutta S., Fiori F., Foà L., Gaggelli A., Gennai S., Giassi A., Giusti S., Kartashov D., Kraan A., Latronico L., Ligabue F., Linari S., Lomtadze T., Lungu G.A., Magazzu G., Mammini P., Mariani F., Martinelli G., Massa M., Messineo A., Moggi A., Palla F., Palmonari F., Petragnani G., Petrucciani G., Profeti A., Raffaelli F., Rizzi D., Sanguinetti G., Sarkar S., Segneri G., Sentenac D., Serban A.T., Slav A., Spagnolo P., Spandre G., Tenchini R., Tolaini S., Tonelli G., Venturi A., Verdini P.G., Vos M., Zaccarelli L., Baccaro S., Barone L., Bartoloni A., Borgia B., Capradossi G., Cavallari F., Cecilia A., D'Angelo D., Dafinei I., Del Re D., Di Marco E., Diemoz M., Ferrara G., Gargiulo C., Guerra S., Iannone M., Longo E., Montecchi M., Nuccetelli M., Organtini G., Palma A., Paramatti R., Pellegrino F., Rahatlou S., Rovelli C., Tehrani F.S., Zullo A., Alampi G., Amapane N., Arcidiacono R., Argiro S., Arneodo M., Bellan R., Benotto F., Biino C., Bolognesi S., Borgia M.A., Botta C., Brasolin A., Cartiglia N., Castello R., Cerminara G., Cirio R., Cordero M., Costa M., Dattola D., Daudo F., Dellacasa G., Demaria N., Dughera G., Dumitrache F., Farano R., Ferrero G., Filoni E., Kostyleva G., Larsen H.E., Mariotti C., Marone M., Maselli S., Menichetti E., Mereu P., Migliore E., Mila G., Monaco V., Musich M., Nervo M., Obertino M.M., Panero R., Parussa A., Pastrone N., Peroni C., Petrillo G., Romero A., Ruspa M., Sacchi R., Scalise M., Solano A., Staiano A., Trapani P.P., Trocino D., Vaniev V., Pereira A.V., Zampieri A., Belforte S., Cossutti F., Ricca G.D., Gobbo B., Kavka C., Penzo A., Kim Y.E., Nam S.K., Kim D.H., Kim G.N., Kim J.C., Kong D.J., Ro S.R., Son D.C., Park S.Y., Kim Y.J., Kim J.Y., Lim I.T., Pac M.Y., Lee S.J., Jung S.Y., Rhee J.T., Ahn S.H., Hong B.S., Jeng Y.K., Kang M.H., Kim H.C., Kim J.H., Kim T.J., Lee K.S., Lim J.K., Moon D.H., Park I.C., Park S.K., Ryu M.S., Sim K.-S., Son K.J., Hong S.J., Choi Y.I., Valdez

H.C., Hernandez A.S., Moreno S.C., Pineda A.M., Aerts A., Van der Stok P., Weffers H., Allfrey P., Gray R.N.C., Hashimoto M., Krofcheck D., Bell A.J., Rodrigues N.B., Butler P.H., Churchwell S., Knegjens R., Whitehead S., Williams J.C., Aftab Z., Ahmad U., Ahmed I., Ahmed W., Asghar M.I., Asghar S., Dad G., Hafeez M., Hoorani H.R., Hussain I., Hussain N., Iftikhar M., Khan M.S., Mehmood K., Osman A., Shahzad H., Zafar A.R., Ali A., Bashir A., Jan A.M., Kamal A., Khan F., Saeed M., Tanwir S., Zafar M.A., Blocki J., Cyz A., Gladysz-Dziadus E., Mikocki S., Rybczynski M., Turnau J., Wlodarczyk Z., Zychowski P., Bunkowski K., Cwiok M., Czyrkowski H., Dabrowski R., Dominik W., Doroba K., Kalinowski A., Kierzkowski K., Konecki M., Krolikowski J., Kudla I.M., Pietrusinski M., Pozniak K., Zabolotny W., Zych P., Gokieli R., Goscilo L., Górski M., Nawrocki K., Traczyk P., Wrochna G., Zalewski P., Pozniak K.T., Romaniuk R., Zabolotny W.M., Alemany-Fernandez R., Almeida C., Almeida N., Vila Verde A.S.A., Monteiro T.B., Bluj M., Silva S.D.M., Tinoco Mendes A.D., Ferreira M.F., Gallinaro M., Husejko M., Jain A., Kazana M., Musella P., Nobrega R., Silva J.R.D., Ribeiro P.Q., Santos M., Silva P., Silva S., Teixeira I., Teixeira J.P., Varela J., Varner G., Vaz Cardoso N., Altsybeev I., Babich K., Belkov A., Belotelov I., Bunin P., Chesnevskaya S., Elsha V., Er-shov Y., Filozova I., Finger M., Finger M., Golunov A., Golutvin I., Gorbounov N., Gramenitski I., Kalagin V., Kamenev A., Karjavin V., Khabarov S., Khabarov V., Kiryushin Y., Konoplyanikov V., Korenkov V., Kozlov G., Kurenkov A., Lanev A., Lysiakov V., Malakhov A., Melnitchenko I., Mitsyn V.V., Moisenz K., Moisenz P., Movchan S., Nikonov E., Oleynik D., Palichik V., Perelygin V., Petrosyan A., Rogalev E., Samsonov V., Savina M., Semenov R., Sergeev S., Shmatov S., Shulha S., Smirnov V., Smolin D., Tcheremoukhine A., Teryaev O., Tikhonenko E., Urkinbaev A., Vasil'ev S., Vishnevskiy A., Volodko A., Zamiatin N., Zarubin A., Zarubin P., Zubarev E., Bondar N., Gavrikov Y., Golovtsov V., Ivanov Y., Kim V., Kozlov V., Lebedev V., Makarenkov G., Moroz F., Neustroev P., Obrant G., Orishchin E., Petrunin A., Shcheglov Y., Shchetkovskiy A., Sknar V., Skorobogatov V., Smirnov I., Sulimov V., Tarakanov V., Uvarov L., Vavilov S., Velichko G., Volkov S., Vorobyev A., Chmelev D., Druzhkin D., Ivanov A., Kudinov V., Logatchev O., Onishchenko S., Orlov A., Sakharov V., Smetannikov V., Tikhomirov A., Zavodthikov S., Andreev Yu., Anisimov A., Duk V., Gninenko S., Golubev N., Gorbunov D., Kirsanov M., Krasnikov N., Matveev V., Pashenkov A., Pastsyak A., Postoev V.E., Sadovski A., Skassyrskaia A., Solovey A., Solovey A., Soloviev D., Toropin A., Troitsky S., Alekhin A., Baldov A., Epshteyn V., Gavrilov V., Ilina N., Kaftanov V., Karpishin V., Kiselevich I., Kolosov V., Kossov M., Krokhotin A., Kuleshov S., Oulianov A., Pozdnyakov A., Safronov G., Semenov S., Stepanov N., Stolin V., Vlasov E., Zaytsev V., Boos E., Dubinin M., Dudko L., Ershov A., Eyyubova G., Gribushin A., Ilyin V., Klyukhin V., Kodolova O., Kruglov N.A., Kryukov A., Lokhtin I., Malinina L., Mikhaylin V., Petrushanko S., Sarycheva L., Savrin V., Shamardin L., Sherstnev A., Snigirev A., Teplov K., Vardanyan I., Fomenko A.M., Konovalova N., Kozlov V., Lebedev A.I., Lvova N., Rusakov S.V., Terkulov A., Abramov V., Akimenko S., Artamonov A., Ashimova A., Azhgirey I., Bitioukov S., Chikilev O., Datsko K., Filine A., Godizov A., Goncharov P., Grishin V., Inyakin A., Kachanov V., Kalinin A., Khmelnikov A., Konstantinov D., Korablev A., Krychkine V., Krinitsyn A., Levine A., Lobov I., Lukanin V., Mel'nik Y., Molchanov V., Petrov V., Petukhov V., Pikalov V., Ryazanov A., Ryutin R., Shelikhov V., Skvortsov V., Slabospitsky S., Sobol A., Sytine A., Talov V., Tourtchanovitch L., Troshin S., Tyurin N., Uzunian A., Volkov A., Zelepoukine S., Lukyanov V., Mamaeva G., Prilutskaya Z., Rumyantsev I., Sokha S., Tataurschikov S., Vasilyev I., Adzic P., Anicin I., Djordjevic M., Jovanovic D., Maletic D., Puzovic J., Smiljkovic N., Navarrete E.A., Aguilar-Benitez M., Munoz J.A., Vega J.M.A., Alberdi J., Maestre J.A., Martin M.A., Arce P., Barcala J.M., Berdugo J., Ramos C.L.B., Lazaro C.B., Bejar C., Calvo E., Cerrada M., Llatas C., Catalán J.J.C., Colino N., Daniel M., Cruz B.D.L., Peris A.D., Bedoya C.F., Ferrando A., Fouz M.C., Ferrero D.F., Romero J.G., Garcia-Abia P., Lopez O.G., Hernandez J.M., Josa I., Marin J., Merino G., Molinero A., Navarrete J.J., Oller J.C., Pelayo J.P., Sanchez J.C.P., Ramirez J., Romero L., Munoz C.V., Willmott C., Yuste C., Albajar C., De Trocóniz J.F., Jimenez I., Macias R., Teixeira R.F., Cuevas J., Caballero I.G., Lopez-Garcia J., Sordo H.N., Garcia J.M.V., Cabrillo I.J., Calderon A., Fernandez D.C., Merino I.D., Menendez J.F., Campderros J.D., Fernandez M., Figueroa C., Moral

L.A.G., Gomez G., Munt F.G.C., Sanchez J.G., Suarez R.G., Jorda C., Pardo P.L., Garcia A.L., Virto A.L., Marco J., Marco R., Rivero C.M., Ruiz del Arbol P.M., Matorras F., Fernandez P.O., Revuelta A.P., Rodrigo T., Gonzalez D.R., Jimeno A.R., Scodellaro L., Sanudo M.S., Vila I., Cortabitarte R.V., Barbero M., Goldin D., Henrich B., Tauscher L., Vlachos S., Wadhwa M., Abbaneo D., Abbas S.M., Ahmed I., Akhtar S., Akhtar M.I., Albert E., Alidra M., Ashby S., Aspell P., Auffray E., Baillon P., Ball A., Bally S.L., Bangert N., Barillère R., Barney D., Beauceron S., Beaudette F., Benelli G., Benetta R., Benichou J.L., Bialas W., Bjorkebo A., Blechschmidt D., Bloch C., Bloch P., Bonacini S., Bos J., Bosteels M., Boyer V., Branson A., Breuker H., Bruneliere R., Buchmuller O., Campi D., Camporesi T., Caner A., Cano E., Carrone E., Cattai A., Chatelain J.P., Chauvey M., Christiansen T., Ciganek M., Cittolin S., Cogan J., Garcia A.C., Cornet H., Corrin E., Corvo M., Cucciarelli S., Curé B., D'Enterria D., De Roeck A., De Visser T., Delaere C., Delattre M., Deldicque C., Delikaris D., Deyrail D., Di Vincenzo S., Domeniconi A., Dos Santos S., Duthion G., Edera L.M., Elliott-Peisert A., Eppard M., Fanzago F., Favre M., Foeth H., Folch R., Frank N., Fratianni S., Freire M.A., Frey A., Fucci A., Funk W., Gaddi A., Gagliardi F., Gastal M., Gateau M., Gayde J.C., Gerwig H., Ghezzi A., Gigi D., Gill K., Giolo-Nicollerat A.S., Girod J.P., Glege F., Glessing W., Garrido R.G.-R., Goudard R., Grabit R., Grillet J.P., Llamas P.G., Mlot E.G., Gutleber J., Hall-wilton R., Hammarstrom R., Hansen M., Harvey J., Herve A., Hill J., Hoffmann H.F., Holzner A., Honma A., Hufnagel D., Huhtinen M., Ilie S.D., Innocente V., Jank W., Janot P., Jarron P., Jeanrenaud M., Jouvel P., Kerkach R., Kloukinas K., Kottelat L.J., Labbe J.C., Lacroix D., Lagrue X., Lasseur C., Laure E., Laurens J.F., Lazeyras P., Le Goff J.M., Lebeau M., Lecoq P., Lemeilleur F., Lenzi M., Leonardo N., Leonidopoulos C., Letheren M., Liendl M., Limia-Conde F., Linssen L., Ljuslin C., Lofstedt B., Loos R., Perez J.A.L., Lourenco C., Lyonnet A., Machard A., Mackenzie R., Magini N., Maire G., Malgeri L., Malina R., Mannelli M., Marchioro A., Martin J., Meijers F., Meridiani P., Meschi E., Meyer T., Cordonnier A.M., Michaud J.F., Mirabito L., Moser R., Mossiere F., Muffat-Joly J., Mulders M., Mulon J., Murer E., Mättig P., Oh A., Onnela A., Oriunno M., Orsini L., Osborne J.A., Paillard C., Pal I., Papotti G., Passardi G., Patino-Revuelta A., Patras V., Solano B.P., Perez E., Perinic G., Pernot J.F., Petagna P., Petiot P., Petit P., Petrilli A., Pfeiffer A., Piccut C., Pimiä M., Pintus R., Pioppi M., Placci A., Pollet L., Postema H., Price M.J., Principe R., Racz A., Radermacher E., Ranieri R., Raymond G., Rebecchi P., Rehn J., Reynaud S., Naraghi H.R., Ricci D., Ridel M., Risoldi M., Moreira P.R.S., Rohlev A., Roiron G., Rolandi G., Rumerio P., Runolfsson O., Ryjov V., Sakulin H., Samyn D., Amaral L.C.S., Sauce H., Sbrissa E., Scharff-Hansen P., Schieferdecker P., Schlatter W.D., Schmitt B., Schmuecker H.G., Schröder M., Schwick C., Schäfer C., Segoni I., Roldán P.S., Sgobba S., Sharma A., Siegrist P., Sigaud C., Sinanis N., Sobrier T., Sphicas P., Spiropulu M., Stefanini G., Strandlie A., Szoncsó F., Taylor B.G., Teller O., Thea A., Tournefier E., Treille D., Tropea P., Troska J., Tsesmelis E., Tsirou A., Valls J., Van Vulpen I., Donckt M.V., Vasey F., Acosta M.V., Veillet L., Vichoudis P., Waurick G., Wellisch J.P., Wertelaers P., Wilhelmsson M., Willers I.M., Winkler M., Zanetti M., Bertl W., Deiters K., Dick P., Erdmann W., Feichtinger D., Gabathuler K., Hochman Z., Horisberger R., Ingram Q., Kaestli H.C., Kotlinski D., König S., Poerschke P., Renker D., Rohe T., Sakhelashvili T., Starodumov A., Aleksandrov V., Behner F., Beniozef I., Betev B., Blau B., Brett A.M., Caminada L., Chen Z., Chivarov N., Da Silva Di Calafiori D., Dambach S., Davatz G., Delachenal V., Marina R.D., Dimov H., Dissertori G., Dittmar M., Djambazov L., Dröge M., Eggel C., Ehlers J., Eichler R., Elmiger M., Faber G., Freudenreich K., Fuchs J.F., Georgiev G.M., Grab C., Haller C., Herrmann J., Hilgers M., Hintz W., Hofer H., Hofer H., Horisberger U., Horvath I., Hristov A., Humbertclaude C., Iliev B., Kastli W., Kruse A., Kuipers J., Langenegger U., Lecomte P., Lejeune E., Leshev G., Lesmond C., List B., Luckey P.D., Lus- termann W., Maillefaud J.D., Marchica C., Maurisset A., Meier B., Milenovic P., Milesi M., Moortgat F., Nanov I., Nardulli A., Nessi-Tedaldi F., Panev B., Pape L., Pauss F., Petrov E., Petrov G., Peynekov M.M., Pitzl D., Punz T., Riboni P., Riedlberger J., Rizzi A., Ronga F.J., Roykov P.A., Röser U., Schinzel D., Schöning A., Sourkov A., Stanishev K., Stoenchev S., Stöckli F., Suter H., TrüB P., Udriot S., Uzunova D.G., Veltchev I., Viertel G., Von Gunten H.P., Waldmeier-Wicki S., Weber R., Weber M., Weng J., Wensveen M., Wittgenstein F., Zagoursky K., Alagoz E., Amsler C., Chiochia V., Hoermann C., Regenfus C., Robmann P., Rommerskirchen T., Schmidt A., Steiner S., Tsirigkas D., Wilke L., Blyth S., Chang Y.H., Chen E.A., Go A., Hung C.C., Kuo C.M., Li S.W., Lin W., Chang P., Chao Y., Chen K.F., Gao Z., Hou G.W.S., Hsiung Y.B., Lei Y.J., Lin S.W., Lu R.S., Shiu J.G., Tzeng Y.M., Ueno K., Velikzhanin Y., Wang C.C., Wang M.-Z., Aydin S., Azman A., Bakirci M.N., Basegmez S., Cerci S., Dumanoglu I., Erturk S., Eskut E., Topaksu A.K., Kisoglu H., Kurt P., Ozdemir K., Koca N.O., Ozkurt H., Ozturk S., Polatöz A., Sogut K., Topakli H., Vergili M., Öt G., Gamsizkan H., Sekmen S., Serin-Zeyrek M., Sever R., Zeyrek M., Deliomeroglu M., Gülmez E., Isiksal E., Kaya M., Kaya O., Ozkorucuklu S., Sonmez N., Grinev B., Lyubynskiy V., Senchyshyn V., Levchuk L., Lukyanenko S., Soroka D., Sorokin P., Zub S., Anjum A., Baker N., Hauer T., McClatchey R., Odeh M., Rogulin D., Solomonides A., Brooke J.J., Croft R., Cussans D., Evans D., Frazier R., Grant N., Hansen M., Head R.D., Heath G.P., Heath H.F., Hill C., Huckvale B., Jackson J., Lynch C., Mackay C.K., Metson S., Nash S.J., Newbold D.M., Presland A.D., Probert M.G., Reid E.C., Smith V.J., Tapper R.J., Walton R., Bateman E., Bell K.W., Brown R.M., Camanzi B., Church I.T., Cockerill D.J.A., Cole J.E., Connolly J.F., Coughlan J.A., Flower P.S., Ford P., Francis V.B., French M.J., Galagedera S.B., Gannon W., Gay A.P.R., Geddes N.I., Greenhalgh R.J.S., Halsall R.N.J., Haynes W.J., Hill J.A., Jacob F.R., Jeffreys P.W., Jones L.L., Kennedy B.W., Lintern A.L., Lodge A.B., Maddox A.J., Morrissey Q.R., Murray P., Patrick G.N., Pattison C.A.X., Pearson M.R., Quinton S.P.H., Rogers G.J., Salisbury J.G., Shah A.A., Shepherd-Themistocleous C.H., Smith B.J., Sproston M., Stephenson R., Taghavi S., Tomalin I.R., Torbet M.J., Williams J.H., Womersley W.J., Worm S.D., Xing F., Apollonio M., Arteche F., Bainbridge R., Barber G., Barrillon P., Batten J., Beuselinck R., Hall P.M.B., Britton D., Cameron W., Clark D.E., Clark I.W., Colling D., Cripps N., Davies G., Negra M.D., Dewhirst G., Dris S., Foudas C., Fulcher J., Futyan D., Graham D.J., Greder S., Greenwood S., Hall G., Hassard J.F., Hays J., Iles G., Kasey V., Khaleeq M., Leaver J., Lewis P., MacEvoy B.C., Maroney O., McLeod E.M., Miller D.G., Nash J., Nikitenko A., Messomo E.N., Noy M., Papageorgiou A., Pesaresi M., Petridis K., Price D.R., Qu X., Raymond D.M., Rose A., Rutherford S., Ryan M.J., Sciacca F., Seez C., Sharp P., Sidiropoulos G., Stettler M., Stoye M., Striebig J., Takahashi M., Tallini H., Tapper A., Timlin C., Toudup L., Virdee T., Wakefield S., Walsham P., Wardrope D., Wingham M., Zhang Y., Zorba O., Da Via C., Goitom I., Hobson P.R., Imrie D.C., Reid I., Selby C., Sharif O., Teodorescu L., Watts S.J., Yaselli I., Hazen E., Heering A., Heister A., Lawlor C., Lazic D., Machado E., Rohlf J., Sulak L., Rodriguez F.V., Wu S.X., Avetisyan A., Bose T., Christofek L., Cutts D., Esen S., Hooper R., Landsberg G., Narain M., Nguyen D., Speer T., Tsang K.V., Breedon R., Case M., Chertok M., Conway J., Cox P.T., Dolen J., Erbacher R., Fisyak Y., Friis E., Grim G., Holbrook B., Ko W., Kopecky A., Lander R., Lin F.C., Lister A., Maruyama S., Pellett D., Rowe J., Searle M., Smith J., Soha A., Squires M., Tripathi M., Sierra R.V., Veelken C., Andreev V., Arisaka K., Bonushkin Y., Chandramouly S., Cline D., Cousins R., Erhan S., Hauser J., Ignatenko M., Jarvis C., Lisowski B., Matthey C., Mohr B., Mumford J., Otwinowski S., Pischalnikov Y., Rakness G., Schlein P., Shi Y., Tannenbaum B., Tucker J., Valuev V., Wallny R., Wang H.G., Yang X., Zheng Y., Andreeva J., Babb J., Campana S., Chrisman D., Clare R., Ellison J., Fortin D., Gary J.W., Gorn W., Hanson G., Jeng G.Y., Kao S.C., Layter J.G., Liu F., Liu H., Luthra A., Pasztor G., Rick H., Satpathy A., Shen B.C., Stringer R., Sytnik V., Tran P., Villa S., Wilken R., Wimpenny S., Zer-Zion D., Branson J.G., Perez J.A.C., Dusinberre E., Kelley R., Lebourgeois M., Letts J., Lipeles E., Mangano B., Martin T., Mojaver M., Muelmenstaedt J., Norman M., Paar H.P., Petrucci A., Pi H., Pieri M., Rana A., Sani M., Sharma V., Simon S., White A., Würthwein F., Yagil A., Affolder A., Allen A., Campagnari C., D'Alfonso M., Dierlamm A., Garberson J., Hale D., Incandela J., Kalavase P., Koay S.A., Kovalskyi D., Krutelyov V., Kyre S., Lamb J., Lowette S., Nikolic M., Pavlunin V., Rebassoo F., Ribnik J., Richman J., Rossin R., Shah Y.S., Stuart D., Swain S., Vlimant J.R., White D., Witherell M., Bornheim A., Bunn J., Chen J., Denis G., Galvez P., Gataullin M., Legrand I., Litvine V., Ma Y., Mao R., Nae D., Narsky I., Newman H.B., Orimoto T., Rogan C., Shevchenko S., Steenberg C., Su X., Thomas M., Timciuc V., Van Lingen F., Veverka J., Voicu B.R., Weinstein A., Wilkinson R., Xia Y., Yang Y., Zhang L.Y., Zhu K., Zhu R.Y., Ferguson T., Jang D.W., Jun S.Y., Paulini M., Russ J., Terentyev N., Vogel H., Vorobiev I., Bunce M., Cumalat J.P., Dinard M.E., Drell B.R., Ford W.T., Givens K., Heyburn B., Johnson D., Nauenberg U., Stenson K., Wagner S.R., Agostino L., Alexander J., Blekman F., Cassel D., Das S., Duboscq J.E., Gibbons L.K., Heltsley B., Jones C.D., Kuznetsov V., Patterson J.R., Riley D., Ryd A., Stroiney S., Sun W., Thom J., Vaughan J., Wittich P., Beetz C.P., Cirino G., Podrasky V., Sanzeni C., Winn D., Abdullin S., Afaq M.A., Albrow M., Amundson J., Apollinari G., Atac M., Badgett W., Bakken J.A., Baldin B., Banicz K., Bauerdick L.A.T., Baumbaugh A., Berryhill J., Bhat P.C., Binkley M., Bloch I., Borcherding F., Boubekeur A., Bowden M., Burkett K., Butler J.N., Cheung H.W.K., Chevenier G., Chlebana F., Churin I., Cihangir S., Dagenhart W., Demarteau M., Dykstra D., Eartly D.P., Elias J.E., Elvira V.D., Evans D., Fisk I., Freeman J., Gaines I., Gartung P., Geurts F.J.M., Giacchetti L., Glenzinski D.A., Gottschalk E., Grassi T., Green D., Grimm C., Guo Y., Gutsche O., Hahn A., Hanlon J., Harris R.M., Hesselroth T., Holm S., Holzman B., James E., Jensen H., Johnson M., Joshi U., Klima B., Kossiakov S., Kousouris K., Kowalkowski J., Kramer T., Kwan S., Lei C.M., Leininger M., Los S., Lueking L., Lukhanin G., Lusin S., Maeshima K., Marraffino J.M., Mason D., McBride P., Miao T., Moccia S., Mokhov N., Mrenna S., Murray S.J., Newman-Holmes C., Noeding C., O'Dell V., Paterno M., Petravick D., Pordes R., Prokofyev O., Ratnikova N., Ronzhin A., Sekhri V., Sexton-Kennedy E., Sfiligoi I., Shaw T.M., Skup E., Smith R.P., Spalding W.J., Spiegel L., Stavrianakou M., Stiehr G., Stone A.L., Suzuki I., Tan P., Tanenbaum W., Temple L.E., Tkaczyk S., Uplegger L., Vaan-dering E.W., Vidal R., Wands R., Wenzel H., Whitmore J., Wicklund E., Wu W.M., Wu Y., Yarba J., Yarba V., Yumiceva F., Yun J.C., Zimmerman T., Acosta D., Avery P., Barashko V., Bartalini P., Bourilkov D., Cavanaugh R., Dolinsky S., Drozdetskiy A., Field R.D., Fu Y., Furic I.K., Gorn L., Holmes D., Kim B.J., Klimenko S., Konigsberg J., Korytov A., Kotov K., Levchenko P., Madorsky A., Matchev K., Mitselmakher G., Pakhotin Y., Prescott C., Ramond L., Ramond P., Schmitt, M., Scurlock B., Stasko J., Stoeck H., Wang D., Yelton J., Gaultney V., Kramer L., Lebolo L.M., Linn S., Markowitz P., Martinez G., Rodriguez J.L., Adams T., Askew A., Atramentov O., Bertoldi M., Dharmaratna W.G.D., Gershtein Y., Gleyzer S.V., Hagopian S., Hagopian V., Jenkins C.J., Johnson K.F., Prosper H., Simek D., Thomaston J., Baarmand M., Baksay L., Guragain S., Hohlmann M., Mermerkaya H., Ralich R., Vodopiyanov I., Adams M.R., Anghel I.M., Apanasevich L., Barannikova O., Bazterra V.E., Betts R.R., Dragoiu C., Garcia-Solis E.J., Gerber C.E., Hofman D.J., Hollis R., Iordanova A., Khalatian S., Mironov C., Shabalina E., Smoron A., Varelas N., Akgun U., Albayrak E.A., Ayan A.S., Briggs R., Cankocak K., Clarida W., Cooper A., Deb- bins P., Duru F., Fountain M., McCliment E., Merlo J.P., Mestvirishvili A., Miller M.J., Moeller A., Newsom C.R., Norbeck E., Olson J., Onel Y., Perera L., Schmidt I., Wang S., Yetkin T., Anderson E.W., Chakir H., Hauptman J.M., Lamsa J., Barnett B.A., Blumenfeld B., Chien C.Y., Giurgiu G., Gritsan A., Kim D.W., Lae C.K., Maksimovic P., Swartz M., Tran N., Baringer P., Bean A., Chen J., Coppage D., Grachov O., Murray M., Radicci V., Wood J.S., Zhukova V., Bandurin D., Bolton T., Kaadze K., Kahl W.E., Maravin Y., Onoprienko D., Sidwell R., Wan Z., Dahmes B., Gronberg J., Hollar J., Lange D., Wright D., Wuest C.R., Baden D., Bard R., Eno S.C., Ferencek D., Hadley N.J., Kellogg R.G., Kirn M., Kunori S., Lockner E., Ratnikov F., Santanastasio F., Skuja A., Toole T., Wang L., Wetstein M., Alver B., Ballintijn M., Bauer G., Busza W., Ceballos G.G., Hahn K.A., Harris P., Klute M., Kravchenko I., Li W., Loizides C., Ma T., Nahn S., Paus C., Pavlon S., Gomez J.P., Roland C., Roland G., Rudolph M., Stephans G., Sumorok K., Vaurynovich S., Wenger E.A., Wyslouch B., Bailleux D., Cooper S., Cushman P., De Benedetti A., Dolgopolov A., Dudero P.R., Egeland R., Franzoni G., Gilbert W.J., Gong D., Grahl J., Haupt J., Klapoetke K., Kronkvist I., Kubota Y., Mans J., Rusack R., Sengupta S., Sherwood B., Singovsky A., Vikas P., Zhang J., Booke M., Cremaldi L.M., Godang R., Kroeger R., Reep M., Reidy J., Sanders D.A., Sonnek P., Summers D., Watkins S., Bloom K., Bockelman B., Claes D.R., Dominguez A., Eads M., Furukawa M., Keller J., Kelly T., Lundstedt C., Malik S., Snow G.R., Swanson D., Ecklund K.M., Iashvili I., Kharchilava A., Kumar A., Strang M., Alverson G., Barberis E., Boeriu O., Eulisse G., McCauley T., Musienko Y., Muzaffar S., Osborne I., Reucroft S., Swain J., Taylor L., Tuura L., Gobbi B., Kubantsev M., Kubik A., Ofierzynski R.A., Schmitt M., Spencer E., Stoynev S., Szleper M., Velasco

M., Won S., Andert K., Baumbaugh B., Beiersdorf B.A., Castle L., Chorny J., Goussiou A., Hildreth M., Jessop C., Karmgard D.J., Kolberg T., Marchant J., Marinelli N., McKenna M., Ruchti R., Vigneault M., Wayne M., Wiand D., Bylsma B., Durkin L.S., Gilmore J., Gu J., Killewald P., Ling T.Y., Rush C.J., Sehgal V., Williams G., Adam N., Chidzik S., Denes P., Elmer P., Garmash A., Gerbaudo D., Halyo V., Jones J., Marlow D., Olsen J., Piroue P., Stickland D., Tully C., Werner J.S., Wildish T., Wynhoff S., Xie Z., Huang X.T., Lopez A., Mendez H., Vargas J.E.R., Zatserklyaniy A., Apresyan A., Arndt K., Barnes V.E., Bolla G., Bortoletto D., Bujak A., Everett A., Fahling M., Garfinkel A.F., Gutay L., Ippolito N., Kozhevnikov Y., Laasanen A.T., Liu C., Maroussov V., Medved S., Merkel P., Miller D.H., Miyamoto J., Neumeister N., Pompos A., Roy A., Sedov A., Shipsey I., Cuplov V., Parashar N., Bargassa P., Lee S.J., Liu J.H., Maronde D., Matveev M., Nussbaum T., Padley B.P., Roberts J., Tumanov A., Bodek A., Budd H., Cammin J., Chung Y.S., De Barbaro P., Demina R., Ginther G., Gotra G., Korjenevski S., Miner D.C., Sakumoto W., Slattery P., Zielinski M., Bhatti A., Demortier L., Goulianos K., Hatakeyama K., Mesropian C., Bartz E., Chuang S.H., Doroshenko J., Halkiadakis E., Jacques P.F., Khits D., Lath A., Macpherson A., Plano R., Rose K., Schnetzer S., Somalwar S., Stone R., Watts T.L., Cerizza G., Hollingsworth M., Lazoflores J., Ragghianti G., Spanier S., York A., Aurisano A., Golyash A., Kamon T., Nguyen C.N., Pivarski J., Safonov A., Toback D., Weinberger M., Akchurin N., Berntzon L., Carrell K.W., Gumus K., Jeong C., Kim H., Lee S.W., Mc Gonagill B.G., Roh Y., Sill A., Spezziga M., Thomas R., Volobouev I., Washington E., Wigmans R., Yazgan E., Bapty T., Engh D., Florez C., Johns W., Keskinpala T., Lopez E.L., Neema S., Nordstrom S., Pathak S., Sheldon P., Andelin D., Arenton M.W., Balazs M., Buehler M., Conetti S., Cox B., Hirosky R., Humphrey M., Imlay R., Ledovskoy A., Phillips II D., Powell H., Ronquest M., Yohay R., Anderson M., Baek Y.W., Bellinger J.N., Bradley D., Cannarsa P., Carlsmith D., Crotty I., Dasu S., Feyzi F., Gorski T., Gray L., Grogg K.S., Grothe M., Jaworski M., Klabbers P., Klukas J., Lanaro A., Lazaridi C., Leonard J., Loveless R., De Abril M.M., Mohapatra A., Ott G., Smith W.H., Weinberg M., Wenman D., Atoian G.S., Dhawan S., Issakov V., Neal H., Poblaguev A., Zeller M.E., Abdullaeva G., Avezov A., Fazylov M.I., Gasanov E.M., Khugaev A., Koblik Y.N., Nishonov M., Olimov K., Umaraliev A., Yuldashev B.S.","The CMS experiment at the CERN LHC",2008,"Journal of Instrumentation","3","8", S08004,"","",,"10.1088/1748-0221/3/08/S08004","https://www.scopus.com/inward/record.uri?eid=2-s2.0-67650317516&doi=10.1088%2f1748-0221%2f3%2f08%2fS08004&partnerID=40&md5=308f3924df6be52a654552a8aded90a8"

176. Cellere G., Cester A., Paccagnella A.,"Radiation induced charge loss mechanisms across the dielectrics of floating gate flash memories",2007,"ECS Transactions","6","3",,"807","843",,"10.1149/1.2728834","https://www.scopus.com/inward/record.uri?eid=2-s2.0-45849144787&doi=10.1149%2f1.2728834&partnerID=40&md5=61936592ae207d9ae70862807fc52e42"

177. Gasperin A., Ghidini G., Cester A., Paccagnella A.,"Oxide-nitride-oxide capacitor reliability under heavy-ion irradiation",2007,"IEEE Transactions on Nuclear Science","54","6",,"1898","1905",,"10.1109/TNS.2007.910120","https://www.scopus.com/inward/record.uri?eid=2-s2.0-37249029252&doi=10.1109%2fTNS.2007.910120&partnerID=40&md5=a2d500d0514070226ea5b800225a4b03"

178. Manuzzato A., Gerardin S., Paccagnella A., Sterpone L., Violante M.,"Effectiveness ofTMR-based techniques to mitigate alpha-induced SEU accumulation in commercial SRAM-based FPGAs",2007,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5205499,"","",,"10.1109/RADECS.2007.5205499","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

70449567539&doi=10.1109%2fRADECS.2007.5205499&partnerID=40&md5=8c80bc5668b298476fae3e3460f06090"

179. Manuzzato A., Rech P., Gerardin S., Paccagnella A., Sterpone L., Violante M.,"Sensitivity evaluation of TMR-hardened circuits to multiple seus induced by alpha particles in commercial SRAM-based FPGAs",2007,"Proceedings - IEEE International Symposium on Defect and Fault Tolerance in VLSI Systems",,, 4358375,"79","86",,"10.1109/DFT.2007.57","https://www.scopus.com/inward/record.uri?eid=2-s2.0-77649315846&doi=10.1109%2fDFT.2007.57&partnerID=40&md5=73fd62fabb4a4c75155a1abc2bc35ab8"
180. Cellere G., Paccagnella A., Visconti A., Bonanomi M., Harboe-Sørensen R., Virtanen A.,"Angular dependence of heavy ion effects in floating gate memory arrays",2007,"IEEE Transactions on Nuclear Science","54","6",,"2371","2378",,"10.1109/TNS.2007.910036","https://www.scopus.com/inward/record.uri?eid=2-s2.0-37249082553&doi=10.1109%2fTNS.2007.910036&partnerID=40&md5=71ea2a5d0d2d11dd9bb3608da5777391"
181. Cester A., Wrachien N., Gasperin A., Paccagnella A., Portoghese R., Gerardi C.,"Radiation tolerance of nanocrystal-based flash memory arrays against heavy ion irradiation",2007,"IEEE Transactions on Nuclear Science","54","6",,"2196","2203",,"10.1109/TNS.2007.908757","https://www.scopus.com/inward/record.uri?eid=2-s2.0-37249071391&doi=10.1109%2fTNS.2007.908757&partnerID=40&md5=f861722cdc3bf72eb57ff3dd1b8d4e0f"
182. Gerardin S., Griffoni A., Tazzoli A., Cester A., Meneghesso G., Paccagnella A.,"Electrostatic discharge effects in irradiated fully depleted SOI MOSFETs with ultra-thin gate oxide",2007,"IEEE Transactions on Nuclear Science","54","6",,"2204","2209",,"10.1109/TNS.2007.910848","https://www.scopus.com/inward/record.uri?eid=2-s2.0-37249065727&doi=10.1109%2fTNS.2007.910848&partnerID=40&md5=b9d08041e613ac041ec44ef8abca147a"
183. Porti M., Gerardin S., Nafría M., Aymerich X., Cester A., Paccagnella A.,"Using AFM related techniques for the nanoscale electrical characterization of irradiated ultrathin gate oxides",2007,"IEEE Transactions on Nuclear Science","54","6",,"1891","1897",,"10.1109/TNS.2007.909483","https://www.scopus.com/inward/record.uri?eid=2-s2.0-37249008708&doi=10.1109%2fTNS.2007.909483&partnerID=40&md5=a4946c2b7ecc1adf55064415a6e1c879"
184. Griffoni A., Gerardin S., Cester A., Paccagnella A., Simoen E., Claeys C.,"Effects of heavy-ion strikes on fully depleted SOI MOSFETs with ultra-thin gate oxide and different strain-inducing techniques",2007,"IEEE Transactions on Nuclear Science","54","6",,"2257","2263",,"10.1109/TNS.2007.909510","https://www.scopus.com/inward/record.uri?eid=2-s2.0-37249005328&doi=10.1109%2fTNS.2007.909510&partnerID=40&md5=6954ca9894d70e13680622aadeb6ab6e"
185. Cellere G., Paccagnella A., Visconti A., Bonanomi M., Beltrami S., Harboe-Sørensen R., Virtanen A.,"Effect of ion energy on charge loss from floating gate memories",2007,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5205579,"","",,"10.1109/RADECS.2007.5205579","https://www.scopus.com/inward/record.uri?eid

=2-s2.0-70449595751&doi=10.1109%2fRADECS.2007.5205579&partnerID=40&md5=036f28388d436a565e6f5e9ec959b38d"

186. Cellere G., Bandiera L., Borgo M., De Toni A., Santoni L., Paccagnella A., Lorenzelli L.,"A purely electronic method to measure transfection efficiency in a single-cell electroporation biochip",2007,"ECS Transactions","6","15",,"1","11",,"10.1149/1.2812435","https://www.scopus.com/inward/record.uri?eid=2-s2.0-49049103046&doi=10.1149%2f1.2812435&partnerID=40&md5=c27fbb2c6f45464ddd920beaea4ed8b4"

187. Cellere G., Paccagnella A., Visconti A., Bonanomi M., Beltrami S., Harboe-Sørensen R., Virtanen A.,"Single event upset in FG memory arrays: Prompt and permanent data corruption in modern and future technologies",2007,"Proceedings - 2007 Non-Volatile Memory Technology Symposium, NVMTS 07",,, 4389939,"25","29",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-48549097453&partnerID=40&md5=d5e47d20f45f441a734515b547f6b8c1"

188. Bagatin M., Cellere G., Gerardin S., Paccagnella A., Visconti A., Beltrami S., Maccarrone M.,"Single event effects in 1Gbit 90nm NAND flash memories under operating conditions",2007,"Proceedings - IOLTS 2007 13th IEEE International On-Line Testing Symposium",,, 4274836,"146","151",,"10.1109/IOLTS.2007.59","https://www.scopus.com/inward/record.uri?eid=2-s2.0-37249015020&doi=10.1109%2fIOLTS.2007.59&partnerID=40&md5=2a1aa59dda0022d653ac75c1f4f01db8"

189. Gasperin A., Wrachien N., Cester A., Paccagnella A., Ottogalli F., Corda U., Fuochi P., Lavalle M.,"Total ionizing dose effects on 4Mbit phase change memory arrays",2007,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5205536,"","",,"10.1109/RADECS.2007.5205536","https://www.scopus.com/inward/record.uri?eid=2-s2.0-70449561164&doi=10.1109%2fRADECS.2007.5205536&partnerID=40&md5=fb43c70e6d1cd780c4e60717fa1bd971"

190. Bandiera L., Borgo M., Cellere G., De Toni A., Santoni L., Dal Maschio M., Girardi S., Lorenzelli L., Paccagnella A.,"Electrical measurement of adhesion and viability of living cells with a silicon chip",2007,"Technical Digest - International Electron Devices Meeting, IEDM",,, 4419083,"855","858",,"10.1109/IEDM.2007.4419083","https://www.scopus.com/inward/record.uri?eid=2-s2.0-50249143462&doi=10.1109%2fIEDM.2007.4419083&partnerID=40&md5=7b839a181a62c9925a6e38653ecab43e"

191. Silvestri M., Gerardin S., Paccagnella A., Faccio F., Gonella L., Pantano D., Re V., Manghisoni M., Ratti L., Ranieri A.,"Channel hot carrier stress on irradiated 130-nm NMOSFETs: Impact of bias conditions during X-ray exposure",2007,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 5205571,"","",,"10.1109/RADECS.2007.5205571","https://www.scopus.com/inward/record.uri?eid=2-s2.0-70449591994&doi=10.1109%2fRADECS.2007.5205571&partnerID=40&md5=b0f30e6b1ca6ed0e34a7b2c9fd127456"

192. Flament O., Brichard B., Chugg A., Dyer C., Edwards R., Ibe E., Lacoe R., Paccagnella A., Holmes-Siedle A., Leray J.L.,"Radiation effects in future electronics from device to systems - Roundtable report",2007,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,,

5205427,"","",,"10.1109/RADECS.2007.5205427","https://www.scopus.com/inward/record.uri?eid=2-s2.0-70449572697&doi=10.1109%2fRADECS.2007.5205427&partnerID=40&md5=3eb5029c1f70e507db640f5670f40a36"

193. Adell P., Baggio J., Blackmore E., Fleetwood D., Hiemstra D., Huston S., Johnston A., Lum G., McNulty P., Normand E., Paccagnella A., Palkuti L., Pease R., Pickel J., Reed R., Shaneyfelt M., Simons M., Xapsos M., Dyer C.,"2007 IEEE nuclear and space radiation effects conference awards comments by the chairman",2007,"IEEE Transactions on Nuclear Science","54","6",,"1877","1878",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-37249090764&partnerID=40&md5=e3c3155200a8173d3efe4962773e37b1"

194. Gasperin A., Cester A., Wrachien N., Paccagnella A., Gerardi C., Ancarani V.,"Role of oxide/nitride interface traps on the nanocrystal memory characteristics",2007,"Annual Proceedings - Reliability Physics (Symposium)",,, 4227740,"658","659",,"10.1109/RELPHY.2007.369999","https://www.scopus.com/inward/record.uri?eid=2-s2.0-34548808078&doi=10.1109%2fRELPHY.2007.369999&partnerID=40&md5=f620db081e2bb0edeea50b25766f504e"

195. Porti M., Gerardin S., Nafría M., Aymerich X., Cester A., Paccagnella A., Schiavuta P., Pierobon R.,"Systematic characterization of soft- and hard-breakdown spots using techniques with nanometer resolution",2007,"Microelectronic Engineering","84","9-10",,"1956","1959",,"10.1016/j.mee.2007.04.063","https://www.scopus.com/inward/record.uri?eid=2-s2.0-34248634316&doi=10.1016%2fj.mee.2007.04.063&partnerID=40&md5=63b122716dbc818306502d3ee9f53923"

196. Martín-Martínez J., Gerardin S., Rodríguez R., Nafría M., Aymerich X., Cester A., Paccagnella A., Ghidini G.,"Lifetime estimation of analog circuits from the electrical characteristics of stressed MOSFETs",2007,"Microelectronics Reliability","47","9-11 SPEC. ISS.",,"1349","1352",,"10.1016/j.microrel.2007.07.088","https://www.scopus.com/inward/record.uri?eid=2-s2.0-34548704303&doi=10.1016%2fj.microrel.2007.07.088&partnerID=40&md5=945e5c057ad987def6fe6727f2bad25c"

197. Cellere G., Paccagnella A., Visconti A., Bonanomi M., Beltrami S., Schwank J.R., Shaneyfelt M.R., Paillet P.,"Total ionizing dose effects in NOR and NAND flash memories",2007,"IEEE Transactions on Nuclear Science","54","4",,"1066","1070",,"10.1109/TNS.2007.901199","https://www.scopus.com/inward/record.uri?eid=2-s2.0-34548065398&doi=10.1109%2fTNS.2007.901199&partnerID=40&md5=c21178bca6f9a649ffe362d4375ac1c1"

198. Violante M., Sterpone L., Manuzzato A., Gerardin S., Rech P., Bagatin M., Paccagnella A., Andreani C., Gorini G., Pietropaolo A., Cardarilli G., Pontarelli S., Frost C.,"A new hardware/software platform and a new 1/E neutron source for soft error studies: Testing FPGAs at the ISIS facility",2007,"IEEE Transactions on Nuclear Science","54","4",,"1184","1189",,"10.1109/TNS.2007.902349","https://www.scopus.com/inward/record.uri?eid=2-s2.0-34548090964&doi=10.1109%2fTNS.2007.902349&partnerID=40&md5=71b304c7518771eda68c34410b4dcfbe"

199. Cester A., Gasperin A., Wrachien N., Paccagnella A., Ancarani V., Gerardi C.,"Ionising radiation and electrical stress on nanocrystal memory cell array",2007,"Microelectronics Reliability","47","4-5 SPEC.

ISS.",,"602","605",,"10.1016/j.microrel.2007.01.008","https://www.scopus.com/inward/record.uri?eid=2-s2.0-34247175828&doi=10.1016%2fj.microrel.2007.01.008&partnerID=40&md5=5272491c3b0578ab3c811c0bb0c23b00"

200. Cellere G., Paccagnella A., Visconti A., Bonanomi M.,"Erratic effects of irradiation in floating gate memory cells",2006,"Proceedings - IOLTS 2006: 12th IEEE International On-Line Testing Symposium","2006",, 1655515,"51","56",,"10.1109/IOLTS.2006.30","https://www.scopus.com/inward/record.uri?eid=2-s2.0-34247250861&doi=10.1109%2fIOLTS.2006.30&partnerID=40&md5=08280f3742f56f0b74c3397339bb326f"
201. Cellere G., Paccagnella A., Visconti A., Bonanomi M.,"Variability in FG memories performance after irradiation",2006,"IEEE Transactions on Nuclear Science","53","6",,"3349","3355",,"10.1109/TNS.2006.886766","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33846283779&doi=10.1109%2fTNS.2006.886766&partnerID=40&md5=c06914cbcf316cbe2a8ac38d5e8ace64"
202. Cellere G., Paccagnella A., Visconti A., Bonanomi M.,"Secondary effects of single ions on floating gate memory cells",2006,"IEEE Transactions on Nuclear Science","53","6",,"3291","3297",,"10.1109/TNS.2006.883996","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33846283041&doi=10.1109%2fTNS.2006.883996&partnerID=40&md5=2dded1c339b08af889a9fd13303396c3"
203. Cellere G., Larcher L., Paccagnella A., Visconti A., Bonanomi M.,"Single event leakage current in flash memory",2006,"2006 IEEE International Conference on Integrated Circuit Design and Technology, ICICDT'06",,, 1669424,"","",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-37649028093&partnerID=40&md5=bc0ef9067a204e953f282965f559a801"
204. Cellere G., Paccagnella A., Visconti A., Bonanomi M., McNulty P.J.,"Single-ion dosemeter based on floating gate memories",2006,"Radiation Protection Dosimetry","122","1-4",,"457","459",,"10.1093/rpd/ncl394","https://www.scopus.com/inward/record.uri?eid=2-s2.0-34347398090&doi=10.1093%2frpd%2fncl394&partnerID=40&md5=9f0b660fa5e379d0413cebeec66cb927"
205. Gerardin S., Bagatin M., Cester A., Paccagnella A., Kaczer B.,"Impact of heavy-ion strikes on minimum-size MOSFETs with ultra-thin gate oxide",2006,"IEEE Transactions on Nuclear Science","53","6",,"3675","3680",,"10.1109/TNS.2006.885374","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33846325445&doi=10.1109%2fTNS.2006.885374&partnerID=40&md5=d25d3a9c215cec6b84e785ca666d8ecb"
206. Cester A., Gasperin A., Wrachien N., Paccagnella A., Ancarani V., Gerardi C.,"Impact of heavy-ion strikes on nanocrystal non volatile memory cell arrays",2006,"IEEE Transactions on Nuclear Science","53","6",,"3195","3202",,"10.1109/TNS.2006.885004","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33846312092&doi=10.1109%2fTNS.2006.885004&partnerID=40&md5=717760c3913457bc18a5c7bdcd766585"
207. Gasperin A., Cester A., Wrachien N., Paccagnella A., Ancarani V., Gerardi C.,"Radiation-induced modifications of the electrical characteristics of nanocrystal memory cells and arrays",2006,"IEEE Transactions on Nuclear Science","53","6",,"3693","3700",,"10.1109/TNS.2006.885109","https://www.scopus.com/inward/

record.uri?eid=2-s2.0-33846278687&doi=10.1109%2fTNS.2006.885109&partnerID=40&md5=0929ebd265a69aab259a930ec95c8179"

208. Bandiera L., Borgo M., Cellere G., De Toni A., Santoni L., Bersani C., Paccagnella A.,"Electrical modeling of a biochip for genetic manipulation of single cells",2006,"Technical Digest - International Electron Devices Meeting, IEDM",,, 4154307,"","",,"10.1109/IEDM.2006.346888","https://www.scopus.com/inward/record.uri?eid=2-s2.0-46049089251&doi=10.1109%2fIEDM.2006.346888&partnerID=40&md5=72898f62cb8ba5aa8c4516070a4349ba"

209. McNulty P.J., Poole K.F., Crissler M., Reneau J., Cellere G., Paccagnella A., Visconti A., Bonanomi M., Stroebel D., Fennell M., Perez R.,"Sensitivity and dynamic range of FGMOS dosemeters",2006,"Radiation Protection Dosimetry","122","1-4",,"460","462",,"10.1093/rpd/ncl487","https://www.scopus.com/inward/record.uri?eid=2-s2.0-34347405547&doi=10.1093%2frpd%2fncl487&partnerID=40&md5=9b16af5a8baa734909a2b9427aa48372"

210. Gerardin S., Griffoni A., Cester A., Paccagnella A., Ghidini G.,"Degradation of static and dynamic behavior of CMOS inverters during constant and pulsed voltage stress",2006,"Microelectronics Reliability","46","9-11",,"1669","1672",,"10.1016/j.microrel.2006.07.052","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33747777087&doi=10.1016%2fj.microrel.2006.07.052&partnerID=40&md5=29b51988294ae2a064cbdf43c789965b"

211. Danesin F., Zanon F., Gerardin S., Rampazzo F., Meneghesso G., Zanoni E., Paccagnella A.,"Degradation induced by 2-MeV alpha particles on AlGaN/GaN high electron mobility transistors",2006,"Microelectronics Reliability","46","9-11",,"1750","1753",,"10.1016/j.microrel.2006.07.066","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33747761585&doi=10.1016%2fj.microrel.2006.07.066&partnerID=40&md5=eb34961a3f64d0368ea2aaa47c4c9847"

212. Cellere G., Paccagnella A., Visconti A., Bonanomi M., Beltrami S.,"Single event effects in NAND flash memory arrays",2006,"IEEE Transactions on Nuclear Science","53","4", 1684022,"1813","1818",,"10.1109/TNS.2006.880944","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33748370563&doi=10.1109%2fTNS.2006.880944&partnerID=40&md5=2bed1a981bbf56541afa15c6917aa240"

213. Gerardin S., Gasperin A., Cester A., Paccagnella A., Ghidini G., Candelori A., Bacchetta N., Bisello D., Glaser M.,"Impact of 24-GeV proton irradiation on 0.13-µm CMOS devices",2006,"IEEE Transactions on Nuclear Science","53","4", 1684038,"1917","1922",,"10.1109/TNS.2006.880943","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33748340024&doi=10.1109%2fTNS.2006.880943&partnerID=40&md5=09594c600fd0a0a45a5fef2e9f120fe9"

214. Cellere G., Paccagnella A., Larcher L., Visconti A., Bonanomi M.,"Subattoampere current induced by single ions in silicon oxide layers of nonvolatile memory cells",2006,"Applied Physics Letters","88","19", 192909,"","",,"10.1063/1.2194819","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33646673088&doi=10.1063%2f1.2194819&partnerID=40&md5=5aab1637f9d654ae9a323cb43a3a562d"

215. Cellere G., Paccagnella A., Visconti A., Bonanomi M.,"Subpicosecond conduction through thin SiO2 layers triggered by heavy ions",2006,"Journal of Applied Physics","99","7", 074101,"","",,"10.1063/1.2181313","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33645940598&doi=10.1063%2f1.2181313&partnerID=40&md5=8cb724b89f28347ee86043353f7f6ad4"

216. Cimino S., Pantisano L., Aoulaiche M., Degraeve R., Kwak D.H., Crupi F., Groeseneken G., Paccagnella A.,"Hot carrier degradation on n-channel HfSiON MOSFETs: Effects on the device performance and lifetime",2005,"IEEE International Reliability Physics Symposium Proceedings",,,,"275","279",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-28844452981&partnerID=40&md5=21ab2dcd6dbd7aac68d5d95f647d7773"

217. Cester A., Gerardin S., Tazzoli A., Paccagnella A., Zanoni E., Ghidini G., Meneghesso G.,"ESD induced damage on ultra-thin gate oxide MOSFETs and its impact on device reliability",2005,"IEEE International Reliability Physics Symposium Proceedings",,,,"84","90",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-24144500114&partnerID=40&md5=f1ef2bf60a5dc38e53478f57768af9eb"

218. Cellere G., Paccagnella A., Visconti A., Bonanomi M.,"Soft errors induced by single heavy ions in Floating Gate memory arrays",2005,"Proceedings - IEEE International Symposium on Defect and Fault Tolerance in VLSI Systems",,,,"275","283",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-28444491400&partnerID=40&md5=d2e255cd5b7c39f80b0303907c6c68b1"

219. Cellere G., Paccagnella A., Valentini M.G.,"PECVD-induced damage on ultra thin SIO2 layers",2005,"Proceedings - Electrochemical Society","PV 2005-01",,,"74","85",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-31844450439&partnerID=40&md5=140aa445155358d9a509fa20b8aaeb4f"

220. Cester A., Gerardin S., Paccagnella A., Ghidini G.,"Modeling MOSFET and circuit degradation through SPICE",2005,"Proceedings of ESSDERC 2005: 35th European Solid-State Device Research Conference","2005",, 1546670,"403","406",,"10.1109/ESSDER.2005.1546670","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33751410328&doi=10.1109%2fESSDER.2005.1546670&partnerID=40&md5=9537bf3687d6f9a3aff419ae30a5fbf1"

221. Cellere G., Paccagnella A., Visconti A., Bonanomi M., Beltrami S.,"Single event effects in NAND flash memory arrays",2005,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 4365568,"C211","C217",,"10.1109/RADECS.2005.4365568","https://www.scopus.com/inward/record.uri?eid=2-s2.0-48349112403&doi=10.1109%2fRADECS.2005.4365568&partnerID=40&md5=3efa3666eb33c5f1a01c580673f1999e"

222. Cester A., Gerardin S., Paccagnella A., Simoen E., Claeys C.,"Electrical stresses on ultra-thin gate oxide SOI MOSFETs after irradiation",2005,"IEEE Transactions on Nuclear Science","52","6",,"2252","2258",,"10.1109/TNS.2005.860666","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33144490099&doi=10.1109%2fTNS.2005.860666&partnerID=40&md5=eb30306b697ef7e17fd617da4540a8a5"

223. Cellere G., Larcher L., Paccagnella A., Visconti A., Bonanomi M.,"Radiation induced leakage current in floating gate memory cells",2005,"IEEE Transactions on Nuclear Science","52","6",,"2144","2152",,"10.1109/TNS.2005.860725","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

33144481902&doi=10.1109%2fTNS.2005.860725&partnerID=40&md5=347806848db8c22ed2d2f3a1a3b39775"

224. Porti M., Nafriáa M., Aymerich X., Cester A., Paccagnella A., Cimino S.,"Leaky spots in irradiated SiO2 gate oxides observed with C-AFM",2005,"2005 Spanish Conference on Electron Devices, Proceedings","2005",, 1504304,"53","56",,"10.1109/SCED.2005.1504304","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33745711915&doi=10.1109%2fSCED.2005.1504304&partnerID=40&md5=5594224e0f0139a21a5e36184f0dd22e"

225. Gerardin S., Cester A., Paccagnella A., Gasiot G., Mazoyer P., Roche P.,"Radiation-induced breakdown in 1.7 nm oxynitrided gate oxides",2005,"IEEE Transactions on Nuclear Science","52","6",,"2210","2216",,"10.1109/TNS.2005.860690","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33144470739&doi=10.1109%2fTNS.2005.860690&partnerID=40&md5=ecf3281fee16c0f1ea7fc74e7c9b93f4"

226. Cellere G., Paccagnella A., Visconti A., Bonanomi M., Candelori A., Lora S.,"Effect of different total ionizing dose sources on charge loss from programmed Floating Gate cells",2005,"IEEE Transactions on Nuclear Science","52","6",,"2372","2377",,"10.1109/TNS.2005.860681","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33144455196&doi=10.1109%2fTNS.2005.860681&partnerID=40&md5=f425d81346f865ba91992d334c1c896c"

227. Cester A., Gerardin S., Gasperin A., Paccagnella A., Simoen E., Claeys C., Candelori A.,"Heavy ion damage in ultra-thin gate oxide SQI MOSFETs",2005,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 4365609,"G41","G47",,"10.1109/RADECS.2005.4365609","https://www.scopus.com/inward/record.uri?eid=2-s2.0-48349136611&doi=10.1109%2fRADECS.2005.4365609&partnerID=40&md5=47ae44bcf8aab4cbf67b2dca48ebb8ea"

228. Alderighi M., Candelori A., Casini F., D'Angelo S., Mancini M., Paccagnella A., Pastore S., Sechi G.R.,"Heavy ion effects on configuration logic of virtex FPGAs",2005,"Proceedings - 11th IEEE International On-Line Testing Symposium, IOLTS 2005","2005",, 1498128,"49","53",,"10.1109/IOLTS.2005.31","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33646491364&doi=10.1109%2fIOLTS.2005.31&partnerID=40&md5=04e00df335629f3a567be360f50c4330"

229. Alderighi M., Candelori A., Casini F., D'Angelo S., Mancini M., Paccagnella A., Pastore S., Sechi G.R.,"SEU sensitivity of virtex configuration logic",2005,"IEEE Transactions on Nuclear Science","52","6",,"2462","2467",,"10.1109/TNS.2005.860741","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33144463742&doi=10.1109%2fTNS.2005.860741&partnerID=40&md5=2f910c36b4541ee3e91964a103ced836"

230. Gerardin S., Gasperin A., Cester A., Paccagnella A., Ghidini G., Candelori A., Bacchetta N., Bisello D., Glaser M.,"Impact of 24-GeV proton irradiation on 0.13-μm CMOS devices",2005,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,, 4365598,"F31","F37",,"10.1109/RADECS.2005.4365598","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

48349143577&doi=10.1109%2fRADECS.2005.4365598&partnerID=40&md5=eeb4bc53d88a0e8cc7d59ea0eebf708e"

231. McNulty P.J., Poole K.F., Crisler M., Reneau J., Cellere G., Paccagnella A., Stroebel D., Fennell M., Perez R., Randall M., Call L.,"Improvements in resolution and dynamic range for FGMOS dosimetry",2005,"IEEE Transactions on Nuclear Science","52","6",,"2597","2601",,"10.1109/TNS.2005.860702","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33144476147&doi=10.1109%2fTNS.2005.860702&partnerID=40&md5=939fb6a2aae74a98980f6ec0036db7ea"

232. Cellere G., Paccagnella A., Visconti A., Bonanomi M.,"Transient conductive path induced in Floating Gate memories by single ions",2005,"2005 International Conference on Integrated Circuit Design and Technology, ICICDT",,,,"29","32",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-25844501558&partnerID=40&md5=c975a27770efa909e744f3f4af2d53ec"

233. Cellere G., Paccagnella A., Valentini M.G., Alessandri M.,"Effect of deuterium anneal on thin gate oxide reliability",2005,"2005 International Conference on Integrated Circuit Design and Technology, ICICDT",,,,"139","142",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-25844437525&partnerID=40&md5=78d9026eae1c073f2045a58fbc4e5cb1"

234. Miranda E., Cester A., Suñé J., Paccagnella A., Ghidini G.,"Simulation of the time-dependent breakdown characteristics of heavy-ion irradiated gate oxides using a mean-reverting Poisson-Gaussian process",2005,"IEEE Transactions on Nuclear Science","52","5 II",,"1462","1467",,"10.1109/TNS.2005.855808","https://www.scopus.com/inward/record.uri?eid=2-s2.0-29144518434&doi=10.1109%2fTNS.2005.855808&partnerID=40&md5=eed18362f768fb128525831dcfb84457"

235. Porti M., Nafría M., Aymerich X., Cester A., Paccagnella A., Cimino S.,"Electrical characterization at a nanometer scale of weak spots in irradiated SiO2 gate oxides",2005,"IEEE Transactions on Nuclear Science","52","5 II",,"1457","1461",,"10.1109/TNS.2005.855647","https://www.scopus.com/inward/record.uri?eid=2-s2.0-29144507347&doi=10.1109%2fTNS.2005.855647&partnerID=40&md5=a1c834aa5df5f8777151d884ff2b935b"

236. Gerardin S., Cester A., Paccagnella A., Ghidini G.,"Impact of Fowler-Nordheim and channel hot carrier stresses on MOSFETs with 2.2nm gate oxide",2005,"Microelectronic Engineering","80","SUPPL.",,"178","181",,"10.1016/j.mee.2005.04.064","https://www.scopus.com/inward/record.uri?eid=2-s2.0-19944378456&doi=10.1016%2fj.mee.2005.04.064&partnerID=40&md5=db17156f128ec244bbe24394783bb4fa"

237. Cellere G., Paccagnella A., Fogle A., Darling D., Blish II R.C., Daszko G.,"Comments on ""Flash memory under cosmic and alpha irradiation""",2005,"IEEE Transactions on Device and Materials Reliability","5","2",,"296","297",,"10.1109/TDMR.2005.848069","https://www.scopus.com/inward/record.uri?eid=2-s2.0-23844460587&doi=10.1109%2fTDMR.2005.848069&partnerID=40&md5=2c022c7a872c11498a97e081dd10c224"

238. Adam W., Bergauer T., Friedl M., Fruehwirth R., Hrubec J., Krammer M., Pernlcka M., Waltenberger W., Beaumont W., de Langhe E., de Wolf E., Tasevsky M., Bouhall O., Clerbaux B., de Lentdecker G., Dewulf J.-P., Neuckermans L., Vander-Velde C., Vanlaer P., Wlckens J., D'Hondt J., Goorens R., Heynlnck J., Lowette S., Tavernler S., Van Lancker L., Yu C., Assouak S., Bonnet J.-L., Bruno G., De-Callatay B., De-Favereau-de-Jeneret J., Delaere C., De-Vlsscher S., Favart D., Gregolre G., Keutgen Th., Lelbenguth G., Lemaltre V., Mlchotte D., Mllltaru O., Ninane A., Ovyn S.,

Piotrzkowski K., Roberfroid V., Rouby X., Van-der-Aa O., Vander-Donckt M., Boulogne I., Dauble E., Defontaines F., Herquet P., Czellar S., Harkonen J., Karimaki V., Katajisto H., Linden T., Luukka P., Lampen T., Maenpaa T., Tuominen E., Tuominiemi J., Tuuva T., Ageron M., Chabanat E., Contardo D., Estre N., Haroutuman R., Lumb N., Mirabito L., Perries S., Trocme B., Blaes R., Charles F., Drouhin F., Ernenwein J.P., Fontaine J.C., Berst J.D., Brom J.M., Didierjean F., Goerlach U., Gross L., Juillot P., Lounis A., Maazouzi C., Olivetto C., Strub R., Vanhove P., Vintache D., Adolphi R., Brauer R., Braunschweig W., Esser H., Feld L., Heister A., Karpinski W., Klein K., König S., Kukulies C., Olzem J., Ostaptchouk A., Pandoulas D., Pierschel G., Raupach F., Schael S., Schultz von Dratzig A., Schwering G., Siedling R., Thomas M., Wlochal M., Beissel F., Boffin K.-D., Duda M., Flossdorf A., Flugge G., Franke T., Hangarter K., Hegner B., Hermanns Th., Kasselmann S., Kress Th., Linn A., Mnich J., Nowack A., Poettgens M., Pooth O., Reinhold B., Bleyl M., Holm U., Klanner R., Pein U., Schleper P., Schirm N., Steinbrück G., Stoye M., Tesch S., van Staa R., Wick K., Atz B., Barvich T., Blüm P., de Boer W., Boegelspacher F., Dirkes G., Fahrer M., Fernandez J., Frey M., Fürgeri A., Grigoriev E., Hartmann F., Heier S., Müller T., Ortega-Gomez T., Simonis H.-J., Steck P., Theel A., Weiler T., Zhükov V., Creanza D., De Filippis N., de Palma M., De Robertis G., Fiore L., Giordano D., Maggi G., Mennea M., My S., Radicci V., Selvaggi G., Silvestris L., Tempesta P., Zito G., Albergo S., Bellini V., Chiorboli M., Costa S., Potenza R., Sütera C., Tricomi A., Tüve C., Bocci A., Ciülli V., Civinini C., D'Alessandro R., Focardi E., Landi G., Macchiolo A., Magini N., Mersi S., Marchettini C., Meschini M., Paoletti S., Parrini G., Ranieri R., Sani M., Bacchetta N., Bisello D., Candelori A., Dorigo T., Giübilato P., Kaminsky A., Loreti M., Nigro M., Paccagnella A., Rando R., Angarano M.M., Babücci E., Benedetti D., Biasini M., Bilei G.M., Brünetti M.T., Checcücci B., Dinü N., Fano L., Giorgi M., Lariccia P., Mantovani G., Postolache V., Püscalaü M., Ricci D., Santinelli R., Santocchia A., Servoli L., Zücchetti C., Azzürri P., Bagliesi G., Basti A., Bernardini J., Boccali T., Borrello L., Bosi F., Castaldi R., D'Alfonso M., Dell'Orso R., Dütta S., Foa L., Gennai S., Giammanco A., Giassi A., Lomtadze T., Mangano B., Messineo A., Moggi A., Palla F., Palmonari F., Raffaelli F., Rizzi A., Rizzi D., Segneri G., Sentenac D., Sgüazzoni G., Spagnolo P., Tonelli G., Verdini P.G., Biino C., Costa M., Demaria N., Favro G., Trapani P., Peroni C., Romero A., Migliore E., Abbaneo D., Ahmed F., Bartalini P., Bernardino-Rodrigüez N., Breüker H., Büchmüller O., Carrone E., Cattai A., Chierici R., Cücciarelli S., Dierlamm A., Eppard M., Frey A., Gill K., Grabit R., Honma A., Hühtinen M., Magazzü G., Mannelli M., Marchioro A., Onnela A., Perea-Solano B., Petagna P., Postema H., Risoldi M., Rolandi G., Siegrist P., Troska I., Tsiroü A., Vasey F., Weber M., Wittmer B., Bertl W., Gabathüler K., Horisberger R., Kästli H.-Ch., Kotlinski D., MacPherson A., Rohe T., Freüdenreich K., Lüstermann W., Paüss F., Eichler R., Erdmann W., Grab C., Schoning A., Amsler C., Chiochia V., Dorokhov A., Hörmann C., Prays H., Prokofiev K., Regenfüs C., Robmann P., Speer T., Bell K.W., Coüghlan J., French M., Halsall R., Jones L., Pearson M., Rogers G., Tomalin I., Bainbridge R., Barrillon P., Colling D., Dris S., Foüdas C., Fülcher J., Hall G., Iles G., Jones J., Leaver J., Macevoy B.C., Noy M., Raymond D.M., Takahashi M., Zorba O., Barnett B., Chien C.-Y., Kim D.W., Liang G., Swartz M., Atac M., Demarteau M., Joshi U., Kwan S., Spiegel L., Tkaczyk S., Gerber C.E., Shabalina E., Ten T., Lander R., Pellett D., Gobbi B., Kubantsev M., Malik S., Tilden R., Baringer P., Bean A., Christofek L., Coppage D., Bolton T.A., Demina R., Kahl W.E., Khanov A., Korjenevski S., Pukhaeva N., Reay N.W., Rizatdinova F., Sidwell R.A., Stanton N.R., Cremaldi L., Sanders D., Bartz E., Doroshenko J., Koeth T., Perera L., Schnetzer S., Stone R., Worm S., Gartung P., Hanson G.G., Jeng G.Y., Páztor G., Eusebi R., Halkiadakis E., Hocker A., Tipton P., Affolder A., Campagnari C., Hale D., Incandela J., Kyre S., Lamb J., Taylor R., White D., Bolla G., Bortoletto D., Garfinkel A., Rott C., Roy A.,"The effect of highly ionising particles on the CMS silicon strip tracker",2005,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","543","2-3",,"463","482",,"10.1016/j.nima.2004.11.049","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

20244373770&doi=10.1016%2fj.nima.2004.11.049&partnerID=40&md5=201099aaca9db9625e6790cef0ae1a5a"

239. Cellere G., Paccagnella A., Mazzocchi A., Valentini M.G.,"Influence of dielectric breakdown on MOSFET drain current",2005,"IEEE Transactions on Electron Devices","52","2",,"211","213",,"10.1109/TED.2004.842711","https://www.scopus.com/inward/record.uri?eid=2-s2.0-13444291995&doi=10.1109%2fTED.2004.842711&partnerID=40&md5=46397ba2f655d6bce58b99c2c6085d35"

240. Porti M., Nafría M., Aymerich X., Cester A., Paccagnella A., Cimino S.,"Irradiation induced weak spots in SiO2 gate oxides of MOS devices observed with C-AFM",2005,"Electronics Letters","41","2",,"101","103",,"10.1049/el:20057289","https://www.scopus.com/inward/record.uri?eid=2-s2.0-13844256591&doi=10.1049%2fel%3a20057289&partnerID=40&md5=13042fd6192c3cab7392a4b1ca187480"

241. Gerardin S., Cester A., Paccagnella A., Ghidini G.,"MOSFET drain current reduction under Fowler-Nordheim and channel hot carrier injection before gate oxide breakdown",2004,"Materials Science in Semiconductor Processing","7","4-6 SPEC. ISS.",,"175","180",,"10.1016/j.mssp.2004.09.114","https://www.scopus.com/inward/record.uri?eid=2-s2.0-9544242749&doi=10.1016%2fj.mssp.2004.09.114&partnerID=40&md5=61a309787c571d920c3d644ef3d52949"

242. Paccagnella A., Cester A., Cellere G.,"Ionizing radiation effects on MOSFET thin and ultra-thin gate oxides",2004,"Technical Digest - International Electron Devices Meeting, IEDM",,,,"473","476",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-21644482654&partnerID=40&md5=810c2484fb8dc423cbcbec7dfb30544e"

243. Bolognani S., Ceschia M., Mattavelli P., Paccagnella A., Zigliotto M.,"Improved FPGA-based dead time compensation for SVM inverters",2004,"IEE Conference Publication","2",,,"662","667",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-17044395452&partnerID=40&md5=43f870e774350ea0909568ec357ffe5d"

244. Gellere G., Paccagnella A., Visconti A., Bonanomi M., Candelori A.,"Transient conductive path induced by a single ion in 10 nm SiO2 layers",2004,"IEEE Transactions on Nuclear Science","51","6 II",,"3304","3311",,"10.1109/TNS.2004.839146","https://www.scopus.com/inward/record.uri?eid=2-s2.0-11044226028&doi=10.1109%2fTNS.2004.839146&partnerID=40&md5=fccca454c3cbd09df62b460773ab3d09"

245. Cellere G., Paccagnella A., Lora S., Pozza A., Tao G., Scarpa A.,"Charge loss after60Co irradiation on Flash arrays",2004,"European Space Agency, (Special Publication) ESA SP",,"536", LN6,"673","677",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-23844438948&partnerID=40&md5=0e7d44339ce7a1ed7d491ec3ca36357d"

246. Cellere G., Paccagnella A., Visconti A., Bonanomi M., Caprara P., Lora S.,"A model for TID effects on floating gate memory cells",2004,"IEEE Transactions on Nuclear Science","51","6 II",,"3753","3758",,"10.1109/TNS.2004.839243","https://www.scopus.com/inward/record.uri?eid=2-s2.0-11044222874&doi=10.1109%2fTNS.2004.839243&partnerID=40&md5=d6908a2c88f4ffa6513b025c997e95b6"

247. Violante M., Sterpone L., Ceschia M., Bortolato D., Bernardi P., Reorda M.S., Paccagnella A.,"Simulation-based analysis of SEU effects in SRAM-based FPGAs",2004,"IEEE Transactions on Nuclear Science","51","6

II",,"3354","3359",,"10.1109/TNS.2004.839516","https://www.scopus.com/inward/record.uri?eid=2-s2.0-11044235410&doi=10.1109%2fTNS.2004.839516&partnerID=40&md5=5f24c0542bfe525a001deada92463a40"

248. Cester A., Schwank J.R., Gerardin S., Vizkelethy G., Paccagnella A., Candelori A., Ghidini G.,"Drain current decrease in MOSFETs after heavy ion irradiation",2004,"IEEE Transactions on Nuclear Science","51","6 II",,"3150","3157",,"10.1109/TNS.2004.839203","https://www.scopus.com/inward/record.uri?eid=2-s2.0-11044233448&doi=10.1109%2fTNS.2004.839203&partnerID=40&md5=198c901886f2c17d17f0a54ef89dca4d"

249. Cellere G., Paccagnella A., Lora S., Pozza A., Tao G., Scarpa A.,"Charge loss after 60Co irradiation of flash arrays",2004,"IEEE Transactions on Nuclear Science","51","5 III",,"2912","2916",,"10.1109/TNS.2004.835056","https://www.scopus.com/inward/record.uri?eid=2-s2.0-8344219866&doi=10.1109%2fTNS.2004.835056&partnerID=40&md5=76b93578119fbe6c4d108eb70801aa6d"

250. Cellere G., Paccagnella A.,"A review of ionizing radiation effects in floating gate memories",2004,"IEEE Transactions on Device and Materials Reliability","4","3",,"359","370",,"10.1109/TDMR.2004.836726","https://www.scopus.com/inward/record.uri?eid=2-s2.0-11144228941&doi=10.1109%2fTDMR.2004.836726&partnerID=40&md5=9381d16cfaec22f36c94db8912f14152"

251. Cellere G., Valentini M.G., Paccagnella A.,"Effect of channel width, length, and latent damage on NBTI",2004,"2004 International Conference on Integrated Circuit Design and Technology, ICICDT",,,,"303","306",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-4143060374&partnerID=40&md5=5b7b770d7a4abe4ab5ffdf98a93a3e53"

252. Cellere G., Paccagnella A., Caprara P., Visconti A.,"Heavy ion irradiation of Floating Gate memory cells",2004,"2004 International Conference on Integrated Circuit Design and Technology, ICICDT",,,,"287","290",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-4143087135&partnerID=40&md5=d100e4ce0c24cad91e05dbf91d3bbfc6"

253. Cellere G., Paccagnella A., Visconti A., Bonanomi M.,"Ionizing radiation effects on floating gates",2004,"Applied Physics Letters","85","3",,"485","487",,"10.1063/1.1773932","https://www.scopus.com/inward/record.uri?eid=2-s2.0-4043079778&doi=10.1063%2f1.1773932&partnerID=40&md5=5060dc2334cc038d961cbabf535f1c96"

254. Bellato M., Bernardi P., Bortolato D., Candelori A., Ceschia M., Paccagnella A., Rebaudengo M., Reorda M.S., Violante M., Zambolin P.,"Evaluating the effects of SEUs affecting the configuration memory of an SRAM-based FPGA",2004,"Proceedings - Design, Automation and Test in Europe Conference and Exhibition","1",,,"584","589",,"10.1109/DATE.2004.1268908","https://www.scopus.com/inward/record.uri?eid=2-s2.0-3042615426&doi=10.1109%2fDATE.2004.1268908&partnerID=40&md5=68ee41139fdfb71a37673208139187f8"

255. Cester A., Paccagnella A.,"Ionizing radiation effects on ultra-thin oxide MOS structures",2004,"International Journal of High Speed Electronics and Systems","14","2",,"563","574",,"10.1142/S012915640400251X","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

8444241545&doi=10.1142%2fS012915640400251X&partnerID=40&md5=2fba821d31d637855064f9dad52d1d58"

256. Cester A., Bandiera L., Cimino S., Paccagnella A., Ghidini G.,"Incidence of oxide and interface degradation on MOSFET performance",2004,"Microelectronic Engineering","72","1-4",,"66","70",,"10.1016/j.mee.2003.12.018","https://www.scopus.com/inward/record.uri?eid=2-s2.0-1642634446&doi=10.1016%2fj.mee.2003.12.018&partnerID=40&md5=86228e4a7725ff2af5f8b08be263ce70"

257. Ceschia M., Violante M., Reorda M.S., Paccagnella A., Bernardi P., Rebaudengo M., Bortolato D., Bellato M., Zambolin P., Candelori A.,"Erratum: Identification and classification of single-event upsets in the configuration memory of SRAM-based FPGAs (IEEE Transactions on Nuclear Science (2003) 50 (2088-2094))",2004,"IEEE Transactions on Nuclear Science","51","2",,"328","",,"10.1109/TNS.2004.827944","https://www.scopus.com/inward/record.uri?eid=2-s2.0-2442436728&doi=10.1109%2fTNS.2004.827944&partnerID=40&md5=8817a1f870533edca922107d70ffc1fa"

258. Cellere G., Paccagnella A., Valentini M.G.,"FGA Effects on Plasma-Induced Damage: Beyond the Appearances",2004,"IEEE Transactions on Electron Devices","51","3",,"332","338",,"10.1109/TED.2003.822275","https://www.scopus.com/inward/record.uri?eid=2-s2.0-1642281922&doi=10.1109%2fTED.2003.822275&partnerID=40&md5=38388de5711c5164ae3219c6153183e5"

259. Cester A., Paccagnella A., Ghidini G., Deleonibus S., Guegan G.,"Collapse of MOSFET Drain Current After Soft Breakdown",2004,"IEEE Transactions on Device and Materials Reliability","4","1",,"63","72",,"10.1109/TDMR.2003.820296","https://www.scopus.com/inward/record.uri?eid=2-s2.0-2342516744&doi=10.1109%2fTDMR.2003.820296&partnerID=40&md5=6415d72f60dae364bce9a35ddd186126"

260. Cellere G., Valentini M.G., Caminati M., Paccagnella A.,"Influence of process parameters on plasma damage during inter-metal dielectric deposition",2004,"Microelectronic Engineering","71","2",,"133","138",,"10.1016/j.mee.2003.10.002","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0347601905&doi=10.1016%2fj.mee.2003.10.002&partnerID=40&md5=b35f7cabe55839610a6bf0993d7df627"

261. Miranda E., Cester A., Paccagnella A.,"Stochastic modeling of progressive breakdown in ultrathin SiO2 films",2003,"Applied Physics Letters","83","24",,"5014","5016",,"10.1063/1.1634372","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0346503157&doi=10.1063%2f1.1634372&partnerID=40&md5=15f5c730f96b2a1e5d71ab2eacfcf468"

262. Berto S., Paccagnella A., Ceschia M., Bolognani S., Zigliotto M.,"Potentials and pitfalls of FPGA application in inverter drives - A case study",2003,"Proceedings of the IEEE International Conference on Industrial Technology","1",,,"500","505",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-19844377862&partnerID=40&md5=623fc9f26fe215f7ae6bbb09bd6f1d79"

263. Cester A., Cimino S., Miranda E., Candelori A., Ghidini G., Paccagnella A.,"Statistical Model for Radiation-Induced Wear-Out of Ultra-Thin Gate Oxides after Exposure to Heavy Ion Irradiation",2003,"IEEE Transactions on Nuclear Science","50","6 I",,"2167","2175",,"10.1109/TNS.2003.821606","https://www.scopus.com/inward/record.uri?eid=2

-s2.0-1242310268&doi=10.1109%2fTNS.2003.821606&partnerID=40&md5=85e3484cd2e9972dca686558f70db1be"

264. Larcher L., Cellere G., Paccagnella A., Chimenton A., Candelori A., Modelli A.,"Data Retention after Heavy Ion Exposure of Floating Gate Memories: Analysis and Simulation",2003,"IEEE Transactions on Nuclear Science","50","6 I",,"2176","2183",,"10.1109/TNS.2003.821598","https://www.scopus.com/inward/record.uri?eid=2-s2.0-1242265231&doi=10.1109%2fTNS.2003.821598&partnerID=40&md5=9e11ae8459e23af64bf643bb85d0dc53"

265. Ceschia M., Violante M., Reorda M.S., Paccagnella A., Bernardi P., Rebaudengo M., Bortolato D., Bellato M., Zambolin P., Candelori A.,"Identification and Classification of Single-Event Upsets in the Configuration Memory of SRAM-Based FPGAs",2003,"IEEE Transactions on Nuclear Science","50","6 I",,"2088","2094",,"10.1109/TNS.2003.821411","https://www.scopus.com/inward/record.uri?eid=2-s2.0-10744225350&doi=10.1109%2fTNS.2003.821411&partnerID=40&md5=cf6fa5019c96da3dd2e2652de2f36c30"

266. Berto S., Bolognani S., Ceschia M., Paccagnella A., Zigliotto M.,"FPGA-based random PWM with real-time dead time compensation",2003,"PESC Record - IEEE Annual Power Electronics Specialists Conference","2",,,"513","518",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0042659128&partnerID=40&md5=4e40075a27b88829872a125e66d3f1bf"

267. Cimino S., Cester A., Paccagnella A., Ghidini G.,"Ionising radiation effects on MOSFET drain current",2003,"Microelectronics Reliability","43","8",,"1247","1251",,"10.1016/S0026-2714(03)00179-3","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0043166507&doi=10.1016%2fS0026-2714%2803%2900179-3&partnerID=40&md5=6d5dc4eaa154ecb072a19b951f2b111c"

268. Cester A., Cimino S., Paccagnella A., Ghidini G., Guegan G.,"Collapse of MOSFET drain current after soft breakdown and its dependence on the transistor aspect ratio W/L",2003,"Annual Proceedings - Reliability Physics (Symposium)",,,,"189","195",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0037972834&partnerID=40&md5=82aaef1b8fb04e8ebea5a017f11fe754"

269. Cellere G., Valentini M.G., Pantisano L., Cheung K.P., Paccagnella A.,"Different nature of process-induced and stress-induced defects in thin SiO 2 layers",2003,"IEEE Electron Device Letters","24","6",,"393","395",,"10.1109/LED.2003.813369","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0041590935&doi=10.1109%2fLED.2003.813369&partnerID=40&md5=db5cc5fb69d2f8b742dccd5531bcb13b"

270. Miranda E., Cester A., Paccagnella A.,"Logistic model for leakage current in electrical stressed ultra-thin gate oxides",2003,"Electronics Letters","39","9",,"749","750",,"10.1049/el:20030485","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0038734418&doi=10.1049%2fel%3a20030485&partnerID=40&md5=6dcb1278235cce4fec98e547d791b6c2"

271. Miranda E., Bandiera L., Cester A., Paccagnella A.,"Logistic modeling of progressive breakdown in ultrathin gate oxides",2003,"European Solid-State Device Research Conference",,, 1256816,"83","86",,"10.1109/ESSDERC.2003.1256816","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

84907686747&doi=10.1109%2fESSDERC.2003.1256816&partnerID=40&md5=b616ad01008723c6659bb3c48964fde7"

272. Cester A., Cimino S., Paccagnella A., Ghidini G., Guegan G.,"Collapse of MOSFET drain current after Soft Breakdown and its dependence on the transistor aspect ratio W/L",2003,"IEEE International Reliability Physics Symposium Proceedings","2003-January",, 1197744,"189","195",,"10.1109/RELPHY.2003.1197744","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84975882600&doi=10.1109%2fRELPHY.2003.1197744&partnerID=40&md5=46cf2a0185a2c1a55ad91f66d4834b31"

273. Cimino S., Paccagnella A., Ghibaudo G., Ghidini G., Wyss J.,"Accelerated Wear-Out of Ultra-Thin Gate Oxides After Irradiation",2003,"IEEE Transactions on Nuclear Science","50","3",,"729","734",,"10.1109/TNS.2003.811281","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0038383138&doi=10.1109%2fTNS.2003.811281&partnerID=40&md5=d0a3ca99839660d464cbe854cec7bc69"

274. Cellere G., Paccagnella A., Lora S., Pozza A., Tao G., Scarpa A.,"Charge loss after 60Co irradiation on Flash Arrays",2003,"European Space Agency, (Special Publication) ESA SP","2003-September",,,"673","677",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-84995693623&partnerID=40&md5=57e3102016e0eee040b9e74622f43a6d"

275. Cellere G., Valentini M.G., Caminati M., Vitali M.E., Moro A., Paccagnella A.,"Plasma damage reduction by using ISSG gate oxides",2003,"International Symposium on Plasma Process-Induced Damage, P2ID, Proceedings","2003-January",, 1200916,"65","68",,"10.1109/PPID.2003.1200916","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84973658808&doi=10.1109%2fPPID.2003.1200916&partnerID=40&md5=25066d3d649b0ef3cb56d785883bbc65"

276. Bandiera L., Cester A., Cimino S., Gerardin S., Paccagnella A., Ghidini G.,"Degradation of low frequency noise and DC characteristics on MOSFETs and its correlation with SILC",2003,"European Solid-State Device Research Conference",,, 1256869,"283","286",,"10.1109/ESSDERC.2003.1256869","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84907705416&doi=10.1109%2fESSDERC.2003.1256869&partnerID=40&md5=24c15aa4f05b706377b5dfeb32a0dac6"

277. Violante M., Ceschia M., Sonza Reorda M., Paccagnella A., Bernardi P., Rebaudengo M., Bortolato D., Bellato M., Zambolin P., Candelori A.,"Analyzing SEU effects is SRAM-based FPGAsb",2003,"Proceedings - 9th IEEE International On-Line Testing Symposium, IOLTS 2003",,, 1214377,"119","123",,"10.1109/OLT.2003.1214377","https://www.scopus.com/inward/record.uri?eid=2-s2.0-27944443776&doi=10.1109%2fOLT.2003.1214377&partnerID=40&md5=974f0dc12861af5b5f68a1a7586f15c2"

278. Bellato M., Ceschia M., Menichelli M., Papi A., Wyss J., Paccagnella A.,"Ion beam testing of SRAM-based FPGA's",2002,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS","1","2",,"474","480",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0036992534&partnerID=40&md5=219c4ce23cee5aba6df665c5b62dd535"

279. Cellere G., Paccagnella A., Larcher L., Chimenton A., Wyss J., Candelori A., Modelli A.,"Anomalous charge loss from floating-gate memory cells due to heavy ions irradiation",2002,"IEEE Transactions on Nuclear Science","49 I","6",,"3051","3058",,"10.1109/TNS.2002.805339","https://www.scopus.com/inward/record.uri?e

id=2-s2.0-0036948062&doi=10.1109%2fTNS.2002.805339&partnerID=40&md5=d39eb6cb9d2b58fb297f487eb2bc178e"

280. Cellere G., Larcher L., Valentini M.G., Paccagnella A.,"Plasma-induced micro breakdown in small-area MOSFETs",2002,"IEEE Transactions on Electron Devices","49","10",,"1768","1774",,"10.1109/TED.2002.803637","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0036772475&doi=10.1109%2fTED.2002.803637&partnerID=40&md5=73aa0e843ea4f5c09b4eba0ac7bd7aa1"

281. Cellere G., Larcher L., Valentini M.G., Paccagnella A.,"Micro breakdown in small-area ultrathin gate oxides",2002,"IEEE Transactions on Electron Devices","49","8",,"1367","1374",,"10.1109/TED.2002.801443","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0036685471&doi=10.1109%2fTED.2002.801443&partnerID=40&md5=e03606f1e6f9020b5199b3db90e7a1e3"

282. Cester A., Bandiera L., Ghidini G., Bloom I., Paccagnella A.,"Soft breakdown current noise in ultra-thin gate oxides",2002,"Solid-State Electronics","46","7",,"1019","1025",,"10.1016/S0038-1101(02)00036-9","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0036642864&doi=10.1016%2fS0038-1101%2802%2900036-9&partnerID=40&md5=02bd846bb88d4e9105c3340514fc27dd"

283. Pantisano L., Cheung K.P., Roussel P.J., Paccagnella A.,"The impact of plasma-charging damage on the RF performance of deep-submicron MOSFET",2002,"IEEE Electron Device Letters","23","6",,"309","311",,"10.1109/LED.2002.1004218","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0036609981&doi=10.1109%2fLED.2002.1004218&partnerID=40&md5=aa9af9d430891664e96d558888b4428f"

284. Cester A., Paccagnella A., Ghidini G.,"Stress induced leakage current under pulsed voltage stress",2002,"Solid-State Electronics","46","3",,"399","405",,"10.1016/S0038-1101(01)00121-6","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0036498141&doi=10.1016%2fS0038-1101%2801%2900121-6&partnerID=40&md5=391838af9e98fc3f5f509897fb8e0aeb"

285. Civinini C., Albergo S., Angarano M., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Bozzi C., Braibant S., Breuker H., Bruzzi M., Buffini A., Busoni S., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Creanza D., D'Alessandro R., Da Rold M., Demaria N., de Palma M., Dell'Orso R., Della Marina R., Dutta S., Eklund C., Feld L., Fiore L., Focardi E., French M., Freudenreich K., Frey A., Fürtjes A., Giassi A., Giorgi M., Giraldo A., Glessing B., Gu W.H., Hall G., Hammarstrom R., Hebbeker T., Honma A., Hrubec J., Huhtinen M., Kaminsky A., Karimaki V., Koenig S., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Mättig P., Maggi G., Mannelli M., Mantovani G., Marchioro A., Mariotti C., Martignon G., Mc Evoy B., Meschini M., Messineo A., Migliore E., My S., Paccagnella A., Palla F., Pandoulas D., Papi A., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Radicci V., Raffaelli F., Raymond M., Santocchia A., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Starodumov A., Stavitski I., Stefanini G., Surrow B., Tempesta P., Tonelli G., Tricomi A., Tuuva T., Vannini C., Verdini P.G., Viertel G., Xie Z., Li Y., Watts S., Wittmer B.,"CMS silicon tracker developments",2002,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","477","1-3",,"440","445",,"10.1016/S0168-9002(01)01824-1","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0037147806&doi=10.1016%2fS0168-9002%2801%2901824-1&partnerID=40&md5=1214751150f182d9ecd1cb9c21306e59"

286. Cellere G., Valentini M.G., Paccagnella A.,"Plasma-induced si/sio2 interface damage in cmos",2002,"Microelectronic Engineering","63","4",,"433","442",,"10.1016/S0167-9317(02)00594-4","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0036722765&doi=10.1016%2fS0167-9317%2802%2900594-4&partnerID=40&md5=8b75a3e9b599a8de3ada4e1645e151a1"
287. Cellere G., Valentini M.G., Caminati M., Paccagnella A.,"P2ID in a modern CMOS technology",2002,"International Symposium on Plasma Process-Induced Damage, P2ID, Proceedings","2002-January",, 1042612,"72","75",,"10.1109/PPID.2002.1042612","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84948739724&doi=10.1109%2fPPID.2002.1042612&partnerID=40&md5=4c89b65172e6ad206ecf53989e8e2d2a"
288. Cellere G., Valentini M.G., Baraldo A., Paccagnella A.,"Plasma induced damage from via etching in pMOSFETs",2002,"International Symposium on Plasma Process-Induced Damage, P2ID, Proceedings","2002-January",, 1042622,"114","117",,"10.1109/PPID.2002.1042622","https://www.scopus.com/inward/record.uri?eid=2-s2.0-40549122280&doi=10.1109%2fPPID.2002.1042622&partnerID=40&md5=bd960dc1e25074e8b39b7529cd05e950"
289. Cellere G., Paccagnella A., Pantisano L., Valentini M.G., Flament O., Mousseau O., Fuochi P.G.,"Radiation-induced depassivation of latent plasma damage",2002,"Microelectronic Engineering","60","3-4",,"439","450",,"10.1016/S0167-9317(01)00704-3","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0036532414&doi=10.1016%2fS0167-9317%2801%2900704-3&partnerID=40&md5=0c4daa3e7b1dc20ca1db6776fd355956"
290. Ceschia M., Bellato M., Paccagnella A., Kaminski A., Lee S.-C., Wan C., Menichelli M., Papi A., Wyss J.,"Ion beam testing of ALTERA APEX FPGAs",2002,"IEEE Radiation Effects Data Workshop","2002-January",, 1045531,"45","50",,"10.1109/REDW.2002.1045531","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84948768331&doi=10.1109%2fREDW.2002.1045531&partnerID=40&md5=673fc5f8f27e0a7d232138c1cf54c3b8"
291. Bellazzini R., Andreanelli L., Angelini F., Allegretti S., Bagagli R., Baldini L., Barbiellini G., Belli F., Brez A., Ceccanti M., Cecchi C., Ceschia M., Cohen Tanugi J., De Angelis A., Favuzzi C., Gargano F., Giannitrapani R., Giglietto A., Giordano F., Kuss M., Latronico L., Longo F., Loparco F., Lubrano P., Massai M.M., Mazziotta M.N., Minuti M., Morselli A., Omodei N., Paccagnella A., Pagliarone C., Picozza P., Prest M., Raino S., Rando R., Spandre G., Spinelli P., Vigiani L., Zetti F.,"The GLAST tracker design and construction",2002,"Nuclear Physics B - Proceedings Supplements","113","1-3",,"303","309",,"10.1016/S0920-5632(02)01856-X","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0036452654&doi=10.1016%2fS0920-5632%2802%2901856-X&partnerID=40&md5=c94a001110273f6cb560fb3d7523e525"
292. Larcher L., Paccagnella A.,"A model of the stress induced leakage current in gate oxides",2001,"IEEE Transactions on Electron Devices","48","2",,"285","288",,"10.1109/16.902728","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0035248925&doi=10.1109%2f16.902728&partnerID=40&md5=349162f0c24054b8850d8cc8e1199944"
293. Gellere G., Pantisano L., Valentini M.G., Paccagnella A.,"Depassivation of latent plasma damage in nmosfets",2001,"IEEE Transactions on Device and Materials Reliability","1","3",,"144","149",,"10.1109/7298.974829","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

0001596172&doi=10.1109%2f7298.974829&partnerID=40&md5=f4af470183999904c96d4a5b1278b58e"

294. Cester A., Bandiera L., Ceschia M., Ghidini G., Paccagnella A.,"Noise characteristics of radiation-induced soft breakdown current in ultrathin gate oxides",2001,"IEEE Transactions on Nuclear Science","48","6 I",,"2093","2100",,"10.1109/23.983178","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0035720550&doi=10.1109%2f23.983178&partnerID=40&md5=79731a2f4f2a5f512214619dc9178461"
295. Cellere G., Pellati P., Chimenton A., Wyss J., Modelli A., Larcher L., Paccagnella A.,"Radiation effects on floating-gate memory cells",2001,"IEEE Transactions on Nuclear Science","48","6 I",,"2222","2228",,"10.1109/23.983199","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0035722077&doi=10.1109%2f23.983199&partnerID=40&md5=bfa1e2d59916e2b47eb0c0d7855d8e50"
296. Bandiera L., Cester A., Paccagnella A., Ghidini G., Bloom I.,"Detrended fluctuation analysis of the soft breakdown current",2001,"Microelectronic Engineering","59","1-4",,"49","53",,"10.1016/S0167-9317(01)00643-8","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0035498573&doi=10.1016%2fS0167-9317%2801%2900643-8&partnerID=40&md5=81db7cfa3521591fb9d3865cbed33276"
297. Cester A., Paccagnella A., Suñé J., Miranda E.,"Post-radiation-induced soft breakdown conduction properties as a function of temperature",2001,"Applied Physics Letters","79","9",,"1336","1338",,"10.1063/1.1398329","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0040752625&doi=10.1063%2f1.1398329&partnerID=40&md5=aaad24ab672bab9c6db42fc8fd9ee82e"
298. Cester A., Paccagnella A., Ghidini G.,"Time decay of stress induced leakage current in thin gate oxides by low-field electron injection",2001,"Solid-State Electronics","45","8",,"1345","1353",,"10.1016/S0038-1101(00)00264-1","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0035417323&doi=10.1016%2fS0038-1101%2800%2900264-1&partnerID=40&md5=baea539805e51f42633b3201d9ef72cc"
299. Albergo S., Angarano M., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Basti A., Biggeri U., Biino C., Bilei G.M., Bisello D., Boemi D., Bosi F., Borello L., Braibant S., Breuker H., Brunetti M.T., Bruzzi M., Buffini A., Busoni S., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Costa M., Creanza D., D'Alessandro R., DeMaria N., de Palma M., Dell'Orso R., Dutta S., Favro G., Fiore L., Focardi E., French M., Freudenreich K., Frey A., Friedl M., Fürtjes A., Giassi A., Giorgi M., Giraldo A., Glessing W., Gu W.H., Hall G., Hammarstrom R., Hebbeker T., Honkanen A., Honma A., Hrubec J., Huhtinen M., Kaminsky A., Karimaki V., Koenig S., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Mattig P., Maggi G., Mannelli M., Mantovani G., Marchioro A., Mariotti C., Martignon G., Mc Evoy B., Meschini M., Messineo A., Migliore E., My S., Neviani A., Paccagnella A., Palla F., Pandoulas D., Papi A., Parrini G., Passeri D., Pernicka M., Pieri M., Piperov S., Potenza R., Radicci V., Raffaelli F., Raymond M., Rizzo F., Santocchia A., Segneri G., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Starodumov A., Stavitski I., Surrow B., Tempesta P., Tonelli G., Tricomi A., Tuominiemi J., Tuuva T., Verdini P.G., Viertel G., Xie Z., Yahong L., Watts S., Wittmer B.,"Optimization of the silicon sensors for the CMS tracker",2001,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","466","2",,"300","307",,"10.1016/S0168-9002(01)00544-7","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0035399219&doi=10.1016%2fS0168-9002%2801%2900544-7&partnerID=40&md5=066c09ea45421b0f9e89e9c1cb5465b5"

300. Candelori A., Paccagnella A., Raggi G., Wyss J., Bisello D., Ghidini G.,"High energy Si ion irradiation effects on 10 nm thick oxide MOS capacitors",2001,"Journal of Non-Crystalline Solids","280","1-3",,"193","201",,"10.1016/S0022-3093(00)00375-6","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0034818431&doi=10.1016%2fS0022-3093%2800%2900375-6&partnerID=40&md5=19828e52bd8d63c365a61b36ec221302"
301. Cellere G., Valentini M.G., Paccagnella A.,"Correlation between soft breakdown and plasma process induced damage",2001,"International Symposium on Plasma Process-Induced Damage, P2ID, Proceedings",,,,"40","43",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0034834927&partnerID=40&md5=586522cc31db5300f22dfe47e0a5acef"
302. Cester A., Bandiera L., Paccagnella A., Ghidini G.,"Leakage current in ultra thin oxides: SILC or soft breakdown?",2001,"European Solid-State Device Research Conference",,,,"463","466",,"10.1109/ESSDERC.2001.195301","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84907521478&doi=10.1109%2fESSDERC.2001.195301&partnerID=40&md5=072b3d57ffd146bc23a7eb53a78b7d2e"
303. Candelori A., Bisello D., Ceschia M., Paccagnella A., Wyss J., Ghidini G.,"Thin Oxide Degradation After High-Energy Ion Irradiation",2001,"IEEE Transactions on Nuclear Science","48","5",,"1735","1743",,"10.1109/23.960365","https://www.scopus.com/inward/record.uri?eid=2-s2.0-85008043223&doi=10.1109%2f23.960365&partnerID=40&md5=b38d82dab155342d48d8f3e7f7faeaaa"
304. Cester A., Bandiera L., Suñe J., Boschiero L., Ghidini G., Paccagnella A.,"A novel approach to quantum point contact for post soft breakdown conduction",2001,"Technical Digest-International Electron Devices Meeting",,,,"305","308",,"10.1109/IEDM.2001.979490","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0035718183&doi=10.1109%2fIEDM.2001.979490&partnerID=40&md5=d7efde3ac366de6940bd9aefdd328e67"
305. Pantisano L., Cheung K.P., Smith P., Chen C.Y., Hwang D., Fiorillo S., Keller R., Paccagnella A.,"The impact of plasma charging damage on the RF performances of deep-submicron silicon MOSFET",2001,"International Symposium on Plasma Process-Induced Damage, P2ID, Proceedings",,,,"56","59",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0034829258&partnerID=40&md5=97579cf9a07d89e000b3789e05389b92"
306. Ceschia M., Paccagnella A., Sandrin S.,"Low field leakage current and soft breakdown in ultra-thin gate oxides after heavy ions, electrons or x-ray irradiation",2000,"IEEE Transactions on Nuclear Science","47","3 PART 1",,"566","573",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0034205654&partnerID=40&md5=d7873331f261c0759d45ad57d222be13"
307. Ceschia M., Paccagnella A., Cester A., Ghidini G., Wyss J.,"From radiation induced leakage current to soft breakdown in irradiated MOS devices with ultra-thin gate oxide",2000,"Materials Research Society Symposium - Proceedings","592",,,"201","206",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0034512753&partnerID=40&md5=7ae13f5d6dd9ec0c9c6c4714162253c4"
308. Pantisano Luigi, Paccagnella A., Cellere G., Colombo P., Valentini M.G.,"Interface state creation due to low-field latent damage depassivation",2000,"International Symposium on Plasma Process-Induced Damage, P2ID, Proceedings",,,,"93","96",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0034505577&partnerID=40&md5=47cc9149f0e66150453da233df35d5a5"

309. Gellere G., Paccagnella A., Pantisano L., Colombo P., Valentin M.G.,"Low-field latent plasma damage depassivation in thin-oxide MOS",2000,"Microelectronics Reliability","40","8-10",,"1347","1352",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0000371201&partnerID=40&md5=a98c4481a6b587a6982888ddef14d550"
310. Ceschia M., Paccagnella A., Turrini M., Candelori A., Ghidini G., Wyss J.,"Heavy ion irradiation of thin gate oxides",2000,"IEEE Transactions on Nuclear Science","47","6 III",,"2648","2655",,"10.1109/23.903821","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0034451210&doi=10.1109%2f23.903821&partnerID=40&md5=d436cf0ed79004c6e8476b45350a9774"
311. Bozzi C., Albergo S., Angarano M.M., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Bartalini P., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Braibant S., Breuker H., Bruzzi M., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Creanza D., D'Alessandro R., da Rold M., Demaria N., de Palma M., Dell'Orso R., Delia Marina R., Dutta S., Eklund C., Elliott-Peisert A., Feld L., Fiore L., Focardi E., French M., Freudenreich K., Fürtjes A., Giassi A., Giraldo A., Glessing B., Gu W.H., Hall G., Hammerstrom R., Hebbeker T., Hrubec J., Huhtinen M., Kaminsky A., Karimaki V., Koenig S., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Mättig P., Maggi G., Mannelli M., Mantovani G., Marchioro A., Mariotti C., Martignon G., Mc Evoy B., Meschini M., Messineo A., My S., Paccagnella A., Palla F., Pandoulas D., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Raffaelli F., Raso G., Raymond M., Rizzo F., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Skog K., Starodumov A., Stavitski I., Stefanini G., Tempesta P., Tonelli G., Tricomi A., Tuuva T., Vannini C., Verdini PG., Viertel G., Xie Z., Wang Y., Watts S., Wittmer B.,"Test results on heavily irradiated silicon detectors for the CMS experiment at LHC",2000,"IEEE Transactions on Nuclear Science","47","6 II",,"2092","2100",,"10.1109/23.903854","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0034450427&doi=10.1109%2f23.903854&partnerID=40&md5=0e672aaf7e998b2101f5251a15e57b22"
312. Focardi E., Albergo S., Angarano M., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Bozzi C., Braibant S., Breuker H., Bruzzi M., Buffini A., Busoni S., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Creanza D., D'Alessandro R., da Rold M., Demaria N., de Palma M., Dell'Orso R., della Marina R., Dutta S., Eklund C., Feld L., Fiore L., French M., Freudenreich K., Frey A., Fürtjes A., Giassi A., Giorgi M., Giraldo A., Glessing B., Gu W.H., Hall G., Hammerstrom R., Hebbeker T., Honma A., Hrubec J., Huhtinen M., Kaminskyd A., Karimaki V., Koenig St., Krammer M., Lariccia P., Lenzi M., Loreti M., Leubelsmeyer K., Lustermann W., Mättig P., Maggi G., Mannelli M., Mantovani G., Marchioro A., Mariotti C., Martignon G., Mc Evoy B., Meschini M., Messineo A., Migliore E., My S., Paccagnella A., Palla F., Pandoulas D., Papi A., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Radicci V., Raffaelli F., Raymond M., Rizzo F., Santocchia A., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Starodumov A., Stavitski I., Stefanini G., Surrow B., Tempesta P., Tonelli G., Tricomi A., Tuuva T., Vannini C., Verdini P.G., Viertel G., Xie Z., Li Y., Watts S., Wittmer B.,"CMS silicon tracker",2000,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","453","1-2",,"121","125",,"10.1016/S0168-9002(00)00616-1","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0034291540&doi=10.1016%2fS0168-9002%2800%2900616-1&partnerID=40&md5=a4dd74f4bbb2b3b4597daee3738e32c5"
313. Cester A., Paccagnella A., Ghidini G.,"Pulsed voltage stress on thin oxides",2000,"Electronics Letters","36","15",,"1319","1320",,"10.1049/el:20000946","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

0034229825&doi=10.1049%2fel%3a20000946&partnerID=40&md5=aafffb2225e2c905335fe5bd7f198c71"

314. Giraldo A., Paccagnella A., Minzoni A.,"Aspect ratio calculation in n-channel MOSFETs with a gate-enclosed layout",2000,"Solid-State Electronics","44","6",,"981","989",,"10.1016/S0038-1101(00)00010-1","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0033745487&doi=10.1016%2fS0038-1101%2800%2900010-1&partnerID=40&md5=d94f0a8c3131474a3701532a3db655fc"

315. Meschini M., Albergo S., Angarano M., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Bozzi C., Braibant S., Breuker H., Bruzzi M., Buffini A., Busoni S., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Creanza D., D'Alessandro R., da Rold M., Demaria N., de Palma M., Dell'Orso R., della Marina R., Dutta S., Eklund C., Elliott-Peisert A., Feld L., Fiore L., Focardi E., French M., Freudenreich K., Fürtjes A., Giassi A., Giorgi M., Giraldo A., Glessing B., Gu W.H., Hall G., Hammerstrom R., Hebbeker T., Hrubec J., Huhtinen M., Kaminsky A., Karimaki V., Koenig St., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Mättig P., Maggi G., Mannelli M., Mantovani G., Marchioro A., Mariotti C., Martignon G., Mc Evoy B., Messineo A., My S., Paccagnella A., Palla F., Pandoulas D., Papi A., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Radicci V., Raffaelli F., Raymond M., Santocchia A., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Skog K., Starodumov A., Stavitski I., Stefanini G., Tempesta P., Tonelli G., Tricomi A., Tuuva T., Vannini C., Verdini P.G., Viertel G., Xie Z., Li Y., Watts S., Wittmer B.,"Performance of CMS silicon microstrip detectors with the APV6 readout chip",2000,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","447","1",,"133","141",,"10.1016/S0168-9002(00)00181-9","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0033714652&doi=10.1016%2fS0168-9002%2800%2900181-9&partnerID=40&md5=35aa3f565590a16ab4e5257ed8f987b5"

316. Demaria N., Albergo S., Angarano M., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bolla G., Bosi F., Borrello L., Bortoletto D., Bozzi C., Braibant S., Breuker H., Bruzzi M., Buffini A., Busoni S., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Creanza D., D'Alessandro R., da Rold M., de Palma M., Dell'Orso R., della Marina R., Dutta S., Eklund C., Elliott-Peisert A., Favro G., Feld L., Fiore L., Focardi E., French M., Freudenreich K., Fürtjes A., Giassi A., Giorgi M., Giraldo A., Glessing B., Gu W.H., Hall G., Hammerstrom R., Hebbeker T., Hrubec J., Huhtinen M., Kaminsky A., Karimaki V., Koenig St., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Mättig P., Maggi G., Mannelli M., Mantovani G., Marchioro A., Mariotti C., Martignon G., Mc Evoy B., Meschini M., Messineo A., Migliore E., My S., Paccagnella A., Palla F., Pandoulas D., Papi A., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Radicci V., Raffaelli F., Raymond M., Santocchia A., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Skog K., Starodumov A., Stavitski I., Stefanini G., Tempesta P., Tonelli G., Tricomi A., Tuuva T., Vannini C., Verdini P.G., Viertel G., Xie Z., Li Y., Watts S., Wittmer B.,"New results on silicon microstrip detectors of CMS tracker",2000,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","447","1",,"142","150",,"10.1016/S0168-9002(00)00182-0","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0033703838&doi=10.1016%2fS0168-9002%2800%2900182-0&partnerID=40&md5=0b9cfe77b85d7cb42f6c8138589aadfa"

317. Riess P., Ceschia M., Paccagnella A., Ghibaudo G., Pananakakis G.,"Comparison of the electrical and thermal stability of stressor radiation-induced leakage current in thin oxides",2000,"Applied Physics Letters","76","9",,"1158","1160",,"10.1063/1.125969","https://www.scopus.com/inward/record.ur

i?eid=2-s2.0-0000361943&doi=10.1063%2f1.125969&partnerID=40&md5=e15fa468f0f295affa2d8dbf4987666a"

318. Snoeys W., Faccio F., Burns M., Campbell M., Cantatore E., Carrer N., Casagrande L., Cavagnoli A., Dachs C., Di Liberto S., Formenti F., Giraldo A., Heijne E.H.M., Jarron P., Letheren M., Marchioro A., Martinengo P., Meddi F., Mikulec B., Morando M., Morel M., Noah E., Paccagnella A., Ropotar I., Saladino S., Sansen W., Santopietro F., Scarlassara F., Segato G.F., Signe P.M., Soramel F., Vannucci L., Vleugels K.,"Layout techniques to enhance the radiation tolerance of standard CMOS technologies demonstrated on a pixel detector readout chip",2000,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","439","2",,"349","360",,"10.1016/S0168-9002(99)00899-2","https://www.scopus.com/inward/record.uri?eid=2-s2.0-17944387744&doi=10.1016%2fS0168-9002%2899%2900899-2&partnerID=40&md5=f1e06992d36457dec1c03f964252f79b"

319. Cester A., Paccagnella A., Bandiera L., Ghidini G.,"Switching behaviour and noise of soft breakdown current in ultra-thin gate oxides",2000,"European Solid-State Device Research Conference",,, 1503754,"500","503",,"10.1109/ESSDERC.2000.194824","https://www.scopus.com/inward/record.uri?eid=2-s2.0-36248929228&doi=10.1109%2fESSDERC.2000.194824&partnerID=40&md5=b00e78a21ec4bcf6c81051cdd77ee40f"

320. Cellere G., Paccagnella A., Pantisano L., Valentini M.G., Flament O., Mousseau O., Fuochi P.G.,"Radiation induced depassivation of latent plasma damage",2000,"International Symposium on Plasma Process-Induced Damage, P2ID, Proceedings",,,,"125","128",,"10.1016/S0167-9317(01)00704-3","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0034510067&doi=10.1016%2fS0167-9317%2801%2900704-3&partnerID=40&md5=3380a141b08348ba7fe52068b4d2fc02"

321. Cester A., Paccagnella A., Ghidini G.,"Time decay of stress induced leakage current in thin gate oxides by low-field electron injection",1999,"Microelectronics Reliability","40","4-5",,"715","718",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-8644270651&partnerID=40&md5=95630131d604e8689fc46e7fd00e7739"

322. Pantisano L., Paccagnella A., Colombo P., Valentini M.G.,"Plasma damage impact on nMOS electrical characteristics during a CCS stress",1999,"International Symposium on Plasma Process-Induced Damage, P2ID, Proceedings",,,,"73","76",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0033317821&partnerID=40&md5=b17bf940d8abc6887dafc77f721072c7"

323. Da Rold M., Bacchetta N., Bisello D., Paccagnella A., Dalla Betta G.-F., Verzellesi G.,"Study of breakdown effects in silicon multiguard structures",1999,"IEEE Transactions on Nuclear Science","46","4 PART 3",,"1215","1223",,"10.1109/23.785736","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0033312975&doi=10.1109%2f23.785736&partnerID=40&md5=ac8c8acb7ee5a3daf9295b370bce68cf"

324. Scarpa A., Riess P., Ghibaudo G., Paccagnella A., Pananakakis G., Ceschia M., Ghidini G.,"Electrically and radiation induced leakage currents in thin oxides",1999,"Microelectronics Reliability","40","1",,"57","67",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0033877271&partnerID=40&md5=92716d3f9ef0828ca7d4ad94b562cdf0"

325. Albergo S., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Bartalini P., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Bozzi C., Breuker H., Bruzzi M., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Connotte J., Creanza D., D'Alessandro R., Da Rold M., De Palma M., Dell'Orso R., Della Marina R.,

Eklund C., Elliott-Peisert A., Feld L., Fiore L., Focardi E., French M., Freudenreich K., Giassi A., Giraldo A., Glessing B., Gu W.H., Hall G., Hammerstrom R., Hrubec J., Huhtinen M., Karimaki V., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Maggi G., Mannelli M., Mantovani G., Marchioro A., Martignon G., Mc Evoy B., Meschini M., Messineo A., My S., Paccagnella A., Palla F., Pandoulas D., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Raffaelli F., Raso G., Raymond M., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Skog K., Starodumov A., Stavitski I., Stefanini G., Tempesta P., Tonelli G., Tricomi A., Tuuva T., Vannini C., Verdini P.G., Viertel G., Xie Z., Wang Y., Watts S., Wittmer B.,"Test results of heavily irradiated Si detectors",1999,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","422","1-3",,"238","241",,"10.1016/S0168-9002(98)01101-2","https://www.scopus.com/inward/record.uri?eid=2-s2.0-9144232489&doi=10.1016%2fS0168-9002%2898%2901101-2&partnerID=40&md5=a411ea0c64207f1687c75d2f3324041b"

326. Albergo S., Angarano M.M., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Bozzi C., Braibant S., Breuker H., Bruzzi M., Buffini A., Busoni S., Calefato G., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Creanza D., D'Alessandro R., Da Rold M., Demaria N., De Palma M., Dell'Orso R., Della Marina R., Dutta S., Eklund C., Elliott-Peisert A., Feld L., Fiore L., Focardi E., French M., Freudenreich K., Fürtjes A., Giassi A., Giorgi M., Giraldo A., Glessing B., Gu W.H., Hall G., Hammerstrom R., Hebbeker T., Hrubec J., Huhtinen M., Kaminsky A., Karimaki V., Koenig St., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Mättig P., Maggi G., Mannelli M., Mantovani G., Marchioro A., Mariotti C., Martignon G., Mc Evoy B., Meschini M., Messineo A., My S., Paccagnella A., Palla F., Pandoulas D., Papi A., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Radicci V., Raffaelli F., Raymond M., Santocchia A., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Skog K., Starodumov A., Stavitski I., Stefanini G.,"High-voltage breakdown studies on Si microstrip detectors",1999,"Nuovo Cimento della Societa Italiana di Fisica A","112","11",,"1271","1283",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0040911187&partnerID=40&md5=3186314c60848832240fdcb5d89e348e"

327. Albergo S., Angarano M., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Bozzi C., Braibant S., Breuker H., Bruzzi M., Buffini A., Busoni S., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Creanza D., D'Alessandro R., Da Rold M., Demaria N., De Palma M., Dell'Orso R., Della Marina R., Dutta S., Eklund C., Feld L., Fiore L., Focardi E., French M., Freudenreich K., Frey A., Fürtjes A., Giassi A., Giorgi M., Giraldo A., Glessing B., Gu W.H., Hall G., Hammarstrom R., Hebbeker T., Honma A., Hrubec J., Huhtinen M., Kaminsky A., Karimaki V., Koenig St., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Mättig P., Maggi G., Mannelli M., Mantovani G., Marchioro A., Mariotti C., Martignon G., Mc Evoy B., Meschini M., Messineo A., Migliore E., My S., Paccagnella A., Palla F., Pandoulas D., Papi A., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Radicci V., Raffaelli F., Raymond M., Rizzo F., Santocchia A., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Starodumov A., Stavitski I.,"The silicon microstrip tracker for CMS",1999,"Nuovo Cimento della Societa Italiana di Fisica A","112","11",,"1307","1316",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0039132823&partnerID=40&md5=9ad43a064215b84edab1b867c9088e31"

328. Albergo S., Angarano M., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Bozzi C., Braibant S., Breuker H., Bruzzi M., Buffini A., Busoni S., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Creanza D., D'Alessandro R., Da Rold M., Demaria N., De Palma M., Dell'Orso R., Della Marina R., Dutta S., Eklund C., Elliott-Peisert A., Feld L., Fiore L., Focardi E.,

French M., Freudenreich K., Fürtjes A., Giassi A., Giorgi M., Giraldo A., Glessing B., Gu W.H., Hall G., Hammerstrom R., Hebbeker T., Hrubec J., Huhtinen M., Kaminsky A., Karimaki V., Koenig St., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Mättig P., Maggi G., Mannelli M., Mantovani G., Marchioro A., Mariotti C., Martignon G., Mc Evoy B., Meschini M., Messineo A., Migliore E., My S., Paccagnella A., Palla F., Pandoulas D., Papi A., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Radicci V., Raffaelli F., Raymond M., Santocchia A., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Skog K., Starodumov A., Stavitski I., Stefanini G.,"Comparative study of 〈111〉 and 〈100〉 crystals and capacitance measurements on Si strip detectors in CMS",1999,"Nuovo Cimento della Societa Italiana di Fisica A","112","11",,"1261","1269",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0007682505&partnerID=40&md5=f58b17ead72e26958e6cd8a7f948c38e"

329. Candelori A., Paccagnella A., Nardi F., Bacchetta N., Bisello D.,"SPICE evaluation of the S/N ratio for Si microstrip detectors",1999,"IEEE Transactions on Nuclear Science","46","5",,"1261","1273",,"10.1109/23.795802","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0033207808&doi=10.1109%2f23.795802&partnerID=40&md5=11340b17c5cb683551a08badd3d57d2b"

330. Focardi E., Albergo S., Angarano M., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Bartalini P., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Bozzi C., Braibant S., Breuker H., Bruzzi M., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Creanza D., D'Alessandro R., da Rold M., Demaria N., de Palma M., Dell'Orso R., della Marina R., Dutta S., Eklund C., Elliott-Peisert A., Feld L., Fiore L., French M., Freudenreich K., Fürtjes A., Giassi A., Giraldo A., Glessing B., Gu W.H., Hall G., Hammerstrom R., Hebbeker T., Hrubec J., Huhtinen M., Kaminsky A., Karimaki V., Koenig St., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Mättig P., Maggi G., Mannelli M., Mantovani G., Marchioro A., Mariotti C., Martignon G., Mc Evoy B., Meschini M., Messineo A., My S., Paccagnella A., Palla F., Pandoulas D., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Raffaelli F., Raso G., Raymond M., Santocchia A., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Skog K., Starodumov A., Stavitski I., Stefanini G., Tempesta P., Tonelli G., Tricomi A., Tuuva T., Vannini C., Verdini P.G., Viertel G., Xie Z., Wang Y., Watts S., Wittmer B.,"The CMS silicon strip tracker",1999,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","435","1-2",,"102","108",,"10.1016/S0168-9002(99)00585-9","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0033207932&doi=10.1016%2fS0168-9002%2899%2900585-9&partnerID=40&md5=1393b8dcae87498a54a8959a189c1f80"

331. Tonelli G., Albergo S., Angarano M., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Bartalini P., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Bozzi C., Braibant S., Breuker H., Bruzzi M., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Creanza D., D'Alessandro R., da Rold M., Demaria N., de Palma M., Dell'Orso R., della Marina R., Dutta S., Eklund C., Elliott-Peisert A., Feld L., Fiore L., Focardi E., French M., Freudenreich K., Fürtjes A., Giassi A., Giraldo A., Glessing B., Gu W.H., Hall G., Hammerstrom R., Hebbeker T., Hrubec J., Huhtinen M., Kaminsky A., Karimaki V., Koenig St., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Mättig P., Maggi G., Mannelli M., Mantovani G., Marchioro A., Mariotti C., Martignon G., Mc Evoy B., Meschini M., Messineo A., My S., Paccagnella A., Palla F., Pandoulas D., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Raffaelli F., Raso G., Raymond M., Schmittg B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Skog K., Starodumov A., Stavitski I., Stefanini G., Tempesta P., Tricomi A., Tuuva T., Vanninia C., Verdini P.G., Viertel G., Xie Z., Wang Y., Watts S., Wittmer B.,"The R&D program for silicon detectors in CMS",1999,"Nuclear Instruments and Methods in Physics Research, Section A:

Accelerators, Spectrometers, Detectors and Associated Equipment","435","1-2",,"109","117",,"10.1016/S0168-9002(99)00419-2","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0033207380&doi=10.1016%2fS0168-9002%2899%2900419-2&partnerID=40&md5=30d93be6d9798fc02fba14b5a2ec7239"

332. Gasparotto A., Carnera A., Paccagnella A., Fraboni B., Priolo F., Gombia E., Mosca R.,"High-resistance buried layers by MeV Fe implantation in n-type InP",1999,"Applied Physics Letters","75","5",,"668","670",,"10.1063/1.124476","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032620140&doi=10.1063%2f1.124476&partnerID=40&md5=1c20d470b80c2e6ed60b868334a45514"

333. Bacchetta N., Albergo S., Azzi P., Babucci E., Bader A., Bagliesi G., Bartalini P., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Bozzi C., Breuker H., Bruzzi M., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Connotte J., Creanza D., D'Alessandro R., Da Rold M., De Palma M., Dell'Orso R., Della Marina R., Eklund C., Elliott-Peisert A., Feld L., Fiore L., Focardi E., French M., Freudenreich K., Giassi A., Giraldo A., Glessing B., Gu W.H., Hall G., Hammerstrom R., Hrubec J., Huhtinen M., Karimaki V., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Maggi G., Mannelli M., Mantovani G., Marchioro A., Martignon G., Mc Evoy B., Meschini M., Messineo A., My S., Paccagnella A., Palla F., Pandoulas D., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Raffaelli F., Raso G., Raymond M., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Skog K., Starodumov A., Stavitski I., Stefanini G., Tempesta P., Tonelli G., Tricomi A., Tuuva T., Vannini C., Verdini P.G., Viertel G., Xie Z., Wang Y., Watts S., Wittmer B.,"CMS silicon microstrip detectors: Research and development",1999,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","426","1",,"16","23",,"10.1016/S0168-9002(98)01461-2","https://www.scopus.com/inward/record.uri?eid=2-s2.0-20244381801&doi=10.1016%2fS0168-9002%2898%2901461-2&partnerID=40&md5=67ffed187ce052aeec716f0530786a51"

334. Candelori A., Paccagnella A., Cammarata M., Ghidini G., Ceschia M.,"Electron irradiation effects on thin MOS capacitors",1999,"Journal of Non-Crystalline Solids","245","1-3",,"238","244",,"10.1016/S0022-3093(98)00887-4","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032657311&doi=10.1016%2fS0022-3093%2898%2900887-4&partnerID=40&md5=5eb735383893705bd5259b219521fc82"

335. Ceschia M., Paccagnella A., Cester A., Scarpa A., Candelori A., Ghidini G.,"Low-field current on thin oxides after constant current or radiation stresses",1999,"Journal of Non-Crystalline Solids","245","1-3",,"232","237",,"10.1016/S0022-3093(98)00865-5","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032664869&doi=10.1016%2fS0022-3093%2898%2900865-5&partnerID=40&md5=57c816f9ad6f849f61cf75d2e5ebd3eb"

336. Cester A., Paccagnella A., Buso M., Ghidini G.,"Time stability of stress induced leakage current in thin gate oxides",1999,"European Solid-State Device Research Conference","13-15 Sept. 1999",, 1505516,"368","371",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-84907904753&partnerID=40&md5=8b8127331dbb896c7f347850f73cd46c"

337. Pantisano L., Paccagnella A., Colombo P., Valentini M.G.,"Depassivation of latent plasma damage in pMOS devices",1999,"Microelectronics Reliability","39","6-7",,"827","832",,"10.1016/S0026-2714(99)00108-0","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0033145298&doi=10.1016%2fS0026-2714%2899%2900108-0&partnerID=40&md5=43bbfb43a3192e3425d2694548366411"

338. Candelori A., Paccagnella A., Saglimbeni G., Bisello D.,"Breakdown of coupling dielectrics for Si microstrip detectors",1999,"Nuovo Cimento della Societa Italiana di Fisica A","112","1-

2",,"87","93",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032646954&partnerID=40&md5=52eae925cd90a950ffcace79aa804ad6"

339. Scarpa A., Pananakakis G., Ghibaudo G., Paccagnella A., Ghidini G.,"On the degradation kinetics of thin oxide layers",1999,"Solid-State Electronics","43","2",,"221","227",,"10.1016/S0038-1101(98)00260-3","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0033080006&doi=10.1016%2fS0038-1101%2898%2900260-3&partnerID=40&md5=56722161babab5dafa1aed44939b876f"

340. Pantisano L., Paccagnella A., Barbazza M., Colombo P., Valentini M.G.,"New experimental approach to evaluate plasma damage in NMOS and PMOS devices",1999,"Annual Proceedings - Reliability Physics (Symposium)",,,,"375","380",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032684507&partnerID=40&md5=577de41a43f2196424bf445d31e41605"

341. Ceschia M., Paccagnella A., Scarpa A., Cester A., Ghidini G.,"Total dose dependence of radiation-induced leakage current in ultra-thin gate oxides",1999,"Microelectronics Reliability","39","2",,"221","226",,"10.1016/S0026-2714(98)00233-9","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032681149&doi=10.1016%2fS0026-2714%2898%2900233-9&partnerID=40&md5=8c0df98fe2bca627ec84f11030a9b967"

342. Candelori A., Paccagnella A., Nardi F., Bacchetta N., Bisello D.,"SPICE evaluation of the S/N ratio for Si microstrip detectors",1999,"Nuovo Cimento della Societa Italiana di Fisica A","112","1-2",,"75","85",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032668448&partnerID=40&md5=39dd0afed48edb6eeef944764da2fcd6"

343. Candelori A., Paccagnella A., Scarpa A., Ghidini G., Fuochi P.G.,"Degradation of electron irradiated MOS capacitors",1999,"Microelectronics Reliability","39","2",,"227","233",,"10.1016/S0026-2714(98)00231-5","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032634976&doi=10.1016%2fS0026-2714%2898%2900231-5&partnerID=40&md5=0fe4923bf0865a70216b389a15b8e806"

344. Scarpa A., De Salvo B., Ghibaudo G., Pananakakis G., Paccagnella A., Ghidini G.,"On the correlation between SILC and hole fluence throughout the oxide",1999,"Microelectronics Reliability","39","2",,"197","201",,"10.1016/S0026-2714(98)00232-7","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032657719&doi=10.1016%2fS0026-2714%2898%2900232-7&partnerID=40&md5=be5910bd791c3e4b43388443799b0399"

345. Gasparotto A., Carnera A., Paccagnella A., Fraboni B., Priolo F., Gombia E., Mosca R., Rossetto G.,"Semi-insulating behaviour in Fe MeV implanted n-type InP",1999,"Nuclear Instruments and Methods in Physics Research, Section B: Beam Interactions with Materials and Atoms","148","1-4",,"411","415",,"10.1016/S0168-583X(98)00701-0","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0033513713&doi=10.1016%2fS0168-583X%2898%2900701-0&partnerID=40&md5=6860373da21e82f8c3050588d212ead0"

346. Jarron P., Anelli G., Calin T., Cosculluela J., Campbell M., Delmastro M., Faccio F., Giraldo A., Heijne E., Kloukinas K., Letheren M., Nicolaidis M., Moreira P., Paccagnella A., Marchioro A., Snoeys W., Velazco R.,"Deep submicron CMOS technologies for the LHC experiments",1999,"Nuclear Physics B - Proceedings Supplements","78","1-3",,"625","634",,"10.1016/S0920-5632(99)00615-5","https://www.scopus.com/inward/record.uri?eid=2-s2.0-20244387403&doi=10.1016%2fS0920-5632%2899%2900615-5&partnerID=40&md5=92a2b09ebf50fc736fd5f0300ddae762"

347. Da Rold M., Bacchetta N., Bisello D., Cavone M., Betta G.-F.D., De Liso G., Dell'orso R., Fuochi P.G., Lanza A., Messineo A., Mihul A., Militaru O., Paccagnella A., Tonelli G., Verdini P.G., Verzellesi G., Wheadon R.,"Multiguard structures for high-voltage operation of radiation-damaged silicon detectors",1999,"Nuovo Cimento della Societa Italiana di Fisica A","112","1-2",,"13","22",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032623322&partnerID=40&md5=7c8e4c13f898cb5bdd8f8673b2db707e"

348. Feld L., Albergo S., Angarano M., Azzi P., Babucci E., Bacchetta N., Bader A., Bagliesi G., Barr A., Bartalini P., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Bozzi C., Braibant S., Breuker H., Bruzzi M., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Creanza D., D'Alessandro R., Da Rold M., Demaria N., De Palma M., Dell'Orso R., Della Marina R., Dutta S., Eklund C., Elliott-Peisert A., Fiore L., Focardi E., French M., Freudenreich K., Fürtjes A., Giassi A., Giraldo A., Glessing W.D., Gu W.H., Hall G., Hammarström R., Hebbeker T., Honkanen A., Hrubec J., Huhtinen M., Kaminsky A., Karimaki V., Kellogg R., Koenig St., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Mättig P., Maggi G., Mannelli M., Mantovani G., Marchioro A., Mariotti C., Martignon G., Mc Evoy B., Meschini M., Messineo A., My S., Paccagnella A., Palla F., Pandoulas D., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Raffaelli F., Raso G., Raymond M., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Skog K., Starodumov A., Stavitski I., Stefanini G., Tempesta P., Tuuva T., Watts S.,"R&D for the CMS silicon tracker",1999,"Nuclear Physics B - Proceedings Supplements","78","1-3",,"322","328",,"10.1016/S0920-5632(99)00565-4","https://www.scopus.com/inward/record.uri?eid=2-s2.0-18744431636&doi=10.1016%2fS0920-5632%2899%2900565-4&partnerID=40&md5=c59f02f746238e1b50607548b32aab12"

349. D'Alessandro R., Albergo S., Angarano M., Azzi P., Babucci E., Bacchetta N., Bagliesi G., Bartalini P., Basti A., Biggeri U., Bilei G.M., Bisello D., Boemi D., Bosi F., Borrello L., Bozzi C., Breuker H., Bruzzi M., Candelori A., Caner A., Castaldi R., Castro A., Catacchini E., Checcucci B., Ciampolini P., Civinini C., Connotte J., Creanza D., Da Rold M., De Palma M., Dell'Orso R., Della Marina R., Eklund C., Elliott-Peisert A., Feld L., Fiore L., Focardi E., French M., Freudenreich K., Giassi A., Giraldo A., Glessing B., Gu W.H., Hall G., Hammerstrom R., Hrubec J., Huhtinen M., Karimäki V., Krammer M., Lariccia P., Lenzi M., Loreti M., Luebelsmeyer K., Lustermann W., Maggi G., Mannelli M., Mantovani G., Marchioro A., Martignon G., Mc Evoy B., Meschini M., Messineo A., My S., Paccagnella A., Palla F., Pandoulas D., Parrini G., Passeri D., Pieri M., Piperov S., Potenza R., Raffaelli F., Raso G., Raymond M., Santocchia A., Schmitt B., Selvaggi G., Servoli L., Sguazzoni G., Siedling R., Silvestris L., Skog K., Starodumov A., Stavitsky I., Stefanini G., Tempesta P., Tonelli G., Tricomi A., Tuuva T., Vannini C., Verdini P.G., Viertel G., Xie Z., Wang Y., Watts S., Wittmer B.,"The CMS silicon tracker",1998,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","419","2-3",,"538","543",,"10.1016/S0168-9002(98)00831-6","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0346310826&doi=10.1016%2fS0168-9002%2898%2900831-6&partnerID=40&md5=a9959650819f387b16638672619b604e"

350. Larcher L., Paccagnella A., Scarpa A., Ghidini G.,"New model of tunnelling current and SILC in ultra-thin oxides",1998,"Technical Digest - International Electron Devices Meeting",,,,"901","904",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032255804&partnerID=40&md5=8cdf8b206b14fa77907781fd0d6ab1b8"

351. Bacchetta N., Bisello D., Candelori A., Da Rold M., Nardi F., Paccagnella A.,"HSPICE simulations of Si microstrip detectors",1998,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","409","1-3",,"142","146",,"10.1016/S0168-9002(97)01253-9","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032067831&doi=10.1016%2fS0168-9002%2897%2901253-9&partnerID=40&md5=b7aca3664e1015ef13d9d280d3d646e7"

352. Bacchetta N., Bisello D., Candelori A., Cavone M., Dalla Betta G.-F., Da Rold M., De Liso G., Dell'Orso R., Fuochi P.G., Messineo A., Mihul A., Militaru O., Paccagnella A., Tonelli G., Verdini P.G., Verzellesi G., Wheadon R.,"High-voltage operation of silicon devices for LHC experiments",1998,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","409","1-3",,"139","141",,"10.1016/S0168-9002(97)01252-7","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

0032066838&doi=10.1016%2fS0168-9002%2897%2901252-7&partnerID=40&md5=c64c1c8e807716824799e17ac5575d33"

353. Bilei G.M., Albergo S., Angarano M., Azzi P., Bacchetta N., Bagliesi G., Bartalini P., Basti A., Biggeri U., Bisello D., Boemi D., Cazzola U., Borrello L., Bozzi C., Breuker H., Bruzzi M., Candelori A., Caner A., Castaldi R., Catacchini E., Checcucci B., Ciampolini P., Ciasnohova A., Civinini C., Connotte J., Creanza D., D'Alessandro R., Da Rold M., De Palma M., DelL'Orso R., Della Marina R., Eklund C., Elliott-Peisert A., Fiore L., Focardi E., French M., Giassi A., Giraldo A., Glessing B., Gu W.H., Hall G., Hammerstrom R., Hrubec J., Huhtinen M., Karimaki V., Krammer M., Lariccia P., Loreti M., Luebelsmeyer K., Lustermann W., Maggi G., Mannelli M., Mantovani G., Marchioro A., Martignon G., Mc Evoy B., Meschini M., Messineo A., My S., Paccagnella A., Pandoulas D., Parrini G., Passeri D., Pieri M., Potenza R., Raffaelli F., Raso G., Raymond M., Santocchia A., Schmitt B., Selvaggi G., Servoli L., Siedling R., Silvestris L., Skassyrskaia A., Skog K., Starodumov A., Stavitsky I., Stefanini G., Tempesta P., Tonelli G., Tricomi A., Tuuva T., Vannini C., Verdini P.G., Viertel G., Xie Z., Watts S., Wittmer B.,"The CMS silicon tracker at LHC",1998,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","409","1-3",,"105","111",,"10.1016/S0168-9002(97)01247-3","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032064249&doi=10.1016%2fS0168-9002%2897%2901247-3&partnerID=40&md5=db481e04a3de8fbc0c2ceed10d7ef3b6"
354. Larcher L., Paccagnella A., Scarpa A., Ghidini G.,"A new model for tunneling conduction in ultra-thin dielectrics",1998,"European Solid-State Device Research Conference",,,1503552,"316","319",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-84908156226&partnerID=40&md5=b489b8b220ca70f4b1256ec527533794"
355. Candelori A., Gomiero E., Ghidini G., Paccagnella A.,"MOSFET parameter degradation after Fowler-Nordheim injection stress",1998,"Microelectronics Reliability","38","2",,"189","193",,"10.1016/S0026-2714(97)00054-1","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0031995590&doi=10.1016%2fS0026-2714%2897%2900054-1&partnerID=40&md5=94db3093de5b73abdda6584e987d836f"
356. Ceschia M., Paccagnella A., Cester A., Scarpa A., Ghidini G.,"Radiation induced leakage current and stress induced leakage current in ultra-thin gate oxides",1998,"IEEE Transactions on Nuclear Science","45","6 PART 1",,"2375","2382",,"10.1109/23.736457","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032306849&doi=10.1109%2f23.736457&partnerID=40&md5=41304ec64005cc7f2cb9112c3fb01a98"
357. Scarpa A., Ghibaudo G., Ghidini G., Pananakakis G., Paccagnella A.,"Stress induced degradation features of very thin gate oxides",1998,"Microelectronics Reliability","38","2",,"195","199",,"10.1016/S0026-2714(97)00053-X","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0031994428&doi=10.1016%2fS0026-2714%2897%2900053-X&partnerID=40&md5=80e9ccac9d4eb27ce658f9d5fafd7bbf"
358. Meneghesso G., Crosato C., Garat F., Martines G., Paccagnella A., Zanoni E.,"Failure mechanisms of Schottky gate contact degradation and deep traps creation in AlGaAs/InGaAs PM-HEMTs submitted to accelerated life tests",1998,"Microelectronics Reliability","38","6-8",,"1227","1232",,"10.1016/S0026-2714(98)00092-4","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0032083915&doi=10.1016%2fS0026-2714%2898%2900092-4&partnerID=40&md5=c1c917525b45927725dfed5dc2bdd00d"
359. Pantisano L., Paccagnella A., Pettarin L., Scarpa A., Valentini G., Baldi L., Alba S.,"A new experimental technique to evaluate the plasma induced damage at wafer level testing",1998,"Microelectronics Reliability","38","6-8",,"919","924",,"10.1016/S0026-2714(98)00102-4","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

0032084091&doi=10.1016%2fS0026-2714%2898%2900102-4&partnerID=40&md5=5d20a9c8f54c8d50a8560c3cc17723eb"

360. Zanoni E., Callegari A., Canali C., Fantini F., Hartnagel H.L., Magistrali F., Paccagnella A., Vanzi M.,"Metal-GaAs interaction and contact degradation in microwave MESFETs",1998,"High-Temperature Electronics",,,,"592","609",,"10.1109/9780470544884.ch78","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84885737777&doi=10.1109%2f9780470544884.ch78&partnerID=40&md5=4d0468d75881c16236b2e0a6ade9566d"

361. Scarpa A., Paccagnella A., Montera F., Candelori A., Ghibaudo G., Pananakakis G., Ghidini G., Fuochi P.G.,"Modifications of Fowler-Nordheim injection characteristics in γ irradiated MOS devices",1998,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,,,"73","78",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0031620079&partnerID=40&md5=b87fb53992605d3cd93fa8089a440fa1"

362. Scarpa A., Paccagnella A., Montera F., Ghibaudo G., Pananakakis G.,"Ionizing radiation induced leakage current on ultra-thin gate oxides",1997,"IEEE Transactions on Nuclear Science","44","6 PART 1",,"1818","1825",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0031357733&partnerID=40&md5=964a34e1afd8a52213245960985e9ce1"

363. Candelori A., Paccagnella A., Bonin F., Bacchetta N., Da Rold M., Biselio D.,"A SPICE model of the ohmic side of double-sided Si microstrip detectors",1997,"IEEE Transactions on Nuclear Science","44","3 PART 1",,"728","735",,"10.1109/23.603741","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33747653618&doi=10.1109%2f23.603741&partnerID=40&md5=65a4e2bd79359fe10db4f224129da280"

364. Meneghesso G., Paccagnella A., Camin D.V., Fedyakin N., Pessina G., Canali C.,"Study of neutron damage in GaAs MESFETs",1997,"IEEE Transactions on Nuclear Science","44","3 PART 1",,"840","846",,"10.1109/23.603762","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0344574384&doi=10.1109%2f23.603762&partnerID=40&md5=facdc7f994e8464e5ccc93c6c683b10b"

365. Da Rold M., Paccagnella A., Da Re A., Verzellesi G., Bacchetta N., Wheadon R., Dalla Betta G.-F., Candelori A., Soncini G., Bisello D.,"Radiation effects on breakdown characteristics of multiguarded devices",1997,"IEEE Transactions on Nuclear Science","44","3 PART 1",,"721","727",,"10.1109/23.603740","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0000255149&doi=10.1109%2f23.603740&partnerID=40&md5=4769fef9d7d5c62f7cb0934541fd5fe7"

366. Bacchetta N., Della Betta G.-F., Da Rold M., Dell'Orso R., Fuochi P.G., Lanza A., Messineo A., Militaru O., Paccagnella A., Verzellesi G., Wheadon R.,"Study of breakdown effects in silicon multi-guard structures",1997,"IEEE Nuclear Science Symposium & Medical Imaging Conference","1",,,"498","502",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0031358377&partnerID=40&md5=8a63352364f9a98dcad5b851b8078424"

367. Scarpa A., Ghibaudo G., Pananakakis G., Paccagnella A., Ghidini G.,"Reliability extrapolation model for stressinduced-leakage current in thin silicon oxides",1997,"Electronics Letters","33","15",,"1342","1344",,"10.1049/el:19970877","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0031188498&doi=10.1049%2fel%3a19970877&partnerID=40&md5=0c96dcb335e979d40256fd7ae8682134"

368. Da Rold M., Paccagnella A., Fardin P., Bacchetta N., Wheadon R., Benetti P., Bisello D.,"Noise characteristics in irradiated multiguard structures",1997,"Nuclear Instruments and

Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","392","1-3",,"202","205",,"10.1016/S0168-9002(97)00285-4","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0031169186&doi=10.1016%2fS0168-9002%2897%2900285-4&partnerID=40&md5=916c1ceec6356a8073aaa7eadef22896"

369. Bacchetta N., Bisello D., Broz F., Catuozzo M., Gotra Y., Guschin E., Lacaita A., Malakhov N., Musienko Y., Nicolosi P., Paccagnella A., Pace E., Pantano D., Sadygov Z., Villoresi P., Zappa F.,"MRS detectors with high gain for registration of weak visible and UV light fluxes",1997,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","387","1-2",,"225","230",,"10.1016/S0168-9002(96)00995-3","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0031098896&doi=10.1016%2fS0168-9002%2896%2900995-3&partnerID=40&md5=279bd5eb38f69d3368b2870fe7b45ac4"
370. Scarpa A., Paccagnella A., Ghidini G., Vianello A., Zanoni E.,"Instability of post-Fowler-Nordheim stress measurements of MOS devices",1997,"Solid-State Electronics","41","7",,"935","938",,"10.1016/S0038-1101(97)00002-6","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0031189611&doi=10.1016%2fS0038-1101%2897%2900002-6&partnerID=40&md5=3360804e8147bc398ca33085fd8c9ef3"
371. Scarpa A., Ghibaudo G., Ghidini G., Pananakakis G., Paccagnella A.,"Stress induced leakage current in ultra-thin gate oxides after constant current stress",1997,"Microelectronic Engineering","36","1-4",,"145","148",,"10.1016/S0167-9317(97)00036-1","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0031150232&doi=10.1016%2fS0167-9317%2897%2900036-1&partnerID=40&md5=1a4a8d78b9e58ccf2f7ce613ef54555e"
372. Scarpa A., Ries P., Ghibaudo G., Paccagnella A., Pananakakis G., Brini J., Ghidini G., Papadas C.,"Stress induced leakage current dependence on oxide thickness, technology and stress level",1997,"European Solid-State Device Research Conference",,,,"592","595",,"10.1109/ESSDERC.1997.194498","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84907506538&doi=10.1109%2fESSDERC.1997.194498&partnerID=40&md5=d8e9ef9b054df5ad6c037c4269c1f113"
373. Bacchetta N., Bisello D., Calgarotto C., Candelori A., Paccagnella A.,"A SPICE model for Si microstrip detectors and read-out electronics",1996,"IEEE Transactions on Nuclear Science","43","3 PART 2",,"1213","1219",,"10.1109/23.506666","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0030165199&doi=10.1109%2f23.506666&partnerID=40&md5=fe23e6f892b3ee07d983e4e88cf91155"
374. Candelori A., Paccagnella A., Bonin F., Bacchetta N., Da Rold M., Bisello D.,"SPICE model of double-sided Si microstrip detectors",1996,"IEEE Nuclear Science Symposium & Medical Imaging Conference","1",,,"568","572",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0030362445&partnerID=40&md5=3caefd5e6e144f026bbf60964b73b005"
375. Meneghesso G., Paccagnella A., Gasparetto G., Camin D.V., Fedyakin N., Pessina G., Canali C.,"Neutron induced damage in GaAs MESFETs",1996,"IEEE Nuclear Science Symposium & Medical Imaging Conference","1",,,"256","260",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0030370808&partnerID=40&md5=ff0ba221bcc0a75fdbcef95328fb448c"
376. Paccagnella A., Ceschia M., Verzellesi G., Dalla Betta G.F., Bellutti P., Fuochi P.G., Soncini G.,"Forward and reverse characteristics of irradiated MOSFETs",1996,"IEEE Transactions on Nuclear Science","43","3 PART 1",,"797","804",,"10.1109/23.510715","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0030165520&doi=10.1109%2f23.510715&partnerID=40&md5=6f7a261bb40504d709980af245762fcc"

377. Bacchetta N., Bisello D., Gotra Yu., Jejer V., Malakhov N., Paccagnella A., Pantano D., Sadygov Z.,"New type of metal-resistive layer-silicon avalanche detectors for visible and UV light detection",1996,"Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment","383","1",,"263","265",,"10.1016/S0168-9002(96)00696-1","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0030408370&doi=10.1016%2fS0168-9002%2896%2900696-1&partnerID=40&md5=45982ec0f8f788d6977f069b1f7476da"
378. Paccagnella A., Candelori A., Milani A., Formigoni E., Ghidini G., Pellizzer F., Drera D., Fuochi P.O., Lavale M.,"Breakdown properties of irradiated MOS capacitors",1996,"IEEE Transactions on Nuclear Science","43","6 PART 1",,"2609","2616",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0030370709&partnerID=40&md5=04ef6fb0d4de8ab09393f661975f4c8a"
379. Bacchetta N., Bisello D., Candelori A., Dalla Betta G.F., Da Re A., Da Rold M., Fardin P., Paccagnella A., Soncini G., Verzellesi G., Wheadon R.,"Breakdown properties of multiguarded devices",1996,"IEEE Nuclear Science Symposium & Medical Imaging Conference","1",,,"563","567",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0030350425&partnerID=40&md5=33e1bc49d9357d832a5066008a961648"
380. Meneghesso G., Paccagnella A., Haddab Y., Canali C., Zanoni E.,"Evidence of interface trap creation by hot-electrons in AlGaAs/GaAs high electron mobility transistors",1996,"Applied Physics Letters","69","10",,"1411","1413",,"10.1063/1.117598","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0030565403&doi=10.1063%2f1.117598&partnerID=40&md5=1aabdf958dc069b63ab490f3a3954d0b"
381. Bisello D., Da Rold M., Franzin L., Paccagnella A., Wheadon R.,"Radiation effects on breakdown in silicon multiguarded diodes",1996,"Nuovo Cimento della Societa Italiana di Fisica A","109","9",,"1343","1350",,"10.1007/BF02773520","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0039562690&doi=10.1007%2fBF02773520&partnerID=40&md5=393ad3ebb5125dc229b49a3d129db787"
382. Paccagnella A., Rizzato A., Scarpa A., Zanoni E., Crisenza G., Ghidini G.,"Electrical and radiation tests of thin tunnel oxides",1996,"Microelectronics Reliability","36","7-8 SPEC. ISS.",,"1033","1044",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-16444363145&partnerID=40&md5=e51f1c5ca83d6d0fca3d0ecde2bd2470"
383. Meneghesso G., Gasparetto G., Paccagnella A., Camin D.V., Pessina G., Fedyakin N., Canali C.,"Experimental study of deep levels in MESFETs",1996,"European Solid-State Device Research Conference",,, 5436165,"563","566",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-84920748954&partnerID=40&md5=4b5d23d18447d4af41d2d5118046c288"
384. Bisello D., Gotra Yu., Jejer V., Kushpil V., Malakhov N., Paccagnella A., Sadygov Z., Stavitsky I., Tsyganov E.,"Silicon avalanche detectors with negative feedback as detectors for high energy physics",1995,"Nuclear Inst. and Methods in Physics Research, A","367","1-3",,"212","214",,"10.1016/0168-9002(95)00540-4","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33749321338&doi=10.1016%2f0168-9002%2895%2900540-4&partnerID=40&md5=d9a403c5f890b9181c832dcb20c1a93e"
385. Adriani O., Angelini F., Bacchetta N., Bagliesi G., Barichello G., Basti A., Bellazzini R., Bisello D., Bondar A., Bozzo M., Brez A., Brom J.-M., Caner A., Carosi R., Castaldi R., Clergeau J.-F., Contardo D., Dell'Orso R., Focardi E., French M., Giraldo A., Hall G., Hammarström R., Haroutunian R., Jones L., Kachelhoffer G., Karimaki V., Kryn D., Loreti M., Ladziński T., MacEvoy B., Markou A., Massai M.M., Messineo A., Meschini M., Millmore M., Morelli A., Meyer T., Nagaslaev V., Paccagnella A., Pallares A., Pantano D., Parodi F., Parrini G., Peisert A., Qian S., Raffaelli F., Raymond

M., Raffo F., Ribeiro R., Riester J.L., Runolfsson O., Sachdeva R., Shekhtman L., Smadja G., Spandre G., Spezziga M., Tonelli G., Toropin A., Vander Velde C., Vanlaer P., Vannini C., Verdini P.G., Vitè D., Wheadon R., Zevgolatakos E.,"Performance of a prototype of the CMS central detector",1995,"Nuclear Inst. and Methods in Physics Research, A","367","1-3",,"189","192",,"10.1016/0168-9002(95)00641-9","https://www.scopus.com/inward/record.uri?eid=2-s2.0-4244054847&doi=10.1016%2f0168-9002%2895%2900641-9&partnerID=40&md5=bb6f665be83377e5003132a409441619"

386. Bacchetta N., Bisello D., Calgarotto C., Candelori A., Paccagnella A.,"SPICE model of Si microstrip detectors",1995,"IEEE Nuclear Science Symposium & Medical Imaging Conference","1",,,"510","514",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0029457765&partnerID=40&md5=ce25a8e34dd733f8a403def91b7c10bf"

387. Paccagnella A., Ceschia M., Verzellesi G., Betta Dalla G.F., Bellutti P., Fuochi P.G., Soncini G.,"Forward and reverse characteristics of irradiated MOSFETs",1995,"Proceedings of the European Conference on Radiation and its Effects on Components and Systems, RADECS",,,,"25","32",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0029454885&partnerID=40&md5=cd81cb48621099a3fb38f73889f6dd88"

388. Bisello D., Paccagnella A., Pantano D., Gotra Yu., Malakhov N., Jejer V., Kushpil V., Sadygov Z.,"Metal-Resistive layer-Silicon (MRS) avalanche detectors with negative feedback",1995,"Nuclear Inst. and Methods in Physics Research, A","360","1-2",,"83","86",,"10.1016/0168-9002(94)01708-5","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0039717539&doi=10.1016%2f0168-9002%2894%2901708-5&partnerID=40&md5=e97dcf9f4d17557737025f2a3df9a3e8"

389. Azzi P., Bacchetta N., Barnett B.A., Bailey M., Bedeschi F., Bisello D., Cammerata J.D., Carithers W.C., Chao H.Y., Chiou C.N., Cihangir S., Ely R.P., Engels Jr. E., Franceschi A., Barbaro-Galtieri A., Guerra M., Garfinkel A.F., Gillespie G., Glenzinski D., Gonzalez H., Gonzalez S., Grimm C., Haber C., Hawke T., Hrycyk M., Incandela J., Kajfasz E., Klein R., Kleinfelder S., Kruse M., Lundberg B., Mando' F., Matthews J., Menzione A., Nelson C., Paccagnella A., Paulini M., Peters M.D., Praticelli N., Raffaelli F., Ratzmann P., Schindler A., Sciacca F.G., Scott L., Shapiro M.D., Shaw N.M., Shaw T., Shepard P., Singh P., Skarha J.E., Snider F.D., Song L., Spalding J., Stuart D., Tipton P., Tkaczyk S., Tollefson K., Tousignant D., Turner K., Wang C.H., Wang M.J., Watts G., Wenzel H., Wu S.C., Yao W., Yarema R., Yun J.C., Zetti F.,"SVX', the new CDF silicon vertex detector",1995,"Nuclear Inst. and Methods in Physics Research, A","360","1-2",,"137","140",,"10.1016/0168-9002(95)00087-9","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0001122963&doi=10.1016%2f0168-9002%2895%2900087-9&partnerID=40&md5=265715f257fd2ebe877aee5766e8120d"

390. Antos J., Chao H.-Y., Cheng M.-T., Chu M.-L., Guo R.-S., Ho C.-L., Teng P.-K., Wang M.-J., Wu S.-C., Yeh G.-P., Yeh P., Blucher E., Frisch H., Sullivan G., Barsotti E., Cihangir S., Gonzalez H., Hrycyk M., Lindenmeyer M., Pawlak J., Ratzmann P., Spalding J., Spiegel L., Swoboda C., Yarema R., Zimmerman S., Zimmerman T., Gay C., Huth J., Oliver J., Iwata Y., Ohmoto T., Ohsugi T., Barnett B., Cammerata J., Skarha J., Bruner N., Frautschi M., Gold M., Hoeferkamp M., Kingsberry P., Matthews J., Yu L., Seidel S., Thomas T.L., Wells S., Tamura N., Bacchetta N., Bisello D., Castro A., Paccagnella A., Boudreau J., Engels Jr. E., Hu P., Huffman T., Shepard P., Vandenbrink S., Bedeschi F., Belforte S., Bonaccorso C., Franceschi A., Galeotti S., Giannetti P., Menzione A., Morsani F., Dell'Orso M., Punzi G., Raffaelli F., Ristori L., Zetti F., Bortoletto D., Garfinkel A., Hardmann A., Hoffman K., Shaw N.M., Done J., Kamon T., Scarpine V., Trost H.-J., Wolinski J., Benjamin D., Sill A., Hou J.-F., Ely R., Haber C., Kipnis I., Kleinfelder S., Milgrome O.,"The SVX II silicon vertex detector upgrade at CDF",1995,"Nuclear Inst. and Methods in Physics Research, A","360","1-2",,"118","124",,"10.1016/0168-9002(94)01230-X","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0010026397&doi=10.1016%2f0168-9002%2894%2901230-X&partnerID=40&md5=38e0c7328d19cc020c77dea24375634f"

391. Meneghesso G., De Bortoli E., Paccagnella A., Zanoni E., Canali C.,"Recovery of Low Temperature Electron Trapping in AlGaAs/InGaAs PM-HEMT's Due to Impact-Ionization",1995,"IEEE Electron Device Letters","16","7",,"336","338",,"10.1109/55.388726","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0029344101&doi=10.1109%2f55.388726&partnerID=40&md5=644527b499af13fba33649d6dbebf1f4"
392. Meneghesso G., Haddab Y., De Bortoli E., Paccagnella A., Zanoni E., Canali C.,"Study of low-temperature degradation of AlGaAs/InGaAs pseudomorphic HEMT's",1995,"European Solid-State Device Research Conference",,,5435981,"169","172",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0342748257&partnerID=40&md5=1c716cc58c3c598b952e903f7726910c"
393. Bacchetta N., Bisello D., Candelori A., Paccagnella A., Spada M., Vanzi M.,"SPICE Analysis of Signal Propagation in Si Microstrip Detectors",1995,"IEEE Transactions on Nuclear Science","42","4",,"459","466",,"10.1109/23.467801","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0029358334&doi=10.1109%2f23.467801&partnerID=40&md5=c1f0aeea3cb26c881f3e0b6ad1acb491"
394. Bisello D., Paccagnella A., Pantano D., Gotra Yu., Malakhov N., Jejer V., Kushpil V., Sadygov Z.,"Electrical characteristics of Metal-Resistive layer-Silicon (MRS) avalanche detectors",1995,"Nuclear Physics B (Proceedings Supplements)","44","1-3",,"397","401",,"10.1016/S0920-5632(95)80060-3","https://www.scopus.com/inward/record.uri?eid=2-s2.0-21844515870&doi=10.1016%2fS0920-5632%2895%2980060-3&partnerID=40&md5=7ca3e58b4d83bd43f551636231af6b39"
395. Castaldini A., Cavallini A., Del Papa C., Fuochi G., Alietti M., Canali C., Nava F., Paccagnella A., Lanzieri C.,"Defects induced by protons and γ-rays in semi-insulating GaAs detectors",1995,"Materials Research Society Symposium - Proceedings","373",,,"523","528",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0029238801&partnerID=40&md5=e66227618391401d47063befd72fdd22"
396. Bacchetta N., Bisello D., Candelori A., Paccagnella A., Spada M., Vanzi M.,"Network analysis of signal propagation in Si microstrip detectors",1994,"IEEE Nuclear Science Symposium & Medical Imaging Conference","2",,,"679","683",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0028753516&partnerID=40&md5=5cd5b4cd126c5d9f8520e3cca4028409"
397. Bacchetta N., Bisello D., Canali C., Da Ros R., Giraldo A., Gotra Yu., Paccagnella A., Piacentino G.M., Verzellesi G.,"FOXFET biased microstrip detectors: an investigation of radiation sensitivity",1994,"Nuclear Inst. and Methods in Physics Research, A","342","1",,"39","48",,"10.1016/0168-9002(94)91408-7","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0028401019&doi=10.1016%2f0168-9002%2894%2991408-7&partnerID=40&md5=f2ce964cbadfe48ae37099e0110c195a"
398. Holmes-Siedle A., Robbins M., Watts S., Allport P., Brenner R., Moser H.-G., Roe S., Straver J., Weilhammer P., Chochula P., Mikulec I., Moszczynski S., Turala M., Dabrowski W., Grybos P., Idzik M., Loukas D., Misiakos K., Siotis I., Zachariadou K., Dulinski W., Michele J., Schaeffer M., Turchetta R., Booth P., Richardson J., Smith N., Gill K., Hall G., Sachdeva R., Sotthibandhu S., Vitè D., Wheadon R., Arrighi C., Delpierre P., Habrard M.-C., Clemens J.-C., Mouthuy T., Avset B.S., Evensen L., Hanneborg A., Hansen T.A., Bisello D., Giraldo A., Paccagnella A., Kurchaninov L., Spiriti E., Apsimon R., Giubellino P., Ramello L., Prado da Silva W.L., Krammer M., Schuster M.,"Radiation tolerance of single-sided silicon microstrips",1994,"Nuclear Inst. and Methods in Physics Research, A","339","3",,"511","523",,"10.1016/0168-9002(94)90188-

0","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0028379831&doi=10.1016%2f0168-9002%2894%2990188-0&partnerID=40&md5=1909a630417e331eeabfa9c48bbd19aa"

399. Paccagnella A.P., Bisello D.B., Da Rold M., Gotra Y., Benetti P.,"Study of Punch Through Characteristics in Irradiated MOSFETs",1994,"IEEE Transactions on Nuclear Science","41","6",,"2511","2520",,"10.1109/23.340609","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0028705541&doi=10.1109%2f23.340609&partnerID=40&md5=85b58032af93216227ed6e13d3ea7e61"

400. Zanoni E., De Bortoli E., Meneghesso G., Neviani A., Vendrame L., Paccagnella A., Canali C.,"A new degradation mechanism induced by DX-centers in AlGaAs/InGaAs PM-HEMT's",1994,"European Solid-State Device Research Conference",,, 5435775,"539","542",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-77950301239&partnerID=40&md5=1c722d571a8cf11fcae754c0155adf9c"

401. Bacchetta N.B., Ros R.D., Giraldo A.G., Gotra Y.G., Bisello D.B., Paccagnella A.P., Verzellesi G.V.,"Punch-Through Characteristics Of Foxfet Biased Detectors",1994,"IEEE Transactions on Nuclear Science","41","4",,"804","810",,"10.1109/23.322810","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0028494406&doi=10.1109%2f23.322810&partnerID=40&md5=55f250ede5cda6ecc039f6499797e86f"

402. Bacchetta N., Bisello D., Da Ros R., Giraldo A., Gotra Yu., Paccagnella A., Verzellesi G.,"Punch-through behaviour of FOXFET biased detectors",1994,"IEEE Nuclear Science Symposium & Medical Imaging Conference",,"pt 1",,"53","57",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0028184713&partnerID=40&md5=f29ec87d232cd0164c674537df80e2bc"

403. Bacchetta N., Bisello D., Bolla G., Canali C., Fuochi P.G., Paccagnella A.,"Radiation effects on ac-coupled microstrip silicon detectors",1993,"Nuclear Inst. and Methods in Physics Research, A","326","1-2",,"381","385",,"10.1016/0168-9002(93)90380-Z","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0027557854&doi=10.1016%2f0168-9002%2893%2990380-Z&partnerID=40&md5=6f6239e1f8e541535fcd3403af721b69"

404. Tedesco C., Canali C., Magistrali F., Paccagnella A., Zanoni E.,"Failures of ALGaAs/GaAs HEMTs induced by hot electrons",1993,"Quality and Reliability Engineering International","9","4",,"371","376",,"10.1002/qre.4680090424","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0027629671&doi=10.1002%2fqre.4680090424&partnerID=40&md5=206c1ff6ce5dfb2d3b7edf71dbbb0137"

405. Bacchetta N., Bisello D., Gotra Y., Paccagnella A., Verzellesi G., Canali C., Fuochi P.G.,"Degradation of Silicon ac-coupled Microstrip Detectors Induced by Radiation",1993,"IEEE Transactions on Nuclear Science","40","6",,"2001","2007",,"10.1109/23.273452","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0027816378&doi=10.1109%2f23.273452&partnerID=40&md5=d7788f65c5887718bdda147fef3d1d60"

406. Bacchetta N., Bisello D., Canali C., Da Ros R., Fuochi P.G., Fusaro G., Giraldo A., Gotra Y., Paccagnella A., Verzellesi G.,"Radiation Tolerance of the FOXFET biasing scheme for AC-coupled Si microstrip detectors",1993,"IEEE Transactions on Nuclear Science","40","6",,"1602","1609",,"10.1109/23.273500","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

0027885870&doi=10.1109%2f23.273500&partnerID=40&md5=6d5e99910cb70e9cb475acbeaee2d884"

407. Tedesco C., Canali C., Magistrali F., Paccagnella A., Zanoni E.,"Hot-electron induced degradation in AlGaAs/GaAs HEMTs",1992,"European Solid-State Device Research Conference",,,5435127,"405","408",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-84926419646&partnerID=40&md5=0fa25d1e3b093bbdb52e3996ccaef87e"

408. Paccagnella A., Tedesco C., Canali C., Cetronio A., Lanzieri C.,"Frequency dispersion of transconductance: A tool to characterise deep levels IN III-V FETs",1992,"Electronics Letters","28","22",,"2107","2109",,"10.1049/el:19921351","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0026932783&doi=10.1049%2fel%3a19921351&partnerID=40&md5=1b643a286b703f56edd0f8ad7df73f8f"

409. Tedesco C., Canali C., Magistrali F., Paccagnella A., Zanoni E.,"Hot-electron induced degradation in AlGaAs/GaAs HEMTs",1992,"Microelectronic Engineering","19","1-4",,"405","408",,"10.1016/0167-9317(92)90463-2","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0026925658&doi=10.1016%2f0167-9317%2892%2990463-2&partnerID=40&md5=1f1b17671f22cfabf0d67b21d8a67618"

410. Zanoni E., Malik R., Pavan P., Nagle J., Paccagnella A., Canali C.,"Negative Base Current and Impact Ionization Phenomena in AlGaAs/GaAs HBT's",1992,"IEEE Electron Device Letters","13","5",,"253","255",,"10.1109/55.145044","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0026867535&doi=10.1109%2f55.145044&partnerID=40&md5=a8b81ec5b4bcb5b2bd1ea834d35c1aa4"

411. Zanoni E., Paccagnella A., Pisoni P., Tedesco C., Manfredi M., Bigliardi S., Canali C.,"Impact Ionization and Light Emission in AlGaAs/GaAs HEMT's",1992,"IEEE Transactions on Electron Devices","39","8",,"1849","1857",,"10.1109/16.144674","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0026908578&doi=10.1109%2f16.144674&partnerID=40&md5=6e98d3591bdf8a51b1f47c410b385a83"

412. Callegari A., Sadana D.K., Buchanan D.A., Paccagnella A., Marshall E.D., Tischler M.A., Norcott M.,"Properties of SiO2/Si/GaAs structures formed by solid phase epitaxy of amorphous Si on GaAs",1991,"Applied Physics Letters","58","22",,"2540","2542",,"10.1063/1.104820","https://www.scopus.com/inward/record.uri?eid=2-s2.0-36449004718&doi=10.1063%2f1.104820&partnerID=40&md5=b7aec5bc8ca8ab81d0e2b191f9301612"

413. Paccagnella A., Callegari A., Carnera A., Gasser M., Latta E., Murakami M., Norcott M.,"WNx Schottky diodes on plasma treated GaAs",1991,"Journal of Applied Physics","69","4",,"2356","2364",,"10.1063/1.348718","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0347643345&doi=10.1063%2f1.348718&partnerID=40&md5=d26b78482ed64f7c25938f9abb0ad60d"

414. Zanoni E., Paccagnella A., Pisoni P., Telaroli P., Tedesco C., Canali C., Testa N., Manfredi M.,"Impact ionization, recombination, and visible light emission in AlGaAs/GaAs high electron mobility transistorsa)",1991,"Journal of Applied Physics","70","1",,"529","531",,"10.1063/1.350269","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0342831634&doi=10.1063%2f1.350269&partnerID=40&md5=d8248a378bddbc8566ce65f7f1085bd9"

415. Carbone A., Demichelis F., Kaniadakis G., Gozzo F., Murri R., Pinto N., Schiavulli L., Della Mea G., Drigo A., Paccagnella A.,"Physical properties of hydrogenated amorphous gallium arsenide",1991,"Il Nuovo Cimento D","13","5",,"571","577",,"10.1007/BF02451284","https://www.scopus.com/inward/record.uri?eid=2-s2.0-51249178684&doi=10.1007%2fBF02451284&partnerID=40&md5=177eec291e0461f8bc016f1430fb1604"

416. Zanoni E., Bigliardi S., Manfredi M., Paccagnella A., Pisoni P., Telaroli P., Tedesco C., Canali C.,"Correlation between impact ionisation, recombination and visible light emission in GaAs MESFETs",1991,"Electronics Letters","27","9",,"770","772",,"10.1049/el:19910479","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0026135797&doi=10.1049%2fel%3a19910479&partnerID=40&md5=1c6e3d58839bf65783c3bdbe8c61379c"

417. Canali C., Magistrali F., Paccagnella A., Sangalli M., Tedesco C., Zanoni E.,"Trap-related effects in AlGaAs/GaAs HEMTs",1991,"IEE proceedings. Part G. Electronic circuits and systems","138","1",,"104","108",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0026105223&partnerID=40&md5=6ff5c099e7caa31ba040a6da527f4c06"

418. Paccagnella A., Callegari A.,"GaAs surface plasma treatments for Schottky contacts",1991,"Solid State Electronics","34","12",,"1409","1414",,"10.1016/0038-1101(91)90037-Y","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0026371921&doi=10.1016%2f0038-1101%2891%2990037-Y&partnerID=40&md5=2aaf312924af2189e0237c6d9740a589"

419. Paccagnella A., Zanoni E., Tedesco C.,"Correlation Between Surface-State Density and Impact Ionization Phenomena in GaAs MESFET'S",1991,"IEEE Transactions on Electron Devices","38","12",,"2682","2684",,"10.1109/16.158692","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0026399114&doi=10.1109%2f16.158692&partnerID=40&md5=47d8b686d130e5f7071daa046a4682cd"

420. Tedesco C., Manfredi M., Paccagnella A., Zanoni E., Canali C.,"Hot carrier induced photon emission in submicron GaAs devices",1991,"Technical Digest - International Electron Devices Meeting, IEDM","1991-January",, 235361,"437","440",,"10.1109/IEDM.1991.235361","https://www.scopus.com/inward/record.uri?eid=2-s2.0-84954169358&doi=10.1109%2fIEDM.1991.235361&partnerID=40&md5=ca1a18ef17a4a313e1854ef1183548e7"

421. Canali C., Paccagnella A., Zanoni E., Lanzieri C., Cetronio A.,"Comments on “Impact Ionization in GaAs MESFET's”",1991,"IEEE Electron Device Letters","12","2",,"80","81",,"10.1109/55.75710","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0026108318&doi=10.1109%2f55.75710&partnerID=40&md5=33a1ec0e44879f48ad157ecb40fc3f7b"

422. Zanoni E., Tedesco C., Paccagnella A., Canali C., Bigliardi S., Manfredi M.,"High energy photon emission in GaAs MESFETs and AlGaAs/GaAs HEMTs",1991,"European Solid-State Device Research Conference",,, 5435266,"581","584",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-84907754005&partnerID=40&md5=fee18dbb8b10ee2d827633243d9b1815"

423. Amato G., Della Mea G., Fizzotti F., Manfredotti C., Marchisio R., Paccagnella A.,"Hydrogen bonding in amorphous silicon with use of the low-pressure chemical-vapor-deposition technique",1991,"Physical Review

B","43","8",,"6627","6632",,"10.1103/PhysRevB.43.6627","https://www.scopus.com/inward/record.uri?eid=2-s2.0-2842608414&doi=10.1103%2fPhysRevB.43.6627&partnerID=40&md5=1e9e294e541f661b9b59e2a1d2e85931"

424. Canali C., Paccagnella A., Pisoni P., Tedesco C., Telaroli P., Zanoni E.,"Impact Ionization Phenomena in Algaas/GaAs Hemt’s",1991,"IEEE Transactions on Electron Devices","38","11",,"2571","2573",,"10.1109/16.97428","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0026254249&doi=10.1109%2f16.97428&partnerID=40&md5=419a48262ea8b17edf0a2b756b978e53"
425. Zanoni E., Tedesco C., Paccagnella A., Canali C., Bigliardi S., Manfredi M.,"High energy photon emission in GaAs MESFETs and AlGaAs/GaAs HEMTs",1991,"Microelectronic Engineering","15","1-4",,"581","584",,"10.1016/0167-9317(91)90289-P","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0026238586&doi=10.1016%2f0167-9317%2891%2990289-P&partnerID=40&md5=28d5f8d844079bdfbd128aec74e8957a"
426. Canali C., Magistrali F., Paccagnella A., Sangalli M., Tedesco C., Zanoni E.,"Degradation mechanisms in 2 W MESFETs",1991,"Quality and Reliability Engineering International","7","4",,"343","349",,"10.1002/qre.4680070422","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0026189242&doi=10.1002%2fqre.4680070422&partnerID=40&md5=493ce8a64a3fd70194ceefb1bb857c1d"
427. Paccagnella A., Callegari A., Batey J., Lacey D.,"Properties and thermal stability of the SiO2/GaAs interface with different surface treatments",1990,"Applied Physics Letters","57","3",,"258","260",,"10.1063/1.104217","https://www.scopus.com/inward/record.uri?eid=2-s2.0-33644620730&doi=10.1063%2f1.104217&partnerID=40&md5=b124708c0887af2ab900898c63abaa26"
428. Battaglin G., Lo Russo S., Paccagnella A., Polato P., Principi G.,"Kr-induced mixing and annealing effects at the Fe/SiO2 interface",1990,"Journal of Non-Crystalline Solids","123","1-3",,"427","431",,"10.1016/0022-3093(90)90814-3","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0025476158&doi=10.1016%2f0022-3093%2890%2990814-3&partnerID=40&md5=f9409fa239c034eb96d8723d639814b9"
429. Paccagnella A., Wang L.C., Canali C., Castellaneta G., Dapor M., Donzelli G., Zanoni E., Lau S.S.,"Pd/Ge ohmic contacts for GaAs metal-semiconductor field effect transistors: Technology and performance",1990,"Thin Solid Films","187","1",,"9","18",,"10.1016/0040-6090(90)90105-M","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0025431910&doi=10.1016%2f0040-6090%2890%2990105-M&partnerID=40&md5=0408480497b275b1255679012eb9e574"
430. Bagnoli P.E., Paccagnella A., Callegari A., Fantini F.,"Surface characteristics of plasma treated WNx/GaAs contacts from C-V measurements",1990,"European Solid-State Device Research Conference",,, 5436413,"113","116",,,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-84907991795&partnerID=40&md5=15a0e06a9e6717333debf0c3e4957342"
431. Petit J.-C., Mea G.D., Dran J.-C., Magonthier M.-C., Mando P.A., Paccagnella A.,"Hydrated-layer formation during dissolution of complex silicate glasses and minerals",1990,"Geochimica et Cosmochimica Acta","54","7",,"1941","1955",,"10.1016/0016-7037(90)90263-K","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0025594316&doi=10.1016%2f0016-7037%2890%2990263-K&partnerID=40&md5=c30e0df5e029dc09366bbc07bc548ac0"
432. Canali C., Corti E., Magistrali F., Sangalli M., Paccagnella A., Tedesco C., Vanzi M.,"Thermally induced parasitic ungated FET in power MESFETs",1990,"Microelectronics Reliability","30","5",,"903","905",,"10.1016/0026-2714(90)90559-

6","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0025625968&doi=10.1016%2f0026-2714%2890%2990559-6&partnerID=40&md5=71faed08cccc6cd7d20f804168dc1956"

433. Canali C., Corti E., Gabrielli B., Magistrali F., Paccagnella A., Sangalli M., Tedesco C.,"Change Of G<inf>M</inf>(F) And Breakdown Voltage Induced By Thermal Annealing Of Surface States In Power Mesfet'S",1990,"IEEE Transactions on Electron Devices","37","4",,"1163","1165",,"10.1109/16.52456","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0025417219&doi=10.1109%2f16.52456&partnerID=40&md5=2c19b9f6311aa0f6d2b995d71120c7a3"
434. Zanoni E., Callegari A., Canali C., Fantini F., Hartnagel H.L., Magistrali F., Paccagnella A., Vanzi M.,"Metal–GaAs interaction and contact degradation in microwave MESFETs",1990,"Quality and Reliability Engineering International","6","1",,"29","46",,"10.1002/qre.4680060108","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0025244479&doi=10.1002%2fqre.4680060108&partnerID=40&md5=f9eb68150be1f95a41906537fad8d2c9"
435. Zanoni E., Bigliardi S., Capelletti R., Lugli P., Magistrali F., Manfredi M., Paccagnella A., Testa N., Canali C.,"Light Emission in AlGaAs/GaAs HEMT’s and GaAs MESFET’s Induced by Hot Carriers",1990,"IEEE Electron Device Letters","11","11",,"487","489",,"10.1109/55.63009","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0025521829&doi=10.1109%2f55.63009&partnerID=40&md5=542a041270874ae5f9ec1647560c1bdb"
436. Petit J.-C., Dran J.-C., Mea G.D., Paccagnella A.,"Dissolution mechanisms of silicate minerals yielded by intercomparison with glasses and radiation damage studies",1989,"Chemical Geology","78","3-4",,"219","227",,"10.1016/0009-2541(89)90059-4","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0024899360&doi=10.1016%2f0009-2541%2889%2990059-4&partnerID=40&md5=2b027eb8584db948f4b44648ef26dc68"
437. Paccagnella A., Callegari A., Latta E., Gasser M.,"Schottky diodes on hydrogen plasma treated n-GaAs surfaces",1989,"Applied Physics Letters","55","3",,"259","261",,"10.1063/1.101922","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0000924255&doi=10.1063%2f1.101922&partnerID=40&md5=d7b5ac12ce420f0e15ce236a5b1b8430"
438. Paccagnella A., Han C.C., Lau S.S., Gasparotto A., Carnera A., Canali C.,"Thermal stability of TaSix/n-GaAs metallizations",1989,"Thin Solid Films","176","2",,"187","196",,"10.1016/0040-6090(89)90092-8","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0024735799&doi=10.1016%2f0040-6090%2889%2990092-8&partnerID=40&md5=9fd6f2b6cf22cf498ad41d675d23f116"
439. Battaglin G., Lo Russo S., Paccagnella A., Polato P., Principi G.,"Ion beam mixing at the Fe/SiO2 interface",1989,"Nuclear Inst. and Methods in Physics Research, B","39","1-4",,"126","129",,"10.1016/0168-583X(89)90754-4","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0024621101&doi=10.1016%2f0168-583X%2889%2990754-4&partnerID=40&md5=ab21e4e5891861602231f6280e24ae6c"
440. Principi G., Polato P., Paccagnella A., Maddalena A., Russo S.L., Battaglin G.,"Effect of Kr ion irradiation on the Fe/SiO2 interface",1989,"Hyperfine Interactions","46","1-4",,"517","526",,"10.1007/BF02398238","https://www.scopus.com/inward/record.uri?eid=2-s2.0-34249966392&doi=10.1007%2fBF02398238&partnerID=40&md5=f638a2603db2647267c2bf92c202a88d"

441. Moersch G., Rava P., Schwarz F., Paccagnella A.,"Thin-Film Transistors with Sputtered CdSe as Semiconductor",1989,"IEEE Transactions on Electron Devices","36","2",,"449","451",,"10.1109/16.19949","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0024610774&doi=10.1109%2f16.19949&partnerID=40&md5=1b3ba3da693df33eba8e78834c2dd7d9"
442. Petit J.-C., Dran J.-C., Paccagnella A., Della Mea G.,"Structural dependence of crystalline silicate hydration during aqueous dissolution",1989,"Earth and Planetary Science Letters","93","2",,"292","298",,"10.1016/0012-821X(89)90077-0","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0024484613&doi=10.1016%2f0012-821X%2889%2990077-0&partnerID=40&md5=862cb1a6ba6e4afa3810c32d506ed708"
443. Paccagnella A., Callegari A., Braslau N., Hovel H., Murakami M.,"WNx Diodes on Plasma-Treated GaAs Surfaces",1989,"IEEE Transactions on Electron Devices","36","11",,"2595","2597",,"10.1109/16.43686","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0024769423&doi=10.1109%2f16.43686&partnerID=40&md5=3ab45f480e9db5fdbb1d86d99b751bf8"
444. Carturan G., della Mea G., Paccagnella A., Soraru G.D., Rizzo C.,"Durability against Ca(OH)2 attack of soda-lime glasses coated by various gel-deposited oxides",1989,"Journal of Non-Crystalline Solids","111","1",,"91","97",,"10.1016/0022-3093(89)90428-6","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0024739134&doi=10.1016%2f0022-3093%2889%2990428-6&partnerID=40&md5=6afe8c8ab2fbbaed1d4242113d6a2991"
445. Demichelis F., Kaniadakis G., Tagliaferro A., Tresso E., Della Mea G., Paccagnella A.,"Investigation on structure and optoelectronic properties of hydrogenated amorphous CSiGe:H alloys",1989,"Solid State Communications","70","3",,"381","384",,"10.1016/0038-1098(89)90348-7","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0024649454&doi=10.1016%2f0038-1098%2889%2990348-7&partnerID=40&md5=69fdf7adc88cb2ef9ca35b75c84102df"
446. Dran J.-C., Della Mea G., Paccagnella A., Petit J.-C., Trotignon L.,"Aqueous dissolution of alkali silicate glasses: Reappraisal of mechanisms by H and Na depth profiling with high energy ion beams",1988,"Physics and Chemistry of Glasses","29","6",,"249","255",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0024130757&partnerID=40&md5=3efaab8743d2423a06eb552e9c786c6c"
447. Petit J.-C., Dran J.-C., Mea G.D., Brousse C., Paccagnella A., Mando P.A.,"Ion-implantation effects on silicates: New insights into their aqueous dissolution",1988,"Nuclear Inst. and Methods in Physics Research, B","32","1-4",,"498","503",,"10.1016/0168-583X(88)90260-1","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0024276040&doi=10.1016%2f0168-583X%2888%2990260-1&partnerID=40&md5=b6b13f1f428509209b208557a60915d6"
448. Principi G., Zhang P.Q., Battaglin G., Lo Russo S., Paccagnella A.,"CEMS analysis of Ar+ irradiated Fe/SiO2 system",1988,"Journal of Materials Science Letters","7","5",,"484","486",,"10.1007/BF01730699","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0024015139&doi=10.1007%2fBF01730699&partnerID=40&md5=71c4b647069e635c6c503a596b995422"
449. Dran J.-C., Mea G.D., Paccagnella A., Petit J.-C., Menager M.-T.,"Sorption of Actinide Analogues on Granite Minerals Studied by MeV Ion Beam Techniques",1988,"Radiochimica Acta","44-45","2",,"299","304",,"10.1524/ract.1988.4445.2.299","https://www.scopus.com/inward/record.uri?eid=2-s2.0-

0024244560&doi=10.1524%2fract.1988.4445.2.299&partnerID=40&md5=ef47d768ce40af6964fafe872a91348a"

450. Paccagnella A., Canali C., Donzelli G., Wang L.C., Lau S.S.,"GaAs Mesfets with Nonalloyed Ohmic Contacts: Technology and Performance",1988,"Electronics Letters","24","11",,"708","709",,"10.1049/el:19880478","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0024010105&doi=10.1049%2fel%3a19880478&partnerID=40&md5=4703f09a6fa64e947c581355460727a4"
451. Paccagnella A., Canali C., Donzelli G., Zanoni E., Zanetti R., Lau S.S.,"Non-alloyed Ge/Pd ohmic contact for GaAs MESFET's",1988,"European Solid-State Device Research Conference",,, 5436953,"C4441","C4444",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-84907780033&partnerID=40&md5=08449a4166174742ae26752599dd9247"
452. Petit J.-C., Dran J.-C., Della Mea G., Brousse C., Paccagnella A., Mando P.A.,"Ion-implantation effects on silicates: New insights into their aqueous dissolution",1988,"NUCL. WASTE MATER. WORKSHOP","32","1-4",,"498","503",,"10.1016/0168-583X(88)90260-1","https://www.scopus.com/inward/record.uri?eid=2-s2.0-17344377160&doi=10.1016%2f0168-583X%2888%2990260-1&partnerID=40&md5=c23123efd76cdcd617bf14b7121179a2"
453. Zhang P.Q., Principi G., Paccagnella A., Russo S.L., Battaglin G.,"Characterization of the ion beam mixed Fe/SiO2 interface by Mössbauer spectroscopy",1987,"Nuclear Inst. and Methods in Physics Research, B","28","4",,"561","566",,"10.1016/0168-583X(87)90503-9","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0023450748&doi=10.1016%2f0168-583X%2887%2990503-9&partnerID=40&md5=ac90e6f673b0b83f046f18cd8669b3b7"
454. Battaglin G., Lo Russo S., Paccagnella A., Principi G., Zhang P.Q.,"Ion beam mixing effects in the Ar+-irradiated Fe/SiO2 system",1987,"Nuclear Inst. and Methods in Physics Research, B","27","3",,"402","409",,"10.1016/0168-583X(87)90520-9","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0023386385&doi=10.1016%2f0168-583X%2887%2990520-9&partnerID=40&md5=3643040177a5f9b229b9033dff1f3fe0"
455. Paccagnella A., Migliori A., Vanzi M., Zhang B., Lau S.S.,"Thermal stability of non-alloyed ohmic contact to n-GaAs",1987,"European Solid-State Device Research Conference",,, 5436709,"605","608",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-84907822065&partnerID=40&md5=4831fb364c215ae22be8c449fa81d8e6"
456. Canali C., Donzelli G., Fantini F., Vanzi M., Paccagnella A.,"Gold-based gate-sinking enhanced by inhomogeneities in power mesfets",1987,"Electronics Letters","23","2",,"83","84",,"10.1049/el:19870060","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0023119689&doi=10.1049%2fel%3a19870060&partnerID=40&md5=72dc62d2e74506872d11147da96014ab"
457. Paccagnella A., Majni G., Ottaviani G., Della Mea G.,"Effects of implanted hydrogen on Pd2Si formation",1985,"Applied Physics Letters","47","8",,"806","808",,"10.1063/1.95990","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0346863263&doi=10.1063%2f1.95990&partnerID=40&md5=083b962da8cd49f68984a350aeab5428"
458. Paccagnella A., Ottaviani G., Fabbri P., Ferla G., Queirolo G.,"Silicon diffusion in aluminium",1985,"Thin Solid Films","128","3-4",,"217","223",,"10.1016/0040-6090(85)90073-2","https://www.scopus.com/inward/record.uri?eid=2-s2.0-0022083722&doi=10.1016%2f0040-6090%2885%2990073-2&partnerID=40&md5=2c116cfd2f4a64d3fedb315ff0ee80d7"
459. Battaglin G., Dal Maschio R., Della Mea G., De Marchi G., Gottardi V., Guglielmi M., Mazzoldi P., Paccagnella A.,"Mechanical properties of ion implanted glasses",1984,"Nuclear Inst.

and Methods in Physics Research, B","1","2-3",,"253","257",,"10.1016/0168-583X(84)90077-6","https://www.scopus.com/inward/record.uri?eid=2-s2.0-30244469632&doi=10.1016%2f0168-583X%2884%2990077-6&partnerID=40&md5=df2bd90bdc3e896e672d036c11197e4b"

460. Battaglin G., Dal Maschio R., Della Mea G., De Marchi G., Gottardi V., Guglielmi M., Mazzoldi P., Paccagnella A.,"MECHANICAL PROPERTIES OF ION IMPLANTED GLASSES.",1983,"Nuclear Instruments and Methods in Physics Research, Section B: Beam Interactions with Materials and Atoms","229 (B1)","2-3",,"253","257",,,"https://www.scopus.com/inward/record.uri?eid=2-s2.0-0020709262&partnerID=40&md5=f1ef5f5a0c3e8ecad7f2de6a305ba094"